P25Q40TU/20TU

Ultra Low Power, 4M/2M-bit

Serial Multi I/O Flash Memory Datasheet

Performance Highlight

- *Wide Supply Range from 1.65 to 3.6V for Read, Erase and Program*
- *Ultra Low Power consumption for Read, Erase and Program*
- *X1, X2 and X4 Multi I/O, QPI Support*
- *High reliability with 100K cycling and 20 Year-retention*

1 Overview

General

- **Single 1.65V to 3.60V supply**
- **Industrial Temperature Range -40C to 85C**
- **Serial Peripheral Interface (SPI) Compatible: Mode 0 and Mode 3**
- **Single, Dual, Quad SPI, QPI**
    - Standard SPI: SCLK,CS#,SI,SO,WP#,HOLD#
    - Dual SPI: SCLK,CS#,IO0,IO1,WP#, HOLD#
    - Quad SPI: SCLK,CS#,IO0,IO1,IO2,IO3
    - QPI: SCLK,CS#,IO0,IO1,IO2,IO3
- **Flexible Architecture for Code and Data Storage**
    - Uniform 256-byte Page Program
    - Uniform 256-byte Page Erase
    - Uniform 4K-byte Sector Erase
    - Uniform 32K/64K-byte Block Erase
    - Full Chip Erase
- **Hardware Controlled Locking of Protected Sectors by WP Pin**
- **One Time Programmable (OTP) Security Register**
    - 3*512-Byte Security Registers With OTP Lock
- **128 bit unique ID for each device**
- **Fast Program and Erase Speed**
    - 2ms Single Page program time
    - 16ms Page erase time
    - 16ms 4K-byte sector erase time
    - 16ms 32K/64K-byte block erase time
- **JEDEC Standard Manufacturer and Device ID Read Methodology**
- **Ultra-Low Power Consumption**
    - 0.1uA Deep Power Down current
    - 9.0uA Standby current
    - 2.5mA Active Read current at 33MHz
    - 2.5mA Active Program or Erase current
- **High Reliability**
    - 100,000 Program / Erase Cycles
    - 20-year Data Retention
- **Industry Standard Green Package Options**
    - 8-Lead SOP (150mil)
    - 8-Pad USON (3x2x0.55mm, 1.5x1.5x0.45mm)
    - 8-Lead TSSOP
    - KGD for SiP

2 Description

The P25Q40TU is a serial interface Flash memory device designed for use in a wide variety of high-volume consumer based applications in which program code is shadowed from Flash memory into embedded or external RAM for execution. The flexible erase architecture of the device, with its page erase granularity it is ideal for data storage as well, eliminating the need for additional data storage devices.

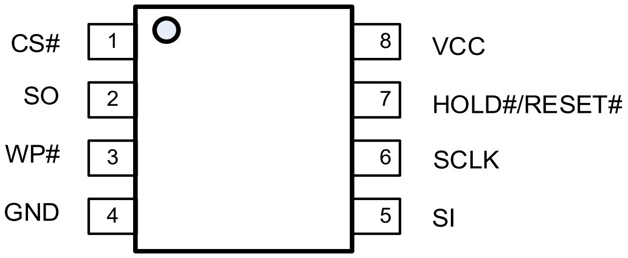
The erase block sizes of the device have been optimized to meet the needs of today's code and data storage applications. By optimizing the size of the erase blocks, the memory space can be used much more efficiently. Because certain code modules and data storage segments must reside by themselves in their own erase regions, the wasted and unused memory space that occurs with large sectored and large block erase Flash memory devices can be greatly reduced. This increased memory space efficiency allows additional code routines and data storage segments to be added while still maintaining the same overall device density.

The device also contains an additional 3*512-byte security registers with OTP lock (One-Time Programmable), can be used for purposes such as unique device serialization, system-level Electronic Serial Number (ESN) storage, locked key storage, etc.

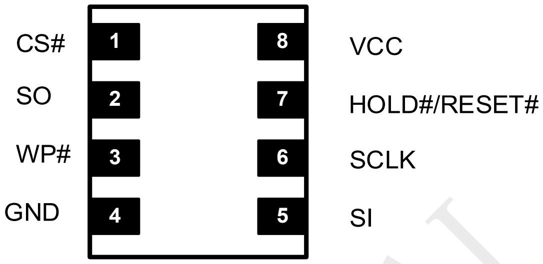
Specifically designed for use in many different systems, the device supports read, program, and erase operations with a wide supply voltage range of 1.65V to 3.6V. No separate voltage is required for programming and erasing.

3 Pin Definition

3.1 Pin Configurations



8-Lead SOP (150mil) and TSSOP



8-Pad USON (1.5x1.5mm/3x2mm)

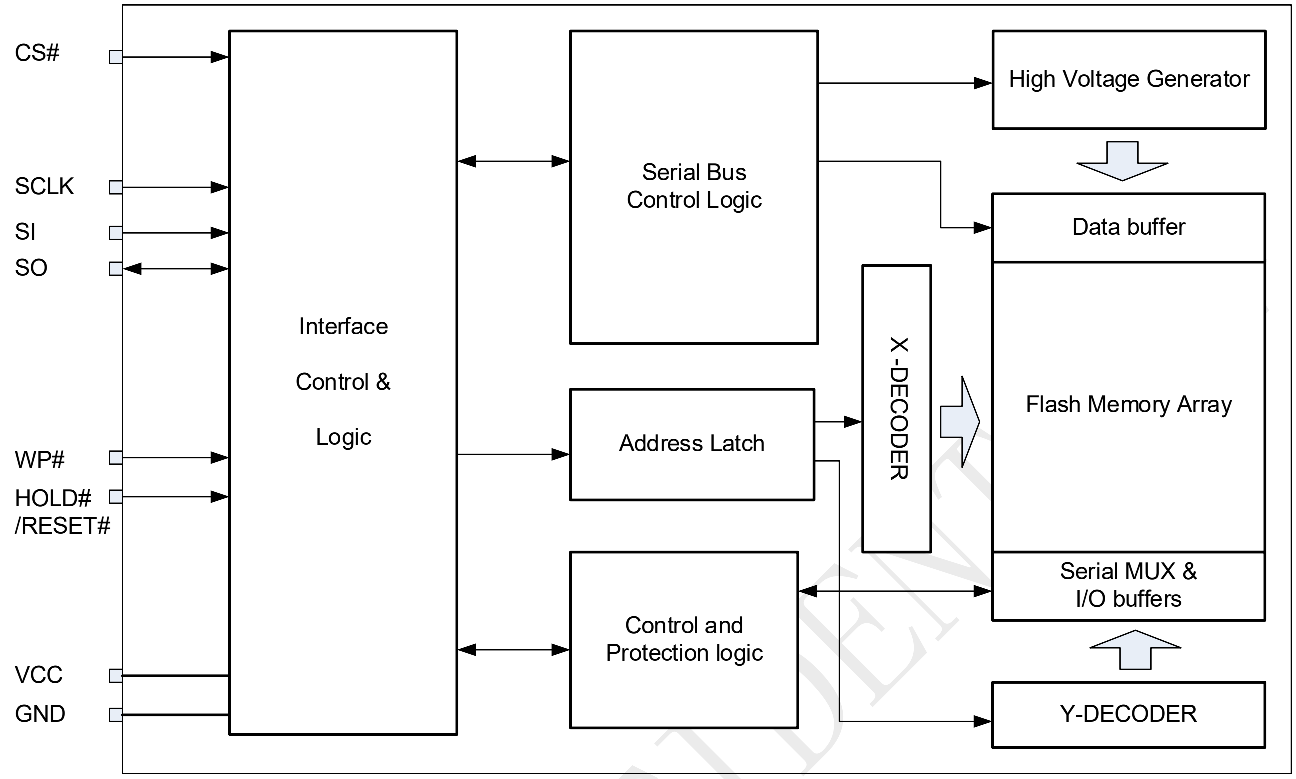
3.2 Pin Descriptions

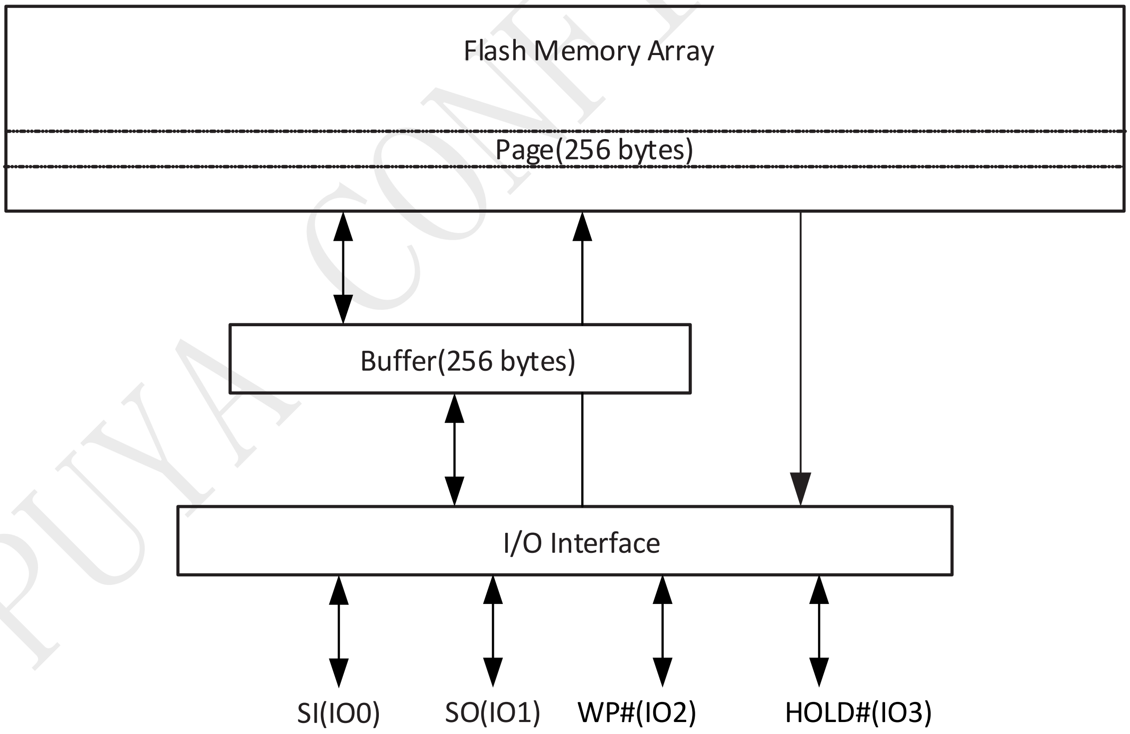
No.	Symbol	Extension	Remarks
1	CS#	-	Chip select
2	SO	SIO1	Serial data output for 1 x I/O Serial data input and output for 4 x I/O read mode
3	WP#	SIO2	Write protection active low Serial data input and output for 4 x I/O read mode
4	GND	-	Ground of the device
5	SI	SIO0	Serial data input for 1x I/O Serial data input and output for 4 x I/O read mode
6	SCLK	-	Serial interface clock input
7	HOLD#/RESET#	SIO3	Hardware Reset Pin Active low or to pause the device without deselecting the device Serial data input and output for 4 x I/O read mode
8	VCC	-	Power supply of the device

Notes:

1. SIO0 and SIO1 are used for Standard and Dual SPI instructions
2. SIO0 – SIO3 are used for Quad SPI/QPI instructions, WP# & HOLD# (or RESET#) functions are only available for Standard/Dual SPI.

4 Block Diagram





5 Electrical Specifications

5.1 Absolute Maximum Ratings

- Storage Temperature ....-65°C to +150°C
- Operation Temperature ....-40°C to +85°C
- Maximum Operation Voltage............. 4.0 V
- Voltage on Any Pin with
  respect to Ground. ....-0.6V to Vcc+0.5V
- DC Output Current ....5.0 mA

NOTICE: Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 5-1 Pin Capacitance [1]

Symbol	Parameter	Max.	Units	Test Condition
C_{OUT}	Output Capacitance	8	pF	V_{OUT}=GND
C_{IN}	Input Capacitance	6	pF	V_{IN}=GND

Note:

1. Test Conditions: T_A = 25°C, F = 1MHz, Vcc = 3.0V.

Figure 5-1 Input Test Waveforms and Measurement Level

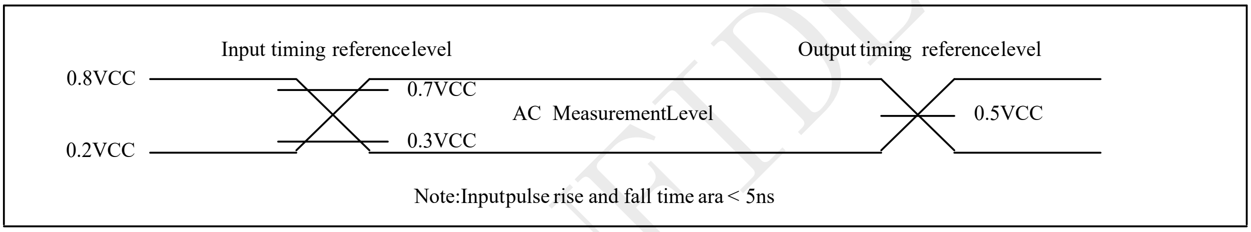
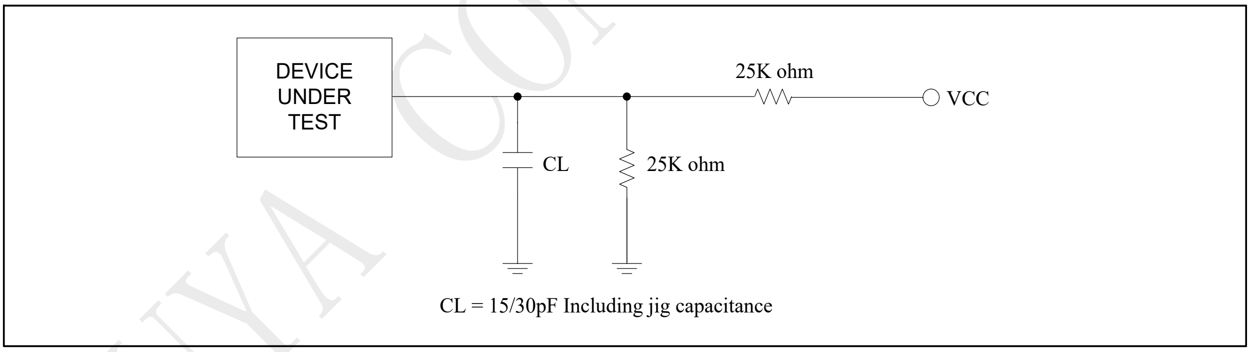


Figure 5-2 Output Loading



5.2 DC Characteristics

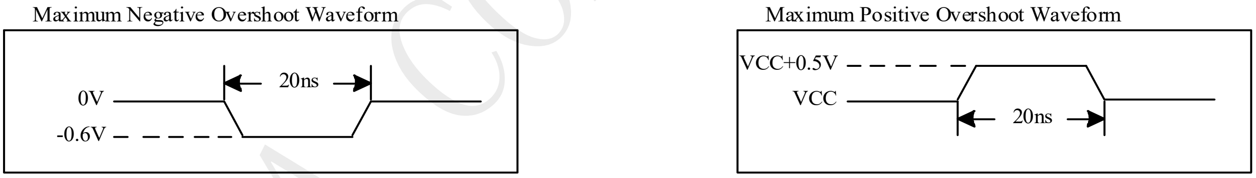
Table 5-2 DC parameters (Ta=-40°C ~ +85°C)

Symbol	Parameter	Conditions	1.65V~2.3V			2.3V~3.6V			Units
			Min	Typ(1)	Max	Min	Typ(2)	Max	
I_{DPD}	Deep power down current	CS#=Vcc, all other inputs at 0V or Vcc		0.1	1.5		0.2	2.5	uA
I_{SB}	Standby current	CS#, HOLD#, WP#=VIH all inputs at CMOS levels		9			10		uA
I_{CC1}	Read current(STR) (1, 2, 4 IO)	f=85MHz; IOUT=0mA		3.0	5.0		5.0	8	mA
		f=120MHz; IOUT=0mA		-	-		8.0	12	mA
I_{CC2}	Program current	CS#=Vcc		2.5	4.0		2.5	4.0	mA
I_{CC3}	Erase current	CS#=Vcc		2.5	4.0		2.5	4.0	mA
I_{LI}	Input load current	All inputs at CMOS level			1.0			2.0	uA
I_{LO}	Output leakage	All inputs at CMOS level			1.0			2.0	uA
V_{IL}	Input low voltage		-0.5		0.2Vcc	-0.5		0.3Vcc	V
V_{IH}	Input high voltage		0.8Vcc		Vcc+0.3	0.7Vcc		Vcc+0.3	V
V_{OL}	Output low voltage	IOL=100uA			0.2			0.2	V
V_{OH}	Output high voltage	IOH=-100uA	Vcc-0.2			Vcc-0.2			V

Note:

1. Typical values measured at 1.8V @ 25°C for the 1.65V to 3.6V range.
2. Typical values measured at 3.0V @ 25°C for the 2.3V to 3.6V range.

Figure 5-3 Maximum Overshoot Waveform



During DC conditions, input or I/O signals should remain equal to or between VSS and VCC. During voltage transitions, inputs or I/Os may negative overshoot to -0.6V or positive overshoot to VCC +0.5 V, for periods up to 20 ns.

5.3 AC Characteristics

Table 5-3-1 AC parameters(Ta=-40°C ~ +85°C)

Symbol	Alt.	Parameter	1.65V~3.6V			2.7V~3.6V			Units
			Min	Typ	Max	Min	Typ	Max	
fSCLK	fC	Clock Frequency for the following instructions: FREAD, RDSFDP, PP, SE, BE32K, BE, CE, DP, RES, WREN, WRDI, RDID, RDSR, WRSR(7)	D.C		85	D.C		120	MHz
fRSCLK	fR	Clock Frequency for READ instructions	D.C		33	D.C		40	MHz
fTSCLK	fT	Clock Frequency for 2READ,DREAD instructions			85			120	MHz
	fw	Clock Frequency for WREAD instructions			70			85	MHz
	fQ	Clock Frequency for 4READ,QREAD, QPI 0Bh,QPI EBh,QPI 0Ch instructions			85			120	MHz
fQPP		Clock Frequency for QPP (Quad page program)			85			120	MHz
tCH(1)	tCLH	Clock High Time	5.3			3.7			ns
tCL(1)	tCLL	Clock Low Time (fSCLK) 45% x (1fSCLK)	5.3			3.7			ns
tCLCH(7)		Clock Rise Time (peak to peak)	0.1			0.1			v/ns
tCHCL(7)		Clock Fall Time (peak to peak)	0.1			0.1			v/ns
tSLCH	tCSS	CS# Active Setup Time (relative to SCLK)	5			5			ns
tCHSL		CS# Not Active Hold Time (relative to SCLK)	5			5			ns
tDVCH	tDSU	Data In Setup Time	2			2			ns
tCHDX	tDH	Data In Hold Time	3			3			ns
tCHSH		CS# Active Hold Time (relative to SCLK)	5			5			ns
tSHCH		CS# Not Active Setup Time (relative to SCLK)	5			5			ns
tSHSL	tCSH	CS# Deselect Time From Read to next Read	20			20			ns
		CS# Deselect Time From Write,Erase,Program to Read Status Register	30			30			ns
tSHQZ(7)	tDIS	Output Disable Time			6			6	ns
tCLQV	tV	Clock Low to Output Valid Loading 30pF			7			7	ns
		Clock Low to Output Valid Loading 15pF			6			6	ns
tCLQX	tHO	Output Hold Time	0.8			0.8			ns
tHLCH		HOLD# Active Setup Time (relative to SCLK)	5			5			ns
tCHHH		HOLD# Active Hold Time (relative to SCLK)	5			5			ns
tHHCH		HOLD# Not Active Setup Time (relative to SCLK)	5			5			ns
tCHHL		HOLD# Not Active Hold Time (relative to SCLK)	5			5			ns
tHHQX	tLZ	HOLD# to Output Low-Z			6			6	ns
tHLQZ	tHZ	HOLD# to Output High-Z			6			6	ns
tWHSL(3)		Write Protect Setup Time	20			20			ns
tSHWL(3)		Write Protect Hold Time	100			100			ns
tDP		CS# High to Deep Power-down Mode			3			3	us
tRES1		CS# High To Standby Mode Without Electronic Signature Read			8			8	us
tRES2		CS# High To Standby Mode With Electronic Signature Read			8			8	us
tW		Write Status Register Cycle Time		8	12		8	12	ms
tReady		Reset recovery time(for erase/program operation except WRSR/WRCR)			50			50	us
		Reset recovery time(for WRSR/WRCR operation)		8	12		8	12	ms

Table 5-3-2 SPI Read Command Performance Comparison(MHz)

Read command	Dummy Cycles (VCC=1.65V~3.6V)				Dummy Cycles (VCC=2.7V~3.6V)			
	4	6	8	10	4	6	8	10
FREAD	-	-	85	-	-	-	120	-
DREAD	-	-	85	-	-	-	120	-
QREAD	-	-	85	-	-	-	120	-
2READ	70 (default)	-	85	-	85 (default)	-	120	-
4READ	-	70 (default)	-	85	-	85 (default)	-	120

Table 5-3-3 QPI Read Command Performance Comparison(MHz)

Read command	Dummy Cycles (VCC=1.65V~3.6V)				Dummy Cycles (VCC=2.7V~3.6V)			
	4	6	8	10	4	6	8	10
FREAD	50	60	70	85 (default)	60	85	104	120 (default)
4READ	50	60	70	85 (default)	60	85	104	120 (default)
BURST READ	50	60	70	85 (default)	60	85	104	120 (default)
RDSFDP	50	60	70	85 (default)	60	85	104	120 (default)

5.4 AC Characteristics for Program and Erase

Table 5-4 AC parameters for program and erase(Ta=-40°C ~ +85°C)

Symbol	Parameter	1.65V~3.6V			Units
		Min	Typ	Max	
$T_{ESL(6)}$	Erase Suspend Latency			30	us
$T_{PSL(6)}$	Program Suspend Latency			30	us
$T_{PRS(4)}$	Latency between Program Resume and next Suspend	20			us
$T_{ERS(5)}$	Latency between Erase Resume and next Suspend	20			us
t_{PP}	Page program time (up to 256 bytes)		2	3	ms
t_{PE}	Page erase time		16	30	ms
t_{SE}	Sector erase time		16	30	ms
t_{BE1}	Block erase time for 32K bytes		16	30	ms
t_{BE2}	Block erase time for 64K bytes		16	30	ms
t_{CE}	Chip erase time		16	30	ms

Note

1. tCH + tCL must be greater than or equal to 1/ Frequency.
2. Typical values given for TA=25°C& VCC = 3.0V. Not 100% tested.
3. Only applicable as a constraint for a WRSR instruction.
4. Program operation may be interrupted as often as system request. The minimum timing of tPRS must be observed before issuing the next program suspend command. However, in order for a Program operation to make progress, tPRS ≥ 100us must be included in resume-to-suspend loop(s). Not 100% tested.
5. Erase operation may be interrupted as often as system request. The minimum timing of tERS must be observed before issuing the next erase suspend command. However, in order for an Erase operation to make progress, tERS ≥ 100us must be included in resume-to-suspend loop(s). Notes. Not 100% tested.
6. Latency time is required to complete Erase/Program Suspend operation.
7. The value guaranteed by characterization, not 100% tested in production.

Figure 5-4 Serial Input Timing

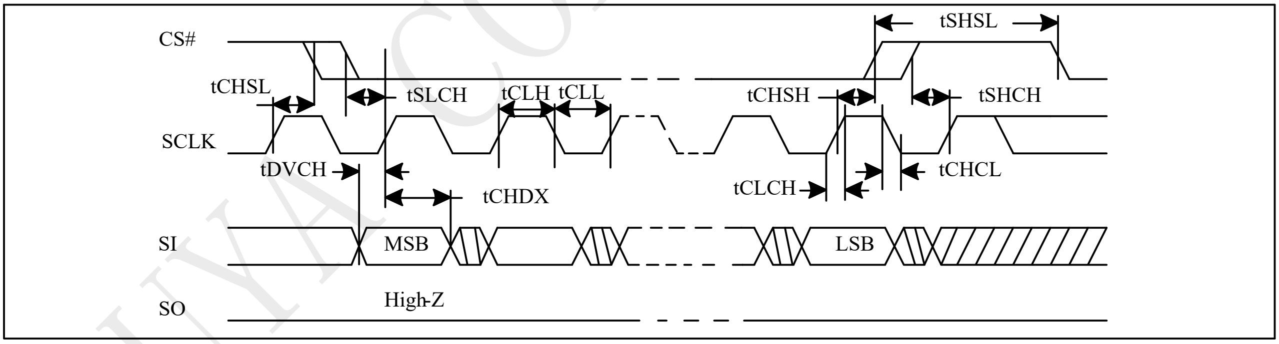


Figure 5-5 Output Timing

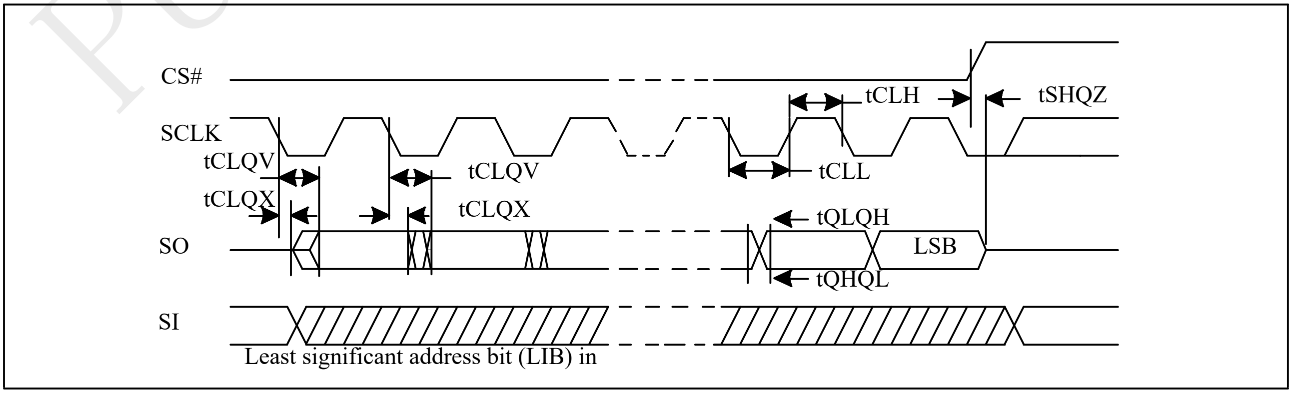


Figure 5-6 Hold Timing

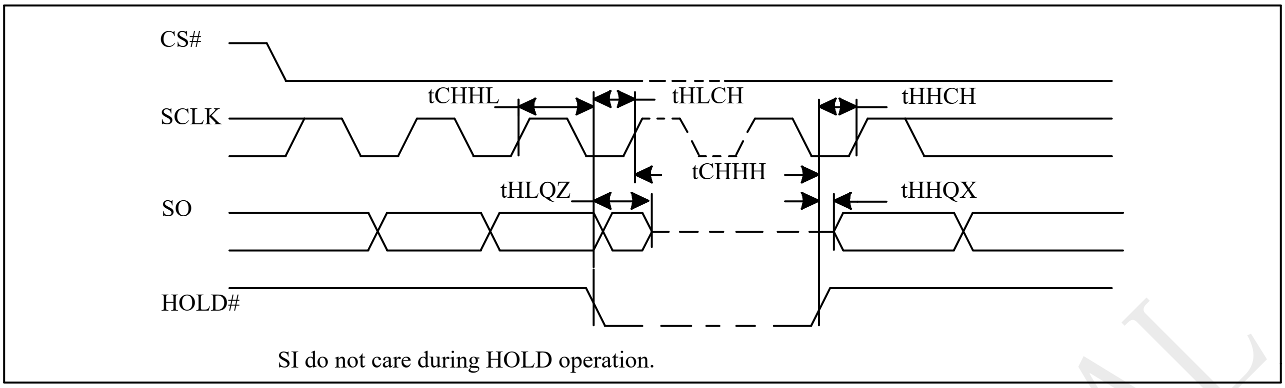
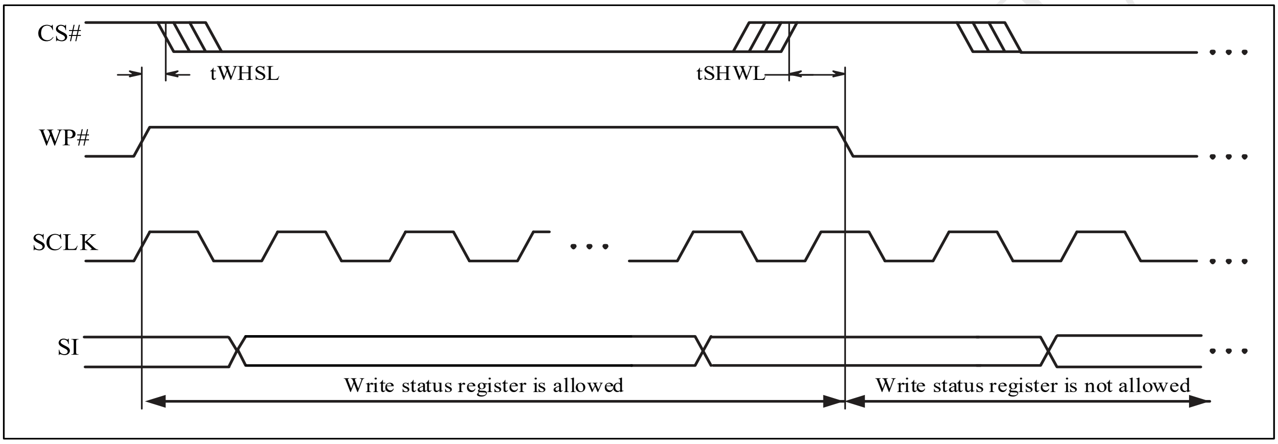


Figure 5-7 WP Timing



5.5 Operation Conditions

At Device Power-Up and Power-Down

AC timing illustrated in "Figure AC Timing at Device Power-Up" and "Figure Power-Down Sequence" are for the supply voltages and the control signals at device power-up and power-down. If the timing in the figures is ignored, the device will not operate correctly.

During power-up and power-down, CS# needs to follow the voltage applied on VCC to keep the device not to be selected. The CS# can be driven low when VCC reach Vcc(min.) and wait a period of tVSL.

Figure 5-8 AC Timing at Device Power-Up

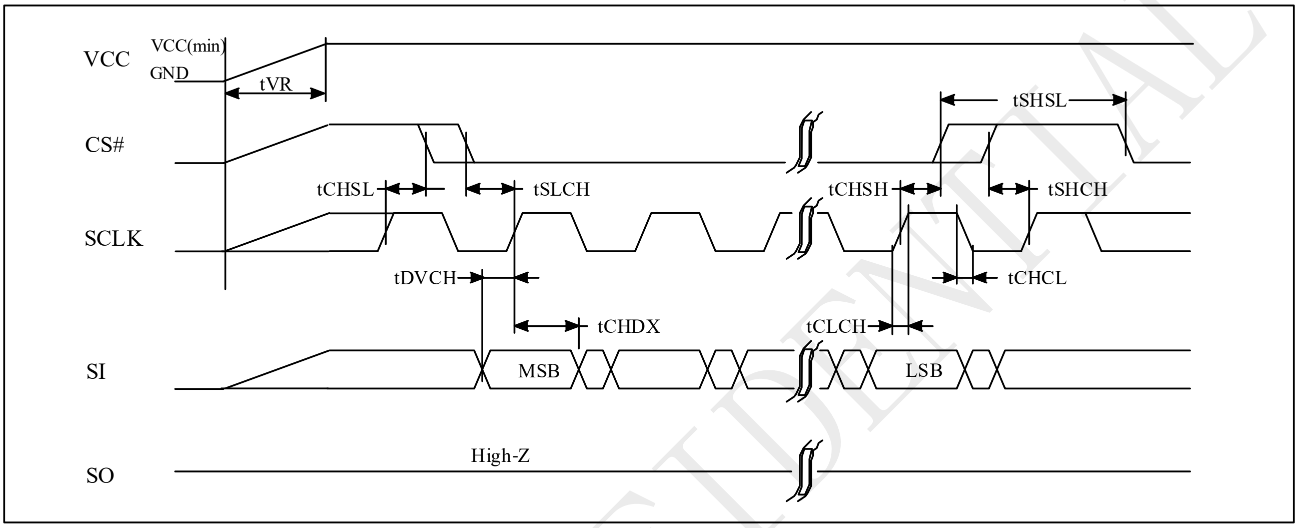
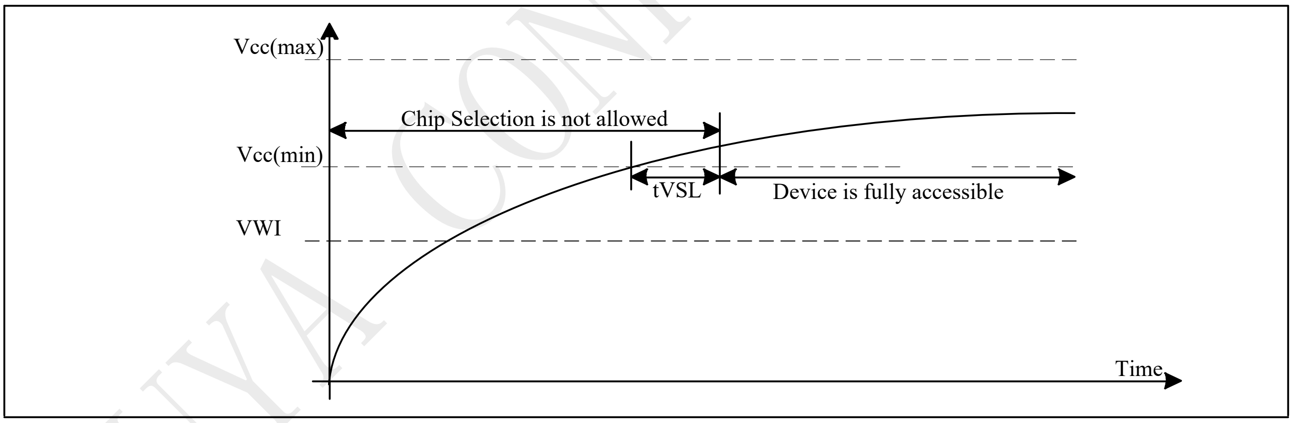


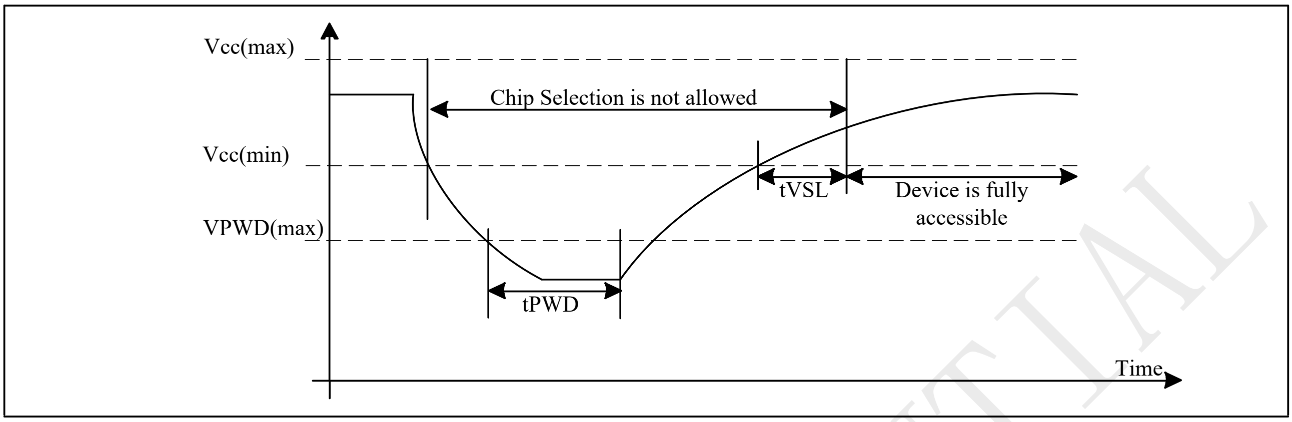
Figure 5-9 Power-up Timing



Power Up/Down and Voltage Drop

For Power-down to Power-up operation, the VCC of flash device must below VPWD for at least tPWD timing. Please check the table below for more detail.

Figure 5-10 Power down-up Timing



Symbol	Parameter	Min	Max	Units
VPWD	VCC voltage needed to below VPWD for ensuring initialization will occur		1	V
tPWD	The minimum duration for ensuring initialization will occur	300		us
tVSL	VCC(min.) to device operation	300		us
tVR	VCC Rise Time	1	500000	us/V
VWI	Write Inhibit Voltage	1.45	1.55	V

Initial Delivery State

The device is delivered with the memory array erased: all bits are set to 1 (each byte contains FFh). The Status Register contains 00h (all Status Register bits are 0).

6 Data Protection

During power transition, there may be some false system level signals which result in inadvertent erasure or programming. The device is designed to protect itself from these accidental write cycles.

The state machine will be reset as standby mode automatically during power up. In addition, the control register architecture of the device constrains that the memory contents can only be changed after specific command sequences have completed successfully.

In the following, there are several features to protect the system from the accidental write cycles during VCC power-up and power-down or from system noise.

- Power-on reset: to avoid sudden power switch by system power supply transition, the power-on reset may protect the Flash.
- Valid command length checking: The command length will be checked whether it is at byte base and completed on byte boundary.
- Write Enable (WREN) command: WREN command is required to set the Write Enable Latch bit (WEL) before issuing other commands to change data.
- Software Protection Mode: The Block Protect (BP4, BP3, BP2, BP1, and BP0) bits define the section of the memory array that can be read but not change.
- Hardware Protection Mode: WP# going low to protected the BP0~BP4bits and SRP0~1bits
- Deep Power-Down Mode: By entering deep power down mode, the flash device is under protected from writing all commands except the Release from Deep Power-Down Mode command.

Protected Area Sizes

Table 6-1. P25Q40TU Protected Area Sizes (CMP bit = 0)

Status bit					Memory Content			
BP4	**BP3**	**BP2**	**BP1**	**BP0**	**Blocks**	**Addresses**	**Density**	**Portion**
x	x	0	0	0	NONE	NONE	NONE	NONE
0	0	0	0	1	7	070000H-07FFFFH	64KB	Upper 1/8
0	0	0	1	0	6 and 7	060000H-07FFFFH	128KB	Upper 1/4
0	0	0	1	1	4 to 7	040000H-07FFFFH	256KB	Upper 1/2
0	1	0	0	1	0	000000H-00FFFFH	64KB	Lower 1/8
0	1	0	1	0	0 and 1	000000H-01FFFFH	128KB	Lower 1/4
0	1	0	1	1	0 to 3	000000H-03FFFFH	256KB	Lower 1/2
0	x	1	x	x	0 to 7	000000H-07FFFFH	512KB	ALL
1	0	0	0	1	7	07F000H-07FFFFH	4KB	Upper 1/128
1	0	0	1	0	7	07E000H-07FFFFH	8KB	Upper 1/64
1	0	0	1	1	7	07C000H-07FFFFH	16KB	Upper 1/32
1	0	1	0	x	7	078000H- 07FFFFH	32KB	Upper 1/16
1	0	1	1	0	7	078000H-07FFFFH	32KB	Upper 1/16
1	1	0	0	1	0	000000H-000FFFH	4KB	Lower 1/128
1	1	0	1	0	0	000000H-001FFFH	8KB	Lower 1/64
1	1	0	1	1	0	000000H-003FFFH	16KB	Lower 1/32
1	1	1	0	x	0	000000H-007FFFH	32KB	Lower 1/16
1	1	1	1	0	0	000000H-007FFFH	32KB	Lower 1/16
1	x	1	1	1	0 to 7	000000H-07FFFFH	512KB	ALL

Table 6-2. P25Q40TU Protected Area Sizes (CMP bit = 1)

Status bit					Memory Content			
BP4	BP3	BP2	BP1	BP0	Blocks	Addresses	Density	Portion
x	x	0	0	0	0 to 7	000000H-07FFFFH	512KB	ALL
0	0	0	0	1	0 to 6	000000H-06FFFFH	448KB	Lower 7/8
0	0	0	1	0	0 to 5	000000H-05FFFFH	384KB	Lower 3/4
0	0	0	1	1	0 to 3	000000H-03FFFFH	256KB	Lower 1/2
0	1	0	0	1	1 to 7	010000H-07FFFFH	448KB	Upper 7/8
0	1	0	1	0	2 to 7	020000H-07FFFFH	384KB	Upper 3/4
0	1	0	1	1	4 to 7	040000H-07FFFFH	256KB	Upper 1/2
0	x	1	x	x	NONE	NONE	NONE	NONE
1	0	0	0	1	0 to 7	000000H-07EFFFH	508KB	Lower 127/128
1	0	0	1	0	0 to 7	000000H-07DFFFH	504KB	Lower 63/64
1	0	0	1	1	0 to 7	000000H-07BFFFH	496KB	Lower 31/32
1	0	1	0	x	0 to 7	000000H-077FFFH	480KB	Lower 15/16
1	0	1	1	0	0 to 7	000000H-077FFFH	480KB	Lower 15/16
1	1	0	0	1	0 to 7	001000-07FFFFH	508KB	Upper 127/128
1	1	0	1	0	0 to 7	002000-07FFFFH	504KB	Upper 63/64
1	1	0	1	1	0 to 7	004000-07FFFFH	496KB	Upper 31/32
1	1	1	0	x	0 to 7	008000-07FFFFH	480KB	Upper 15/16
1	1	1	1	0	0 to 7	008000-07FFFFH	480KB	Upper 15/16
1	x	1	1	1	NONE	NONE	NONE	NONE

Table 6-3. P25Q20TU Protection Area Sizes (CMP bit=0)

Status bit					Memory Content			
BP4	BP3	BP2	BP1	BP0	Blocks	Addresses	Density	Portion
0	x	x	0	0	NONE	NONE	NONE	NONE
0	0	x	0	1	3	030000H-03FFFFH	64KB	Upper 1/4
0	0	x	1	0	2 and 3	020000H-03FFFFH	128KB	Upper 1/2
0	1	x	0	1	0	000000H-00FFFFH	64KB	Lower 1/4
0	1	x	1	0	0 and 1	000000H-01FFFFH	128KB	Lower 1/2
0	x	x	1	1	0 to 3	000000H-03FFFFH	256KB	ALL
1	x	0	0	0	NONE	NONE	NONE	NONE
1	0	0	0	1	3	03F000H-03FFFFH	4KB	Upper 1/64
1	0	0	1	0	3	03E000H-03FFFFH	8KB	Upper 1/32
1	0	0	1	1	3	03C000H-03FFFFH	16KB	Upper 1/16
1	0	1	0	x	3	038000H-03FFFFH	32KB	Upper 1/8
1	0	1	1	0	3	038000H-03FFFFH	32KB	Upper 1/8
1	1	0	0	1	0	000000H-000FFFH	4KB	Lower 1/64
1	1	0	1	0	0	000000H-001FFFH	8KB	Lower 1/32
1	1	0	1	1	0	000000H-003FFFH	16KB	Lower 1/16
1	1	1	0	x	0	000000H-007FFFH	32KB	Lower 1/8
1	1	1	1	0	0	000000H-007FFFH	32KB	Lower 1/8
1	x	1	1	1	0 to 3	000000H-03FFFFH	256KB	ALL

Table 6-4. P25Q20TU Protection Area Sizes (CMP bit=1)

Status bit					Memory Content			
BP4	BP3	BP2	BP1	BP0	Blocks	Addresses	Density	Portion
0	x	x	0	0	0 to 3	000000H-03FFFFH	256KB	ALL
0	0	x	0	1	0 to 2	000000H-02FFFFH	192KB	Lower 3/4
0	0	x	1	0	0 and 1	000000H-01FFFFH	128KB	Lower 1/2
0	1	x	0	1	1 to 3	010000H-03FFFFH	192KB	Upper 3/4
0	1	x	1	0	2 and 3	020000H-03FFFFH	128KB	Upper 1/2
0	x	x	1	1	NONE	NONE	NONE	NONE
1	x	0	0	0	0 to 3	000000H-03FFFFH	256KB	ALL
1	0	0	0	1	0 to 3	000000H-03EFFFH	252KB	Lower 63/64
1	0	0	1	0	0 to 3	000000H-03DFFFH	248KB	Lower 31/32
1	0	0	1	1	0 to 3	000000H-03BFFFH	240KB	Lower 15/16
1	0	1	0	x	0 to 3	000000H-037FFFH	224KB	Lower 7/8
1	0	1	1	0	0 to 3	000000H-037FFFH	224KB	Lower 7/8
1	1	0	0	1	0 to 3	001000-03FFFFH	252KB	Upper 63/64
1	1	0	1	0	0 to 3	002000-03FFFFH	248KB	Upper 31/32
1	1	0	1	1	0 to 3	004000-03FFFFH	240KB	Upper 15/16
1	1	1	0	x	0 to 3	008000-03FFFFH	224KB	Upper 7/8
1	1	1	1	0	0 to 3	008000-03FFFFH	224KB	Upper 7/8
1	x	1	1	1	NONE	NONE	NONE	NONE

Note:

1. X=don’t care

2. If any erase or program command specifies a memory that contains protected data portion, this command will be ignored.

7 Memory Address Mapping

The memory array can be erased in three levels of granularity including a full chip erase. The size of the erase blocks is optimized for both code and data storage applications, allowing both code and data segments to reside in their own erase regions.

Each device has	Each block has	Each sector has	Each page has	
512K	64/32K	4K	256	bytes
2K	256/128	16	-	pages
127	16/8	-	-	sectors
8/16	-	-	-	blocks

P25Q40TU Memory Organization

Block 64K	Block 32K	Sector	Address Range	
7	15 ~ 14	127	07_F000H	07_FFFFH
		……	……	……
		112	07_0000H	07_0FFFH
6	13 ~ 12	111	06_F000H	06_FFFFH
		……	……	……
		96	06_0000H	06_0FFFH
……	……	……	……	……
		……	……	……
		……	……	……
……	……	……	……	……
		……	……	……
		……	……	……
1	3 ~ 2	31	01_F000H	01_FFFFH
		……	……	……
		16	01_0000H	01_0FFFH
0	1 ~ 0	15	00_F000H	00_FFFFH
		……	……	……
		0	00_0000H	00_0FFFH

P25Q20TU Memory Organization

Block 64K	Block 32K	Sector	Address Range	
3	7 ~ 6	63	03_F000H	03_FFFFH
		……	……	……
		48	03_0000H	03_0FFFH
2	5 ~ 4	47	02_F000H	02_FFFFH
		……	……	……
		32	02_0000H	02_0FFFH
1	3 ~ 2	31	01_F000H	01_FFFFH
		……	……	……
		16	01_0000H	01_0FFFH
0	1 ~ 0	15	00_F000H	00_FFFFH
		……	……	……
		0	00_0000H	00_0FFFH

8 Device Operation

Before a command is issued, status register should be checked to ensure device is ready for the intended operation.

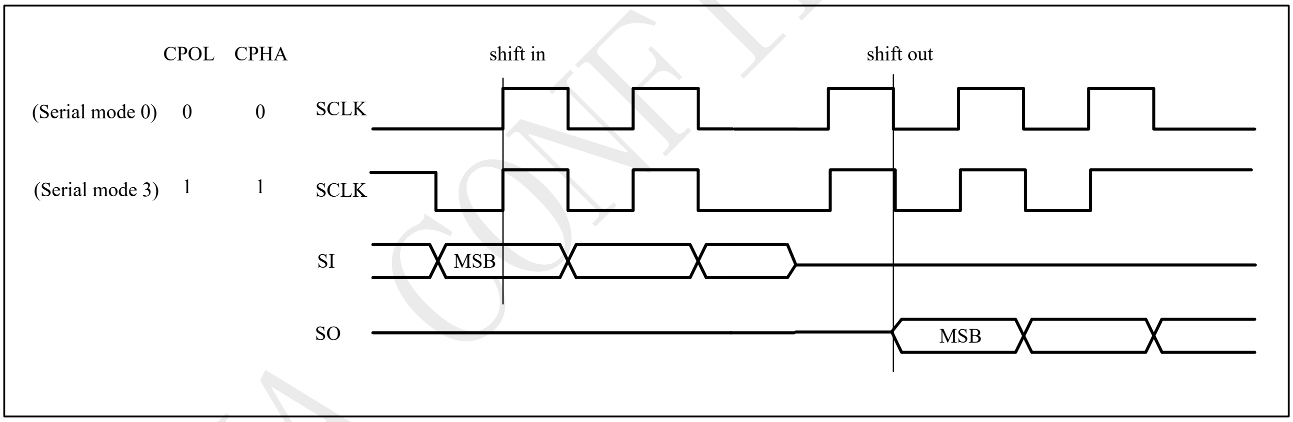
When incorrect command is inputted to this LSI, this LSI becomes standby mode and keeps the standby mode until next CS# falling edge. In standby mode, SO pin of this LSI should be High-Z. When correct command is inputted to this LSI, this LSI becomes active mode and keeps the active mode until next CS# rising edge.

Input data is latched on the rising edge of Serial Clock (SCLK) and data shifts out on the falling edge of SCLK. The difference of serial peripheral interface mode 0 and mode 3 is shown as Figure 8-1.

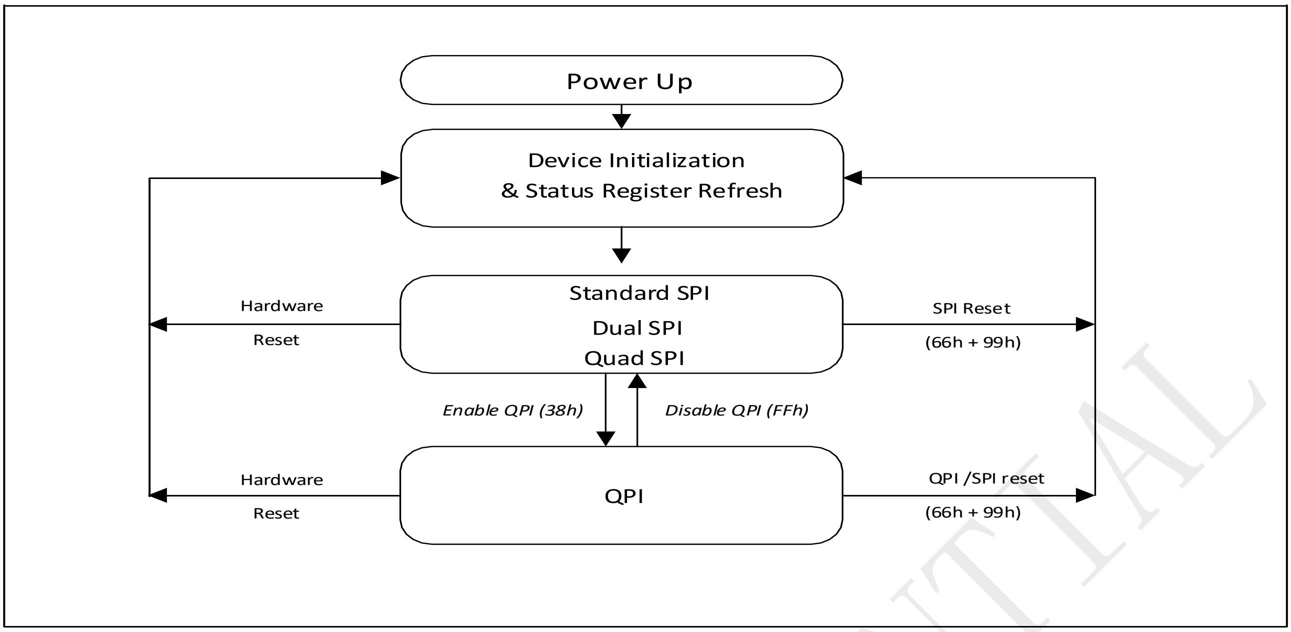
For the following instructions: RDID, RDSR, RDSR1, RDSCUR, READ, FREAD, DREAD, 2READ, 4READ, QREAD, RDSFDP, RES, REMS, DREMS, QREMS, the shifted-in instruction sequence is followed by a data-out sequence. After any bit of data being shifted out, the CS# can be high. For the following instructions: WREN, WRDI, WRSR, PE, SE, BE32K, BE, CE, PP, QPP, DP, ERSCUR, PRSCUR, SUSPEND, RESUME, RSTEN, RST, the CS# must go high exactly at the byte boundary; otherwise, the instruction will be rejected and not executed.

During the progress of Write Status Register, Program, Erase operation, to access the memory array is neglected and not affect the current operation of Write Status Register, Program, Erase.

Figure 8-1 Serial Peripheral Interface Modes Supported



Note: CPOL indicates clock polarity of serial master, CPOL=1 for SCLK high while idle, CPOL=0 for SCLK low while not transmitting. CPHA indicates clock phase. The combination of CPOL bit and CPHA bit decides which serial mode is supported.



Standard SPI

The P25Q40TU features a serial peripheral interface on 4 signals bus: Serial Clock (SCLK), Chip Select (CS#), Serial Data Input (SI) and Serial Data Output (SO). Both SPI bus mode 0 and 3 are supported. Input data is latched on the rising edge of SCLK and data shifts out on the falling edge of SCLK.

Dual SPI

The P25Q40TU supports Dual SPI operation when using the “Dual Output Fast Read” and “Dual I/O Fast Read” (3BHand BBH) commands. These commands allow data to be transferred to or from the device at two times the rate of the standard SPI. When using the Dual SPI command the SI and SO pins become bidirectional I/O pins: IO0 and IO1.

Quad SPI

The P25Q40TU supports Quad SPI operation when using the “Quad Output Fast Read”,” Quad I/O Fast Read” (6BH, EBH) commands. These commands allow data to be transferred to or from the device at four times the rate of the standard SPI. When using the Quad SPI command the SI and SO pins become bidirectional I/O pins: IO0 and IO1, and WP# and HOLD# pins become IO2 andIO3. Quad SPI commands require the non-volatile Quad Enable bit(QE) in Status Register to be set.

QPI

The P25Q40TU supports Quad Peripheral Interface (QPI) operations only when the device is switched from Standard/Dual/Quad SPI mode to QPI mode using the “Enable the QPI (38H)” command. The QPI mode utilizes all four IO pins to input the command code. Standard/Dual/Quad SPI mode and QPI mode are exclusive. Only one mode can be active at any given times. “Enable the QPI(38H)”and “Disable the QPI(FFH)” commands are used to switch between these two modes. Upon power-up and after software reset (66H) using “Reset (99H)” command, the default state of the device is Standard/Dual/Quad SPI mode. The QPI mode requires the non-volatile Quad Enable bit (QE) in Status Register to be set.

Software Reset

The P25Q40TU can be reset to the initial power-on state by a software Reset sequence, either in SPI mode or QPI mode. This sequence must include two consecutive commands: Enable Reset (66h) & Reset (99h). If the command sequence is successfully accepted, the device will take approximately 50uS (tReady) to reset. No command will be accepted during the reset period.

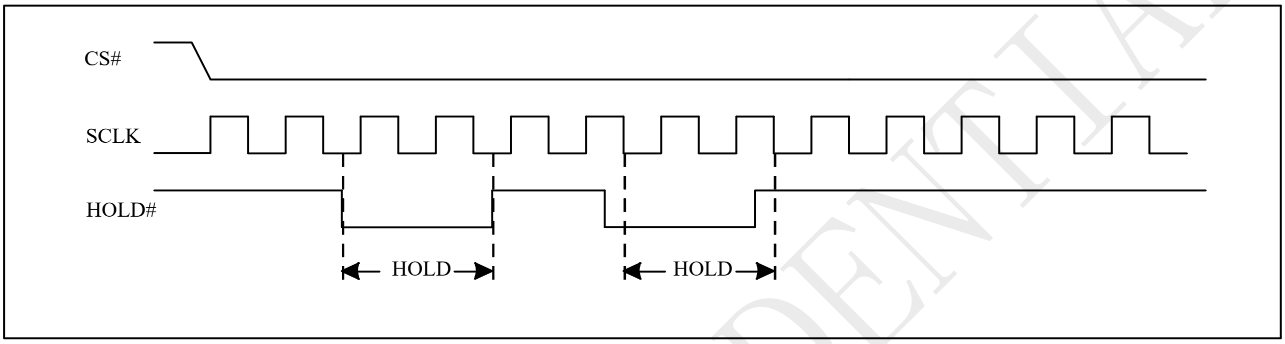
If QE bit is set to 1, the HOLD or RESET function will be disabled, the pin will become one of the four data I/O pins.

9 Hold Feature

HOLD# pin signal goes low to hold any serial communications with the device. The HOLD feature will not stop the operation of write status register, programming, or erasing in progress.

The operation of HOLD requires Chip Select(CS#) keeping low and starts on falling edge of HOLD# pin signal while Serial Clock (SCLK) signal is being low (if Serial Clock signal is not being low, HOLD operation will not start until Serial Clock signal being low). The HOLD condition ends on the rising edge of HOLD# pin signal while Serial Clock(SCLK) signal is being low (if Serial Clock signal is not being low, HOLD operation will not end until Serial Clock being low).

Figure 9-1 Hold Condition Operation



During the HOLD operation, the Serial Data Output (SO) is high impedance when Hold# pin goes low and will keep high impedance until Hold# pin goes high. The Serial Data Input (SI) is don't care if both Serial Clock (SCLK) and Hold# pin goes low and will keep the state until SCLK goes low and Hold# pin goes high. If Chip Select (CS#) drives high during HOLD operation, it will reset the internal logic of the device. To re-start communication with chip, the HOLD# must be at high and CS# must be at low.
Note: The HOLD feature is disabled during Quad I/O mode.

10 Commands

10.1 Commands listing

Figure 10-1 Command set (STR Standard/Dual/Quad SPI instruction)

Commands	Abbr.	Code	ADR Bytes	DMY Cycles	Data Bytes	Function description
Read						
Read Array (fast)	FREAD	0Bh	3	8	1+	n bytes read out until CS# goes high
Read Array (low power)	READ	03h	3	0	1+	n bytes read out until CS# goes high
Read Dual Output	DREAD	3Bh	3	8	1+	n bytes read out by Dual output
Read 2IO	2READ	BBh	3	4/8	1+	n bytes read out by 2IO
Read Quad Output	QREAD	6Bh	3	8	1+	n bytes read out by Quad output
Read 4IO	4READ	EBh	3	6(10)	1+	n bytes read out by 4IO
Read Word 4IO	WREAD	E7h	3	4	1+	n bytes word read out by 4IO
Program and Erase						
Page Erase	PE	81h	3	0	0	erase selected page
Sector Erase (4K bytes)	SE	20h	3	0	0	erase selected sector
Block Erase (32K bytes)	BE32	52h	3	0	0	erase selected 32K block
Block Erase (64K bytes)	BE	D8h	3	0	0	erase selected 64K block
Chip Erase	CE	60h/C7h	0	0	0	erase whole chip
Page Program	PP	02h	3	0	1+	program selected page
Quad page program	QPP	32h	3	0	1+	quad input to program selected page
Program/Erase Suspend	PES	75h	0	0	0	suspend program/erase operation
Program/Erase Resume	PER	7Ah	0	0	0	continue program/erase operation
Protection						
Write Enable	WREN	06h	0	0	0	sets the write enable latch bit
Write Disable	WRDI	04h	0	0	0	resets the write enable latch bit
Volatile SR Write Enable	VWREN	50h	0	0	0	Write enable for volatile SR
Security						
Erase Security Registers	ERSCUR	44h	3	0	0	Erase security registers
Program Security Registers	PRSCUR	42h	3	0	1+	Program security registers
Read Security Registers	RDSCUR	48h	3	8	1+	Read value of security register

Command set (Standard/Dual/Quad SPI) Cont'd

Commands	Abbr.	Code	ADR Bytes	DMY Cycles	Data Bytes	Function
Status Register						
Read Status Register	RDSR	05h	0	0	1	read out status register
Read Status Register-1	RDSR1	35h	0	0	1	Read out status register-1
Read Configure Register	RDCR	15h	0	0	1	Read out configure register
Write Status Register	WRSR	01h	0	0	1/2	Write data to status registers
Write Status Register-1	WRSR1	31h	0	0	1	Write data to status registers-1
Write Configure Register	WRCR	11h	0	0	1	Write data to configuration register
Other Commands						
Reset Enable	RSTEN	66h	0	0	0	Enable reset
Reset	RST	99h	0	0	0	Reset
Enable QPI	QPIEN	38h	0	0	0	Enable QPI mode
Read Manufacturer/device ID	RDID	9Fh	0	0	1 to 3	output JEDEC ID: 1-byte manufacturer ID & 2-byte device ID
Read Manufacture ID	REMS	90h	3	0	1+	Read manufacturer ID/device ID data
Dual Read Manufacture ID	DREMS	92h	3	4	1+	Dual output read manufacture/device ID
Quad Read Manufacture ID	QREMS	94h	3	8	1+	Quad output read manufacture/device ID
Deep Power-down	DP	B9h	0	0	0	enters deep power-down mode
Release Deep Power-down / Read Electronic ID	RDP/RES	ABh	3	0	1	Read electronic ID data
Set burst length	SBL	77h	0	0	0	Set burst length
Read SFDP	RDSFDP	5Ah	3	8	1+	Read SFDP parameter
Release read enhanced		FFh	0	0	0	Release from read enhanced
Read unique ID	RUID	4Bh	3	8	1+	Read unique ID

Command set(STR QPI Instructions)

Commands	Abbr.	Code	ADR Bytes	DMY Cycles	Data Bytes	Function description
Read						
Fast read	FREAD	0Bh	3	10/4/6/8	1+	n bytes read out until CS# goes high
Burst Read with Wrap		0Ch	3	10/4/6/8	1+	n bytes burst read with wrap by 4IO
Read Word 4x I/O	4READ	EBh	3	10/4/6/8	1+	n bytes read out by 4IO
Program and Erase						
Page Program	PP	02h	3	0	1+	program selected page
Page Erase	PE	81h	3	0	0	erase selected page
Sector Erase (4K bytes)	SE	20h	3	0	0	erase selected sector
Block Erase (32K bytes)	BE32	52h	3	0	0	erase selected 32K block
Block Erase (64K bytes)	BE	D8h	3	0	0	erase selected 64K block
Chip Erase	CE	60h/C7h	0	0	0	erase whole chip
Program/Erase Suspend	PES	75h	0	0	0	suspend program/erase operation
Program/Erase Resume	PER	7Ah	0	0	0	continue program/erase operation
Protection						
Write Enable	WREN	06h	0	0	0	sets the write enable latch bit
Volatile SR Write Enable	VWREN	50h	0	0	0	Write enable for volatile status

Commands	Abbr.	Code	ADR Bytes	DMY Cycles	Data Bytes	Function description
						register
Write Disable	WRDI	04h	0	0	0	resets the write enable latch bit
Status Register						
Read Status Register	RDSR	05h	0	0	1	read out status register
Read Status Register-1	RDSR1	35h	0	0	1	Read out status register-1
Read Configure Register	RDCR	15h	0	0	1	Read out configure register
Write Status Register	WRSR	01h	0	0	1/2	Write data to status registers
Write Status Register-1	WRSR1	31h	0	0	1	Write data to status registers-1
Write Configure Register	WRCR	11h	0	0	1	Write data to configuration register
Other Command						
Deep Power-down	DP	B9h	0	0	0	enters deep power-down mode
Release Deep Power-down/Read Electronic ID	RDP/RES	ABh	3	0	1	Read electronic ID data
Set Read Parameters		C0h	0	0	1	Set read dummy and wrap
Read Manufacture ID	REMS	90h	3	0	1+	Read manufacturer ID/device ID data
Read Manufacturer/device ID	RDID	9Fh	0	0	1 to 3	output JEDEC ID: 1-byte manufacturer ID & 2-byte device ID
Read SFDP	RDSFDP	5Ah	3	10/4/6/8	1+	Read SFDP parameter
Disable QPI		FFh	0	0	0	Release from read enhanced
Reset Enable	RSTEN	66h	0	0	0	Enable reset
Reset	RST	99h	0	0	0	Reset

NOTE:

1. Dual Output data
IO0 = (D6, D4, D2, D0)
IO1 = (D7, D5, D3, D1)

2. Dual Input Address
IO0 = A22, A20, A18, A16, A14, A12, A10, A8 A6, A4, A2, A0, M6, M4, M2, M0
IO1 = A23, A21, A19, A17, A15, A13, A11, A9 A7, A5, A3, A1, M7, M5, M3, M1

3. Quad Output Data
IO0 = (D4, D0, …..)
IO1 = (D5, D1, …..)
IO2 = (D6, D2, …..)
IO3 = (D7, D3,…..)

4. Quad Input Address
IO0 = A20, A16, A12, A8, A4, A0, M4, M0
IO1 = A21, A17, A13, A9, A5, A1, M5, M1
IO2 = A22, A18, A14, A10, A6, A2, M6, M2
IO3 = A23, A19, A15, A11, A7, A3, M7, M3

5. Fast Read Quad I/O Data
IO0 = (x, x, x, x, D4, D0,…)
IO1 = (x, x, x, x, D5, D1,…)
IO2 = (x, x, x, x, D6, D2,…)
IO3 = (x, x, x, x, D7, D3,…)

6. Fast Word Read Quad I/O Data
IO0 = (x, x, D4, D0,…)
IO1 = (x, x, D5, D1,…)
IO2 = (x, x, D6, D2,…)
IO3 = (x, x, D7, D3,…)

7. Fast Word Read Quad I/O Data: the lowest address bit must be 0.

8. QPI Command, Address, Data input/output format:
CLK #0 1 2 3 4 5 6 7 8 9 10 11
IO0= C4, C0, A20, A16, A12, A8, A4, A0, D4, D0, D4, D0,
IO1= C5, C1, A21, A17, A13, A9, A5, A1, D5, D1, D5, D1
IO2= C6, C2, A22, A18, A14, A10, A6, A2, D6, D2, D6, D2
IO3= C7, C3, A23, A19, A15, A11, A7, A3, D7, D3, D7, D3

9. Security Registers Address:
Security Register1: A23-A16=00H, A15-A12=0001,A11-A9=000, A8-A0= Byte Address;
Security Register2: A23-A16=00H, A15-A12=0010,A11-A9=000, A8-A0= Byte Address;
Security Register3: A23-A16=00H, A15-A12=0011, A11-A9=000, A8-A0= Byte Address;

10.2 Write Enable (WREN)

The Write Enable (WREN) instruction is for setting Write Enable Latch (WEL) bit. For those instructions like PP, QPP, PE, SE, BE32K, BE, CE, BFPP and WRSR, WRCR, ERSCUR, PRSCUR which are intended to change the device content, should be set every time after the WREN instruction setting the WEL bit.

The sequence of issuing WREN instruction is: CS# goes low→ sending WREN instruction code→ CS# goes high.

Figure 10-2 Write Enable (WREN) Sequence (Command 06)

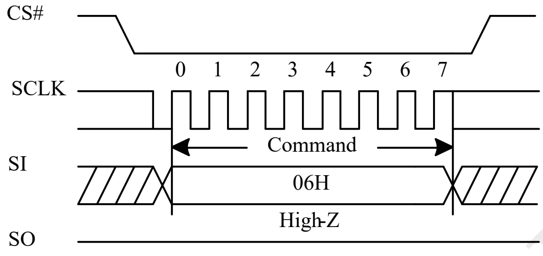
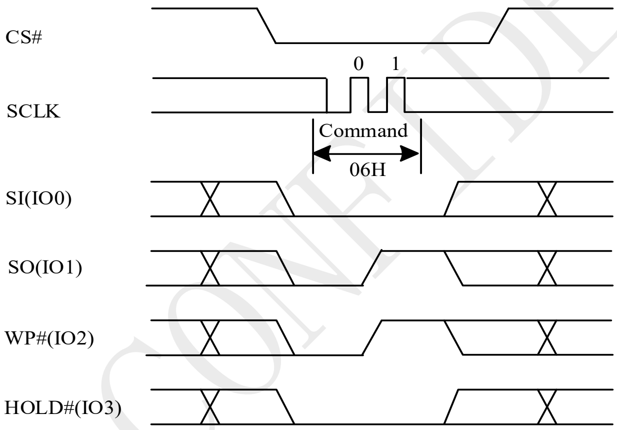


Figure 10-2a Write Enable (WREN) Sequence (QPI)



10.3 Write Disable (WRDI)

The Write Disable (WRDI) instruction is for resetting Write Enable Latch (WEL) bit.

The sequence of issuing WRDI instruction is: CS# goes low→ sending WRDI instruction code→ CS# goes high.

The WEL bit is reset by following situations:
- Power-up
- Write Disable (WRDI) instruction completion
- Write Status Register (WRSR/WRCR) instruction completion
- Page Program (PP) instruction completion
- Quod Page Program (QPP) instruction completion
- Page Erase (PE) instruction completion
- Sector Erase (SE) instruction completion
- Block Erase (BE32K, BE) instruction completion
- Chip Erase (CE) instruction completion
- Erase Security Register (ERSCUR) instruction completion
- Program Security Register (PRSCUR) instruction completion
- Reset (RST) instruction completion

Figure 10-3 Write Disable (WRDI) Sequence (Command 04)

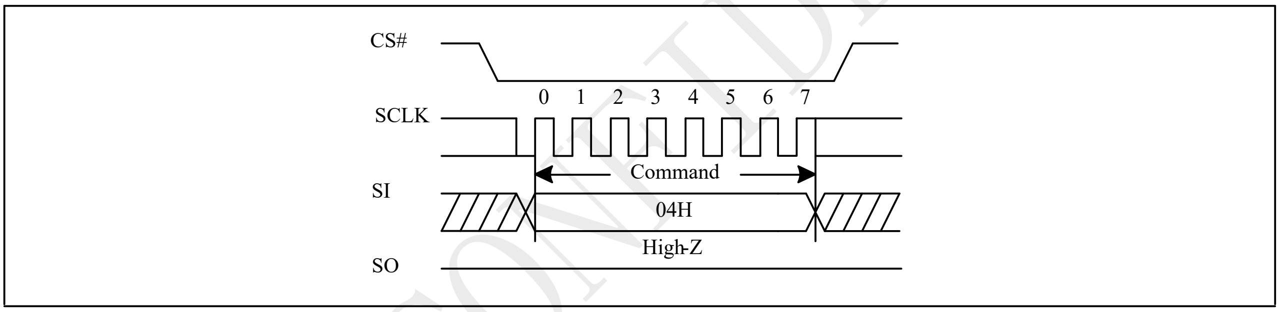
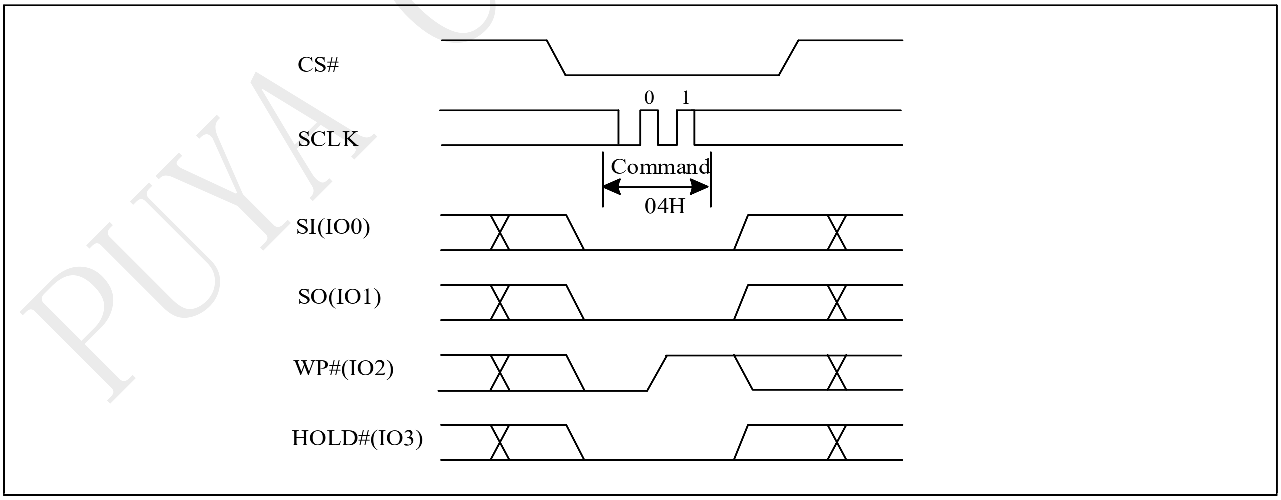


Figure 10-3a Write Disable (WRDI) Sequence (QPI)



10.4 Write Enable for Volatile Status Register

The non-volatile Status Register bits can also be written to as volatile bits. This gives more flexibility to change the system configuration and memory protection schemes quickly without waiting for the typical non-volatile bit write cycles or affecting the endurance of the Status Register non-volatile bits. The Write Enable for Volatile Status Register command must be issued prior to a Write Status Register command. The Write Enable for Volatile Status Register command will not set the Write Enable Latch bit, it is only valid for the Write Status Register command to change the volatile Status Register bit values.

The sequence of issuing Write Enable for Volatile Status Register instruction is: CS# goes low→ sending Write Enable for Volatile Status Register instruction code→ CS# goes high.

Figure 10-4 Write Enable for Volatile Status Register Sequence (Command 50)

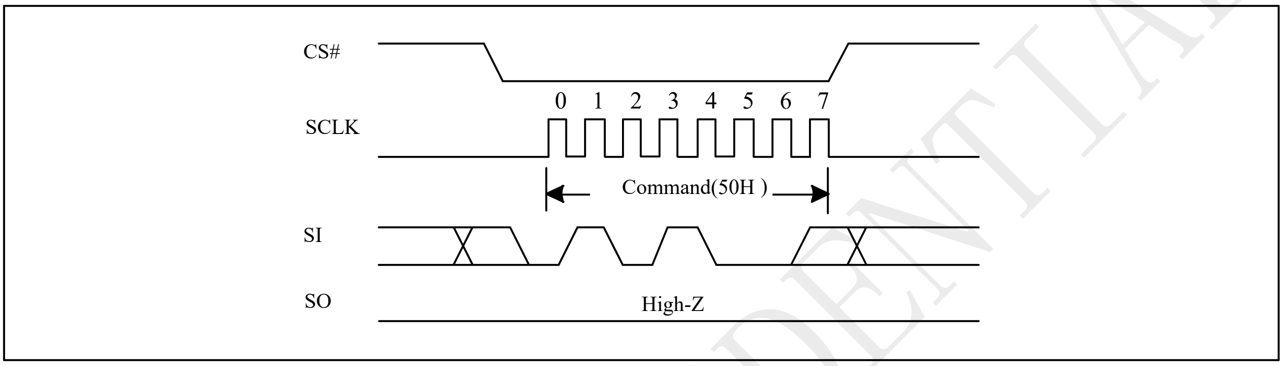
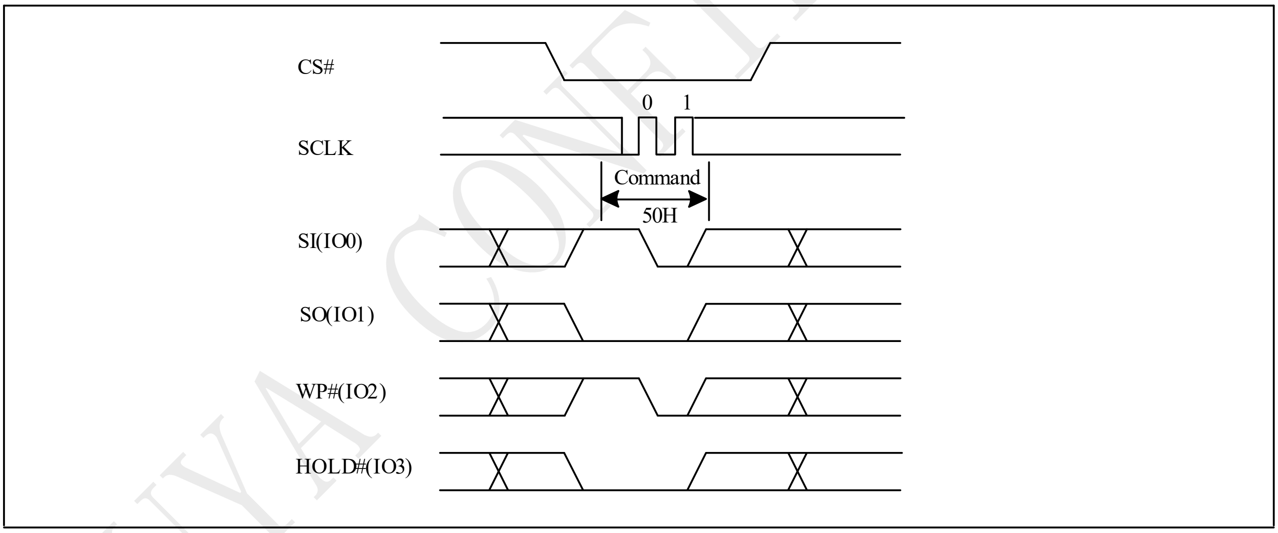


Figure 10-4a Write Enable for Volatile Status Register Sequence (QPI)



10.5 Read Status Register (RDSR)

The RDSR instruction is for reading Status Register Bits. The Read Status Register can be read at any time (even in program/erase/write status register condition). It is recommended to check the Write in Progress (WIP) bit before sending a new instruction when a program, erase, or write status register operation is in progress. For command code “05H”, the SO will output Status Register bits S7~S0. The command code “35H”, the SO will output Status Register bits S15~S8.

The sequence of issuing RDSR instruction is: CS# goes low→ sending RDSR instruction code→ Status Register data out on SO. The SIO[3:1] are "don't care".

Figure 10-5 Read Status Register (RDSR) Sequence (Command 05 or 35)

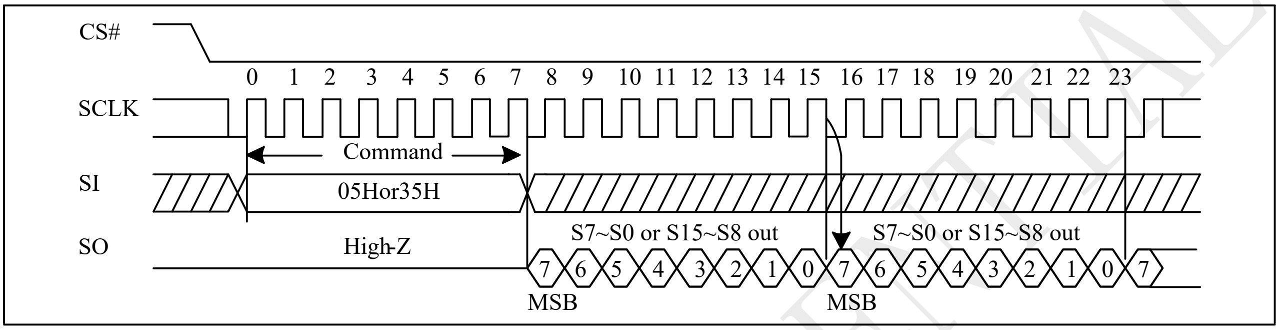
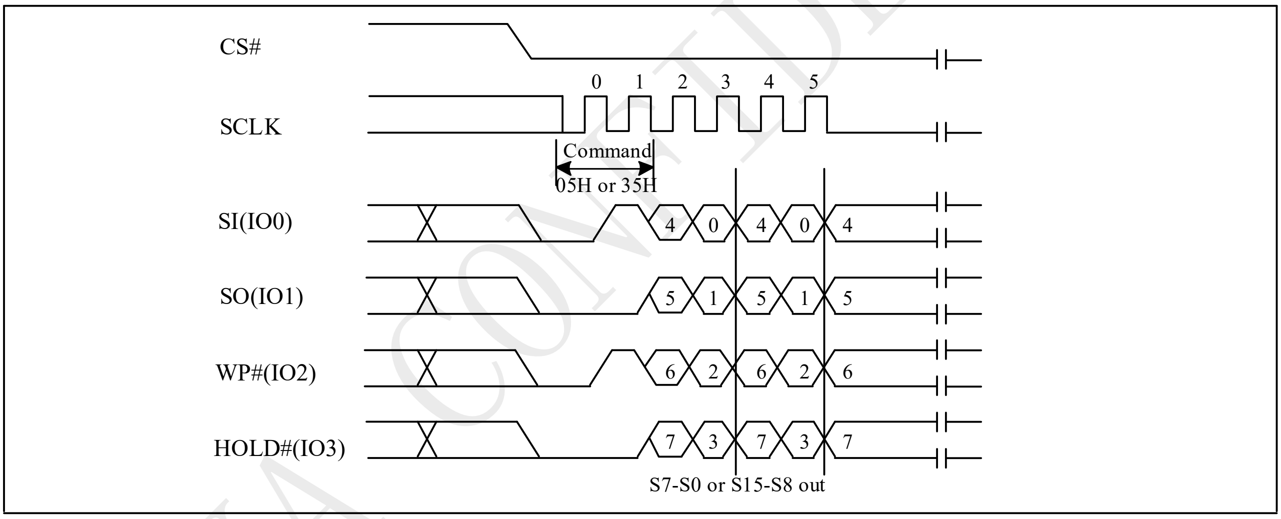


Figure 10-5a Read Status Register (RDSR) Sequence (QPI)



Status Register

BIT	S15	S14	S13	S12	S11	S10	S9	S8
Definition	SUS	CMP	LB3	LB2	LB1	EP_FAIL	QE	SRP1
Volatile	RO	NV	OTP	OTP	OTP	RO	NV	NV
default	0	0	0	0	0	0	0	0

BIT	S7	S6	S5	S4	S3	S2	S1	S0
Definition	SRP0	BP4	BP3	BP2	BP1	BP0	WEL	WIP
Volatile	NV	NV	NV	NV	NV	NV	V	RO
default	0	0	0	0	0	0	0	0

Note: OTP=One Time program. V=Volatile. NV=nonvolatile, RO=Read Only

The definition of the status register bits is as below:

WIP bit.
The Write in Progress (WIP) bit indicates whether the memory is busy in program/erase/write status register progress. When WIP bit sets to 1, means the device is busy in program/erase/write status register progress, when WIP bit sets 0, means the device is not in program/erase/write status register progress.

WEL bit.
The Write Enable Latch (WEL) bit indicates the status of the internal Write Enable Latch. When set to 1 the internal Write Enable Latch is set, when set to 0 the internal Write Enable Latch is reset and no Write Status Register, Program or Erase command is accepted.

BP4, BP3, BP2, BP1, BP0 bits.
The Block Protect (BP4, BP3, BP2, BP1, and BP0) bits are non-volatile. They define the size of the area to be software protected against Program and Erase commands. These bits are written with the Write Status Register (WRSR) command. When the Block Protect (BP4, BP3, BP2, BP1, BP0) bits are set to 1, the relevant memory area (as defined in Table “Protected Area Sizes”) becomes protected against Page Program (PP), Page Erase (PE), Sector Erase (SE) and Block Erase (BE) commands. The Block Protect (BP4, BP3, BP2, BP1, and BP0) bits can be written provided that the Hardware Protected mode has not been set. The Chip Erase (CE) command is executed, only if the Block Protect (BP4, BP3, BP2, BP1and BP0) are set to “None protected”.

SRP1, SRP0 bits.
The Status Register Protect (SRP1 and SRP0) bits are non-volatile Read/Write bits in the status register. The SRP bits control the method of write protection: software protection, hardware protection, power supply lock-down or one time programmable protection

SRP1	SRP0	WP#	Status Register	Description
0	0	x	Software Protected	The Status Register and Configure Register can be written to after a Write Enable command, WEL=1.(Default)
0	1	0	Hardware Protected	WP#=0, the Status Register and Configure Register locked and cannot be written to.
0	1	1	Hardware Unprotected	WP#=1, the Status Register and Configure Register is unlocked and can be written to after a Write Enable command, WEL=1.
1	0	x	Power Supply Lock-Down(1)	Status Register and Configure Register are protected and cannot be written to again until the next Power-Down, Power-Up cycle.
1	1	x	One Time Program(2)	Status Register and Configure Register are permanently protected and cannot be written to.

NOTE:
1. When SRP1, SRP0= (1, 0), a Power-Down, Power-Up cycle will change SRP1, SRP0 to (0, 0) state.
2. This feature is available on special order. Please contact PUYA for details.

QE bit.
The Quad Enable (QE) bit is a non-volatile Read/Write bit in the Status Register that allows Quad operation. When the QE bit is set to 0 (Default) the WP# pin and HOLD# pin are enable. When the QE pin is set to 1, the Quad IO2 and IO3 pins are enabled. (The QE bit should never be set to 1 during standard SPI or Dual SPI operation if the WP# or HOLD# pins are tied directly to the power supply or ground)

EP_FAIL bit.
The Erase/Program Fail bit is a read only bit which shows the status of the last Program/Erase operation. The bit will be set to "1" if the program/erase operation failed or reseted or the program/erase region was

protected. It will be automatically cleared to "0" if the next program/erase operation succeeds. Please note that it will not interrupt or stop any operation in the flash memory.

LB3, LB2, LB1, bits.
The LB3, LB2, LB1, bits are non-volatile One Time Program (OTP) bits in Status Register (S13-S11) that provide the write protect control and status to the Security Registers. The default state of LB3-LB1are0, the security registers are unlocked. The LB3-LB1bitscan be set to 1 individually using the Write Register instruction. The LB3-LB1bits are One Time Programmable, once its set to 1, the Security Registers will become read-only permanently.

CMP bit
The CMP bit is a non-volatile Read/Write bit in the Status Register(S14). It is used in conjunction the BP4-BP0 bits to provide more flexibility for the array protection. Please see the table “Protected Area Size” for details. The default setting is CMP=0.

SUS bit
The SUS bit is read only bit in the status register (S15) that is set to 1 after executing an Program/Erase Suspend (75H) command. The SUS bit is cleared to 0 by Program/Erase Resume (7AH) command as well as a power-down, power-up cycle.

10.6 Read Configure Register (RDCR)

The RDCR instruction is for reading Configure Register Bits. The Read Configure Register can be read at any time (even in program/erase/write status register condition). It is recommended to check the Write in Progress (WIP) bit before sending a new instruction when a program, erase, or write status register operation is in progress.

The sequence of issuing RDCR instruction is: CS# goes low→ sending RDCR instruction code→ Configure Register data out on SO. The SIO[3:1] are "don't care".

Figure 10-6 Read Status Register (RDCR) Sequence (Command 15)

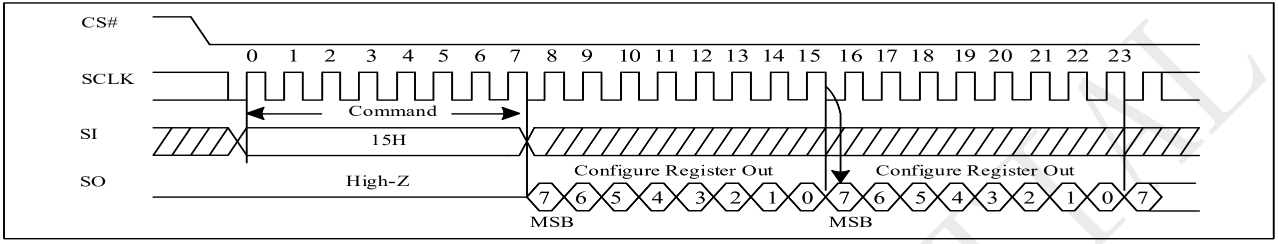
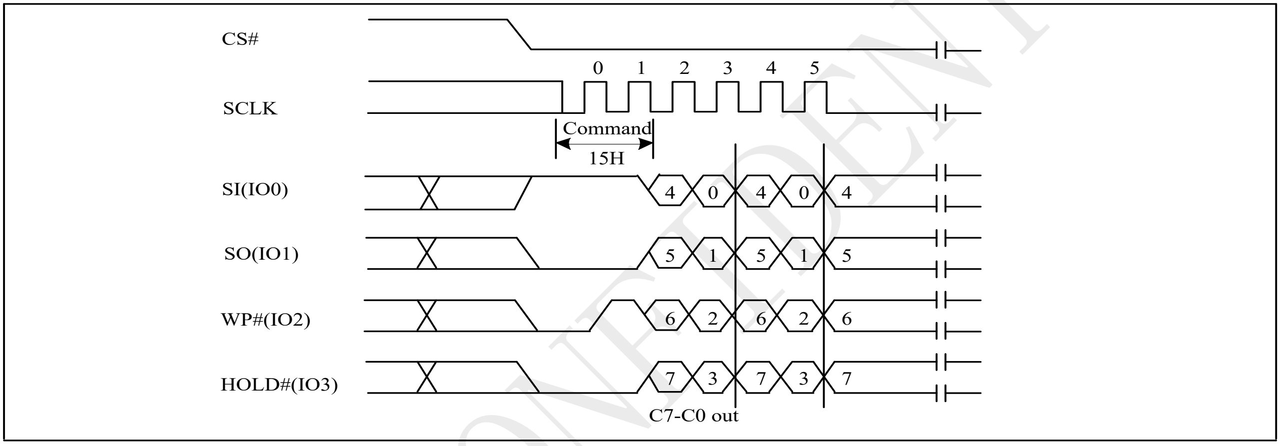


Figure 10-6a Read Status Register (RDCR) Sequence (QPI)



Configure Register

BIT	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Definition	HOLD/RST	Reserved	Reserved	reserved	reserved	reserved	DC	reserved
Volatile	NV	NV	NV	RO	RO	RO	V	RO
default	0	0	0	0	0	0	0	0

HOLD/RST bit.

The HOLD/RST bit is a nonvolatile Read/Write bit in the Configure Register which is used to determine whether /HOLD or /RESET function should be implemented on the hardware pin for 8-pin packages. When HOLD/RST=0 (factory default), the pin acts as /HOLD; when HOLD/RST=1, the pin acts as /RESET. However, /HOLD or /RESET functions are only available when QE=0. If QE is set to 1, the /HOLD and /RESET functions are disabled, the pin acts as a dedicated data I/O pin.

DC bit

The Dummy Cycle (DC) bit is a volatile bit. The Dummy Cycle (DC) bit can be used to configure the number of dummy clocks for “SPI 2 X IO Read (BBH)” command, “SPI 4X I/O Read (EBH)” command.

Table Dummy Cycle Table

Command	Mode	DC	Number of dummy cycles
SPI command	BB SPI	0(default)	4
		1	8
	EB SPI	0(default)	6
		1	10

10.7 Write Status Register (01H/31H)

The Write Status Register (WRSR) and Write Status Register-1 (WRSR1) commands allow new values to be written to the Status Register-0 and Status Register-1. Before it can be accepted, a Write Enable (WREN) command must previously have been executed. After the Write Enable (WREN) command has been decoded and executed, the device sets the Write Enable Latch (WEL).

The WRSR and WRSR1 command has no effect on S15, S10, S1 and S0 of the Status Register. CS# must be driven high after the eighth bit or sixteen bit (just for WRSR command) of the data byte has been latched in. If not, the command is not executed. If CS# is driven high after eight bits of the data byte, the CMP and QE and SRP1 bits will be cleared to "0". As soon as CS# is driven high, the self-timed Write Status Register cycle (whose duration is tW) is initiated. While the Write Status Register cycle is in progress, the Status Register may still be read to check the value of the Write in Progress (WIP) bit. The Write in Progress (WIP) bit is 1 during the self-timed Write Status Register cycle, and is 0 when it is completed. When the cycle is completed, the Write Enable Latch (WEL) is reset.

The WRSR command allows the user to change the values of the Block Protect (BP4, BP3, BP2, BP1, and BP0) bits, to define the size of the area that is to be treated as read-only, as defined in Table6-1 and Table6-2. The WRSR and WRSR1 commands also allow the user to set or reset the Status Register Protect (SRP0 and SRP1) bits respectively in accordance with the Write Protect (WP#) signal. The Status Register Protect (SRP0 and SRP1) bits and Write Protect (WP#) signal allow the device to be put in the Hardware Protected Mode. The Write Status Register (WRSR) command is not executed once the Hardware Protected Mode is entered.

The sequence of issuing WRSR instruction is: CS# goes low→ sending WRSR instruction code→ Status Register data on SI→CS# goes high.

The CS# must go high exactly at the eight bits data boundary; otherwise, the instruction will be rejected and not executed. The self-timed Write Status Register cycle time (tW) is initiated as soon as Chip Select (CS#) goes high. The Write in Progress (WIP) bit still can be checked during the Write Status Register cycle is in progress. The WIP sets "1" during the tW timing, and sets "0" when Write Status Register Cycle is completed, and the Write Enable Latch (WEL) bit is reset.

Figure 10-7Write Status Register (WRSR) Sequence (Command 01h or 31h)

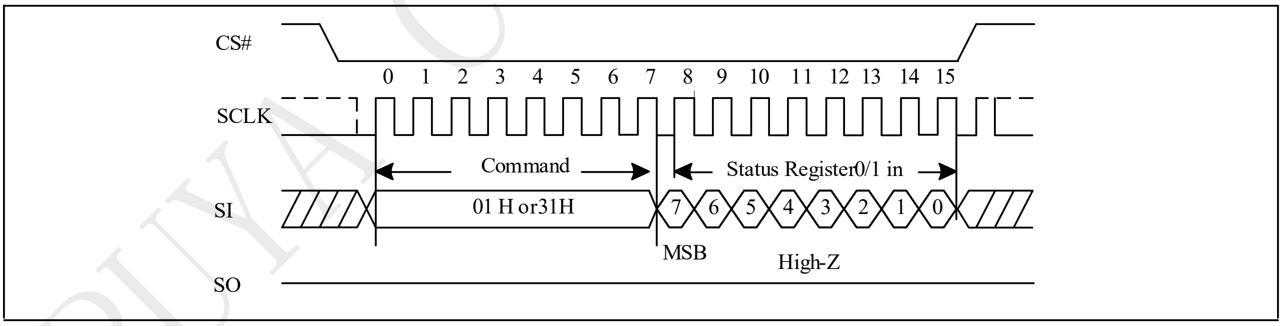
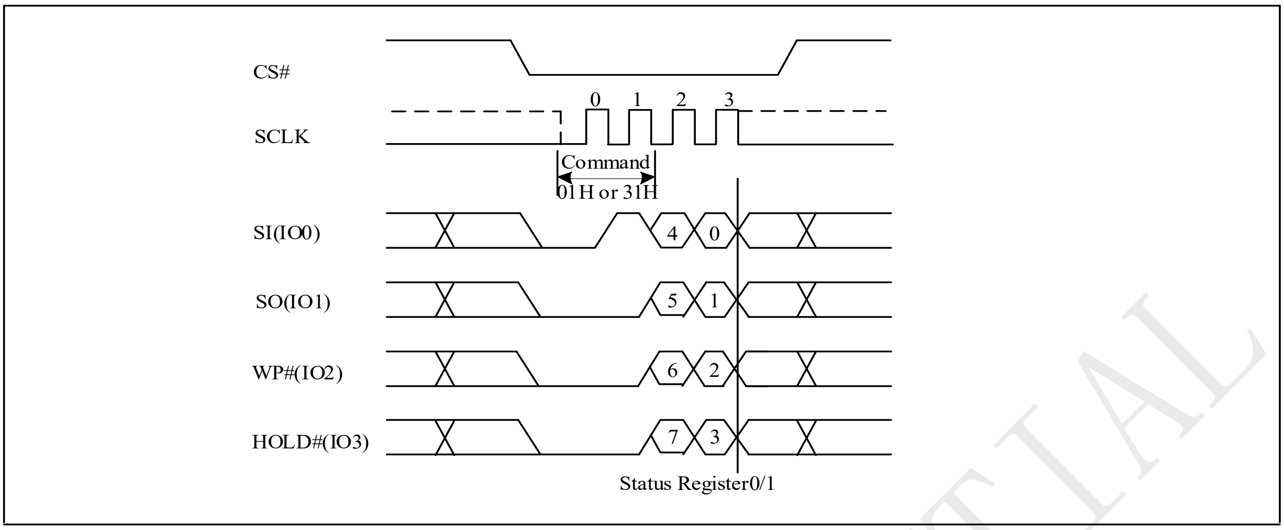


Figure 10-7a Write Status Register (WRSR) Sequence (QPI)



To be backward compatible to Puya's previous serial flash product, The Write Status Register (WRSR) command also support to write Status Register-0 and Status Register-1 in same time. To complete this function, CS# must be driven high after the sixteenth bit of the data byte has been latched in. If CS# is driven high after the eighth clock, the Write Status Register (01h) command will only program the Status Register-0, the Status Register-1 will not be affected (Previous product will clear CMP and QE bits).

Figure 10-7b Write Status Register (WRSR) with 2 Byte data Sequence (SPI)

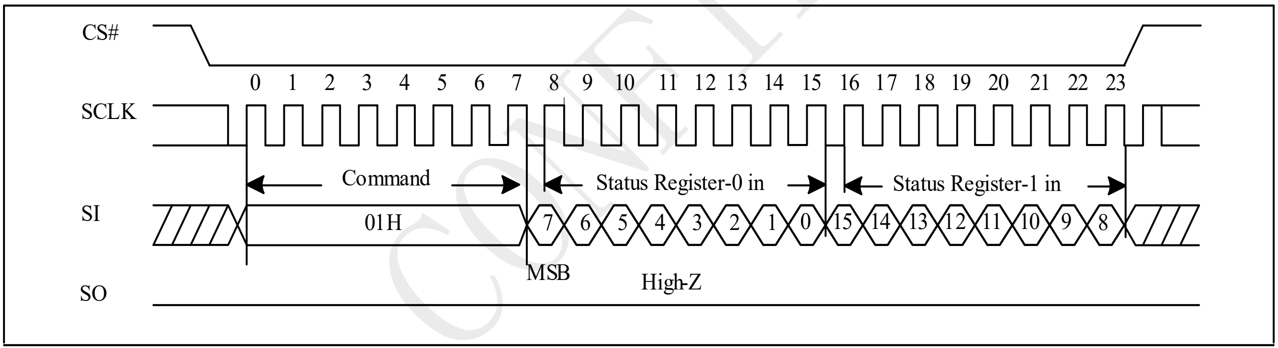
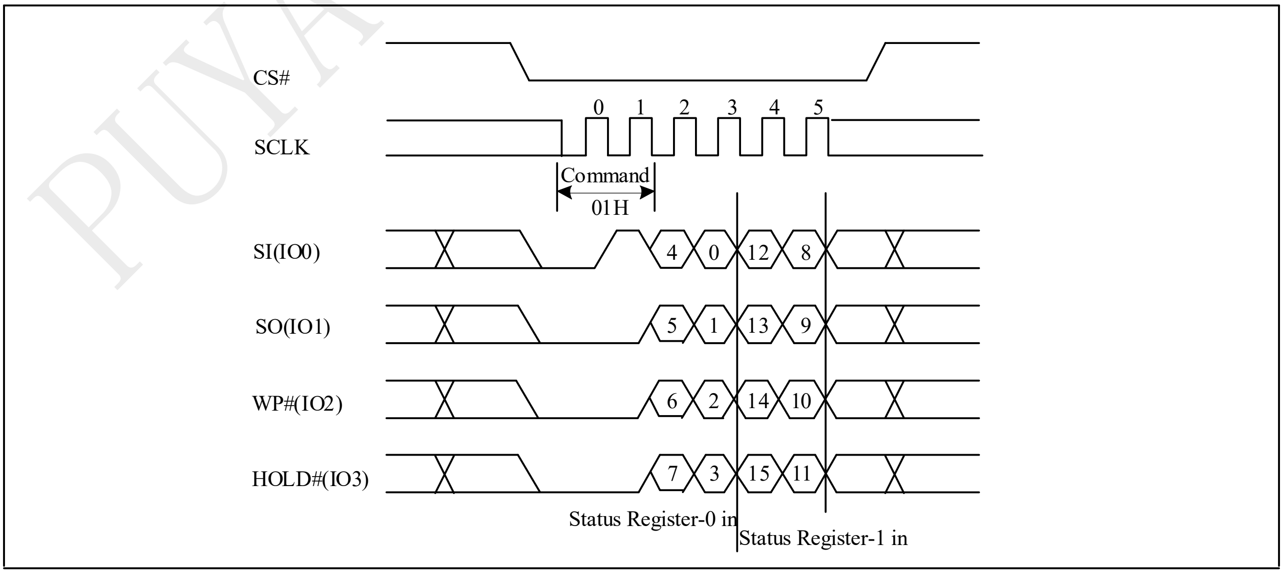


Figure 10-7C Write Status Register (WRSR) with 2 Byte data Sequence (QPI)



10.8 Write Configure Register (WRCR)

The Write Configure Register (WRCR) command allows new values to be written to the Configure Register. Before it can be accepted, a Write Enable (WREN) command must previously have been executed. After the Write Enable (WREN) command has been decoded and executed, the device sets the Write Enable Latch (WEL).

The sequence of issuing WRCR instruction is: CS# goes low→ sending WRCR instruction code→ Configure Register data on SI→CS# goes high.

The CS# must go high exactly at the 8 bits data boundary; otherwise, the instruction will be rejected and not executed. The self-timed Write Status Register cycle time (tW) is initiated as soon as Chip Select (CS#) goes high. The Write in Progress (WIP) bit still can be checked during the Write Status Register cycle is in progress. The WIP sets 1 during the tW timing, and sets 0 when Write Configure Register Cycle is completed, and the Write Enable Latch (WEL) bit is reset.

Figure 10-8 Write Configure Register (WRCR) Sequence (Command 11)

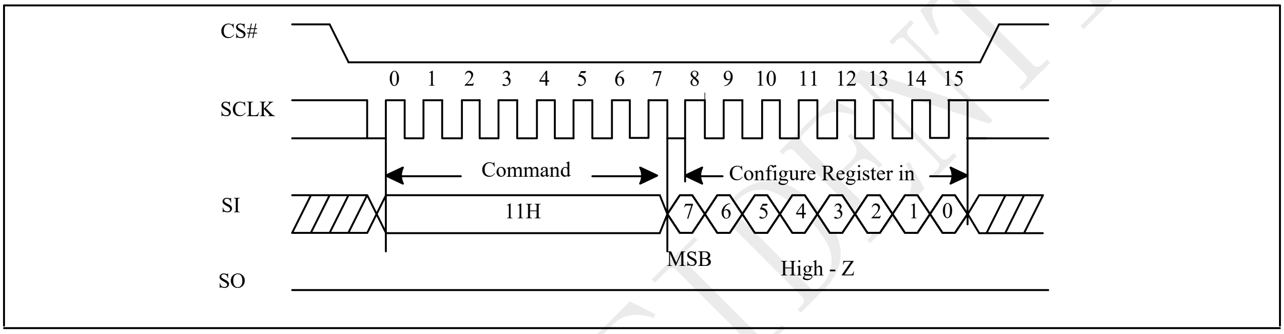
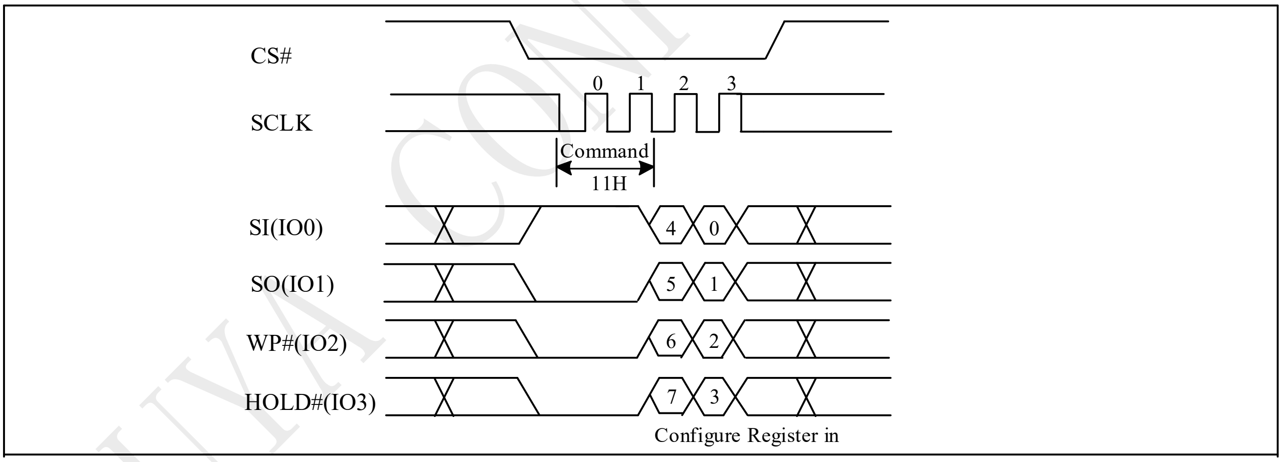


Figure 10-8a Write Configure Register (WRCR) Sequence (QPI)

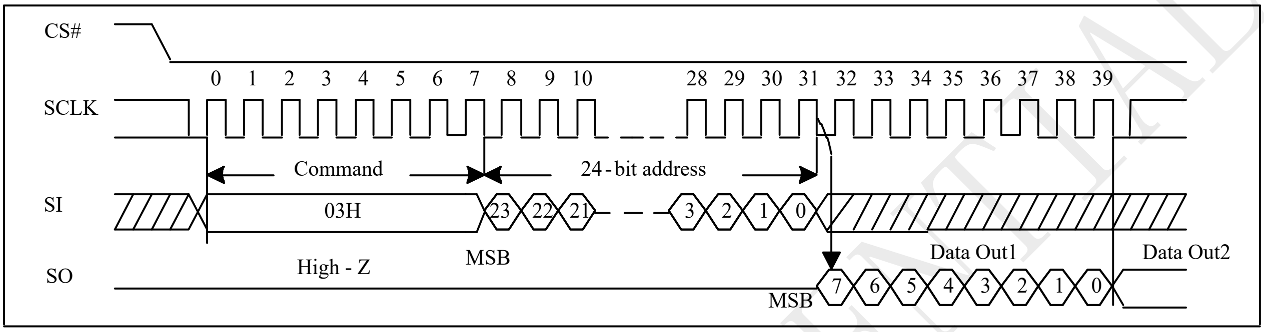


10.9 Read Data Bytes (READ)

The read instruction is for reading data out. The address is latched on rising edge of SCLK, and data shifts out on the falling edge of SCLK at a maximum frequency fR. The first address byte can be at any location. The address is automatically increased to the next higher address after each byte data is shifted out, so the whole memory can be read out at a single READ instruction. The address counter rolls over to 0 when the highest address has been reached.

The sequence of issuing READ instruction is: CS# goes low→ sending READ instruction code→ 3-byte address on SI→ data out on SO→ to end READ operation can use CS# to high at any time during data out.

Figure 10-9 Read Data Bytes (READ) Sequence (Command 03)



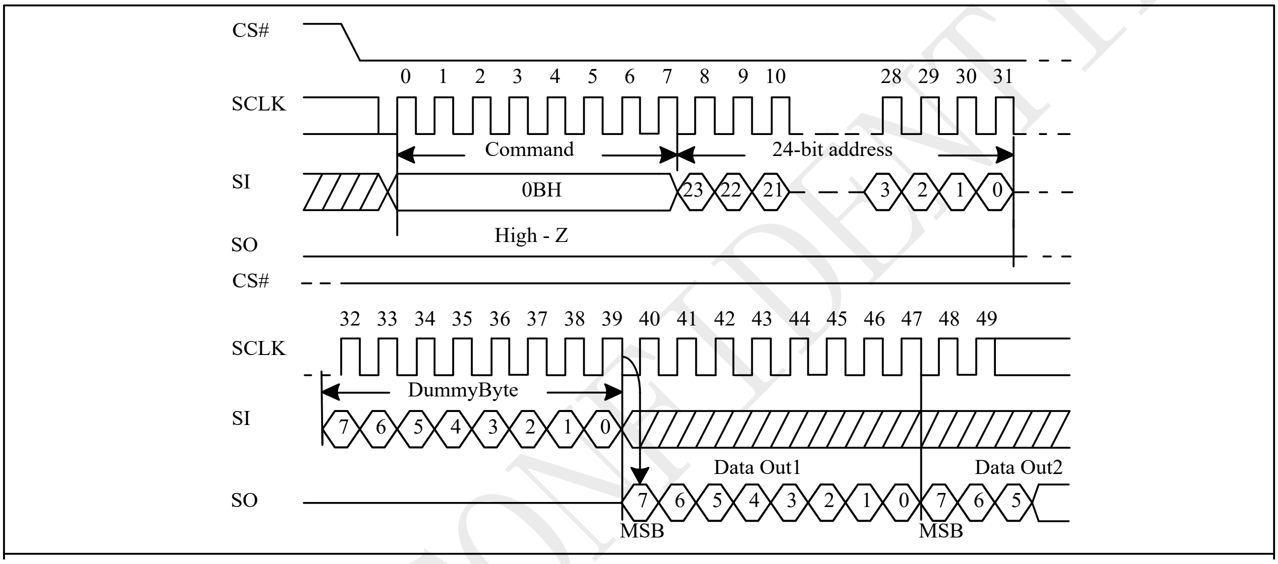
10.10 Fast Read (FREAD)

The FAST READ instruction is for quickly reading data out. The address is latched on rising edge of SCLK, and data of each bit shifts out on the falling edge of SCLK at a maximum frequency fC. The first address byte can be at any location. The address is automatically increased to the next higher address after each byte data is shifted out, so the whole memory can be read out at a single FREAD instruction. The address counter rolls over to 0 when the highest address has been reached.

The sequence of issuing FREAD instruction is: CS# goes low→ sending FREAD instruction code→3-byte address on SI→ 1-dummy byte address on SI→data out on SO→ to end FREAD operation can use CS# to high at any time during data out.

While Program/Erase/Write Status Register cycle is in progress, FREAD instruction is rejected without any impact on the Program/Erase/Write Status Register current cycle.

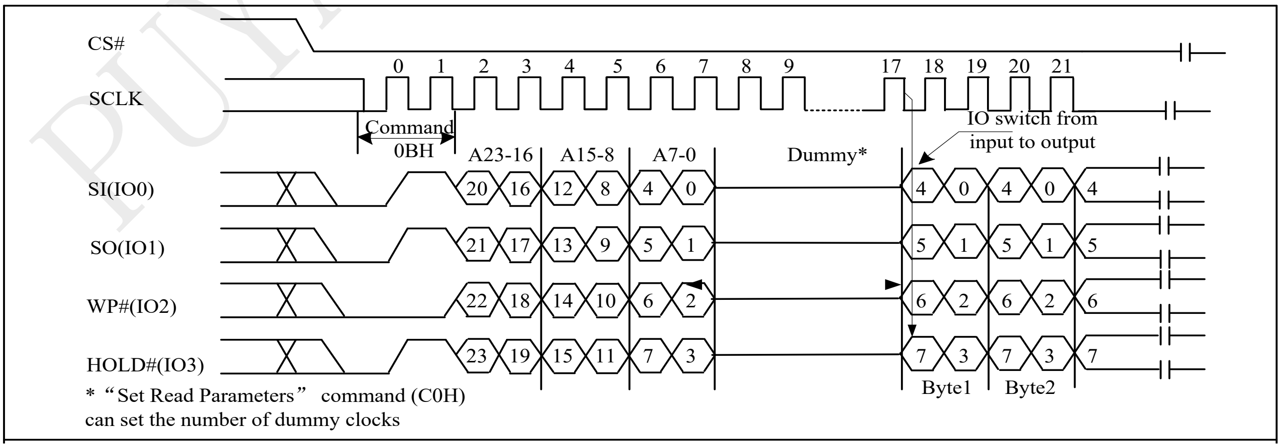
Figure 10-10 Fast Read (FREAD) Sequence (Command 0B)



Fast Read in QPI mode

The Fast Read command is also supported in QPI mode. In QPI mode, the number of dummy clocks is configured by the “Set Read Parameters (C0H)” command to accommodate a wide range application with different needs for either maximum Fast Read frequency or minimum data access latency. Depending on the Read Parameter Bits P[5:4] setting, the number of dummy clocks can be configured.

Figure 10-10a Fast Read Sequence (QPI)



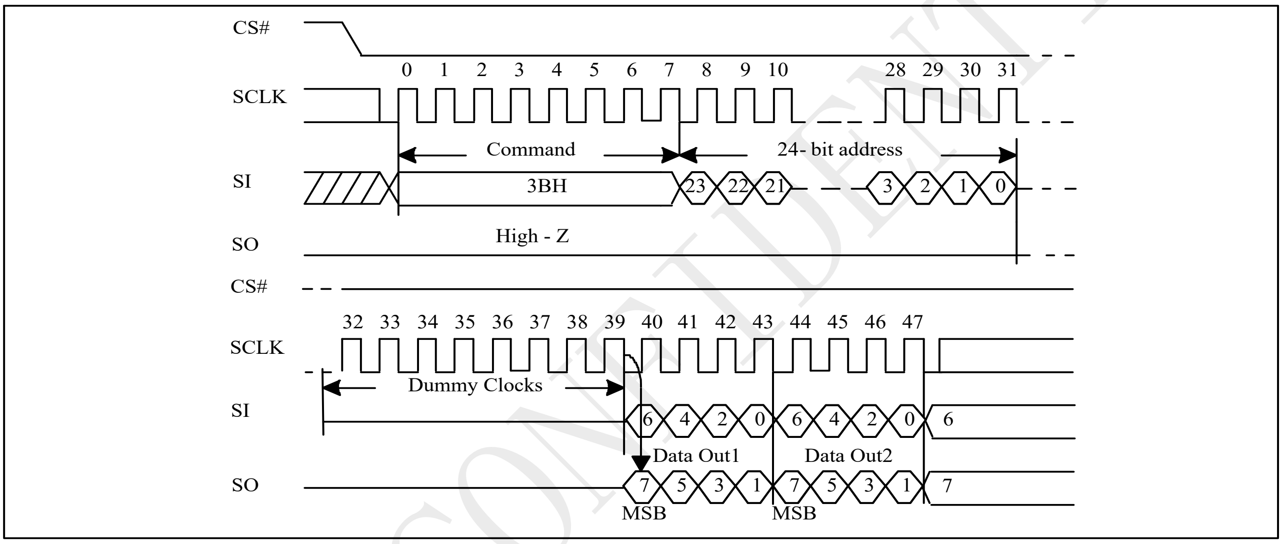
10.11 Dual Read (DREAD)

The DREAD instruction enable double throughput of Serial NOR Flash in read mode. The address is latched on rising edge of SCLK, and data of every two bits (interleave on 2 I/O pins) shift out on the falling edge of SCLK at a maximum frequency fT. The first address byte can be at any location. The address is automatically increased to the next higher address after each byte data is shifted out, so the whole memory can be read out at a single DREAD instruction. The address counter rolls over to 0 when the highest address has been reached. Once writing DREAD instruction, the following data out will perform as 2-bit instead of previous 1-bit.

The sequence of issuing DREAD instruction is: CS# goes low → sending DREAD instruction → 3-byte address on SI → 8-bit dummy cycle → data out interleave on SIO1 & SIO0 → to end DREAD operation can use CS# to high at any time during data out.

While Program/Erase/Write Status Register cycle is in progress, DREAD instruction is rejected without any impact on the Program/Erase/Write Status Register current cycle.

Figure 10-11 Dual Read Mode Sequence (Command 3B)



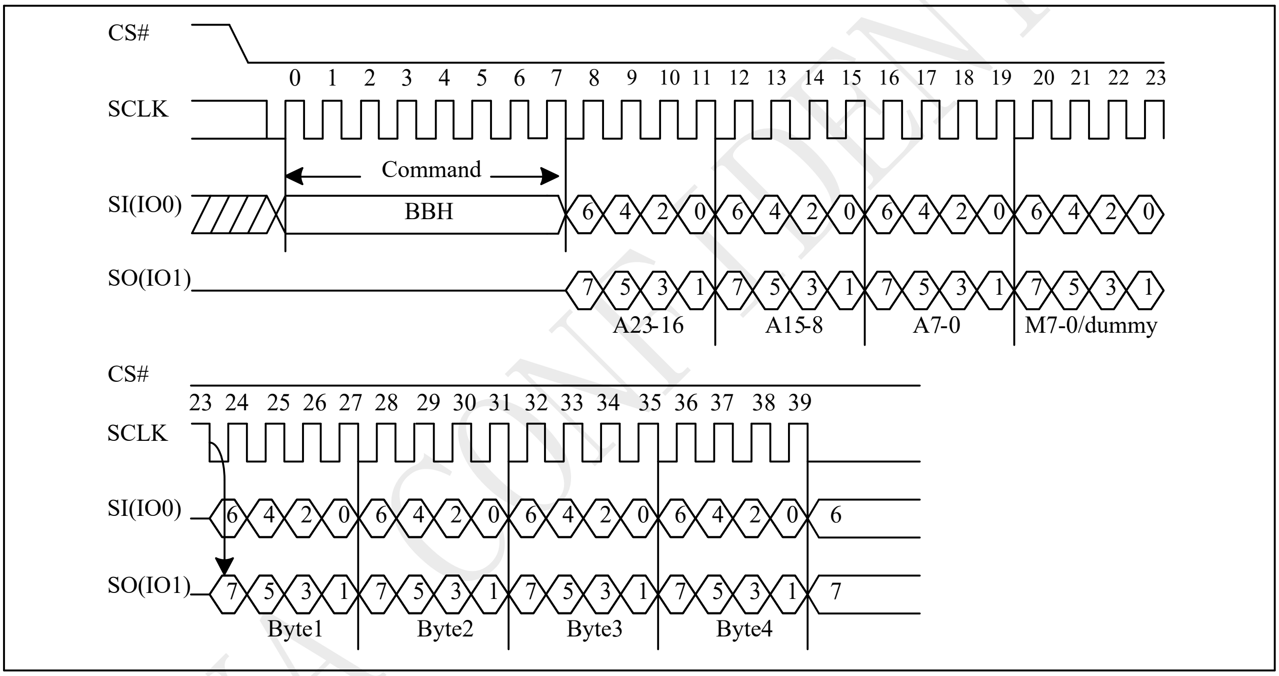
10.12 2IO Read (2READ)

The 2READ instruction enables Double Transfer Rate of Serial NOR Flash in read mode. The address is latched on rising edge of SCLK, and data of every two bits (interleave on 2 I/O pins) shift out on the falling edge of SCLK at a maximum frequency fT. The first address byte can be at any location. The address is automatically increased to the next higher address after each byte data is shifted out, so the whole memory can be read out at a single 2READ instruction. The address counter rolls over to 0 when the highest address has been reached. Once writing 2READ instruction, the following address/dummy/data out will perform as 2-bit instead of previous 1-bit.

The sequence of issuing 2READ instruction is: CS# goes low→ sending 2READ instruction→ 24-bit address interleave on SIO1 & SIO0→ 8-bit dummy cycle on SIO1 & SIO0→ data out interleave on SIO1 & SIO0→ to end 2READ operation can use CS# to high at any time during data out.

While Program/Erase/Write Status Register cycle is in progress, 2READ instruction is rejected without any impact on the Program/Erase/Write Status Register current cycle.

Figure 10-12 2IO Read Sequence (Command BB M5-4 ≠ (1,0))



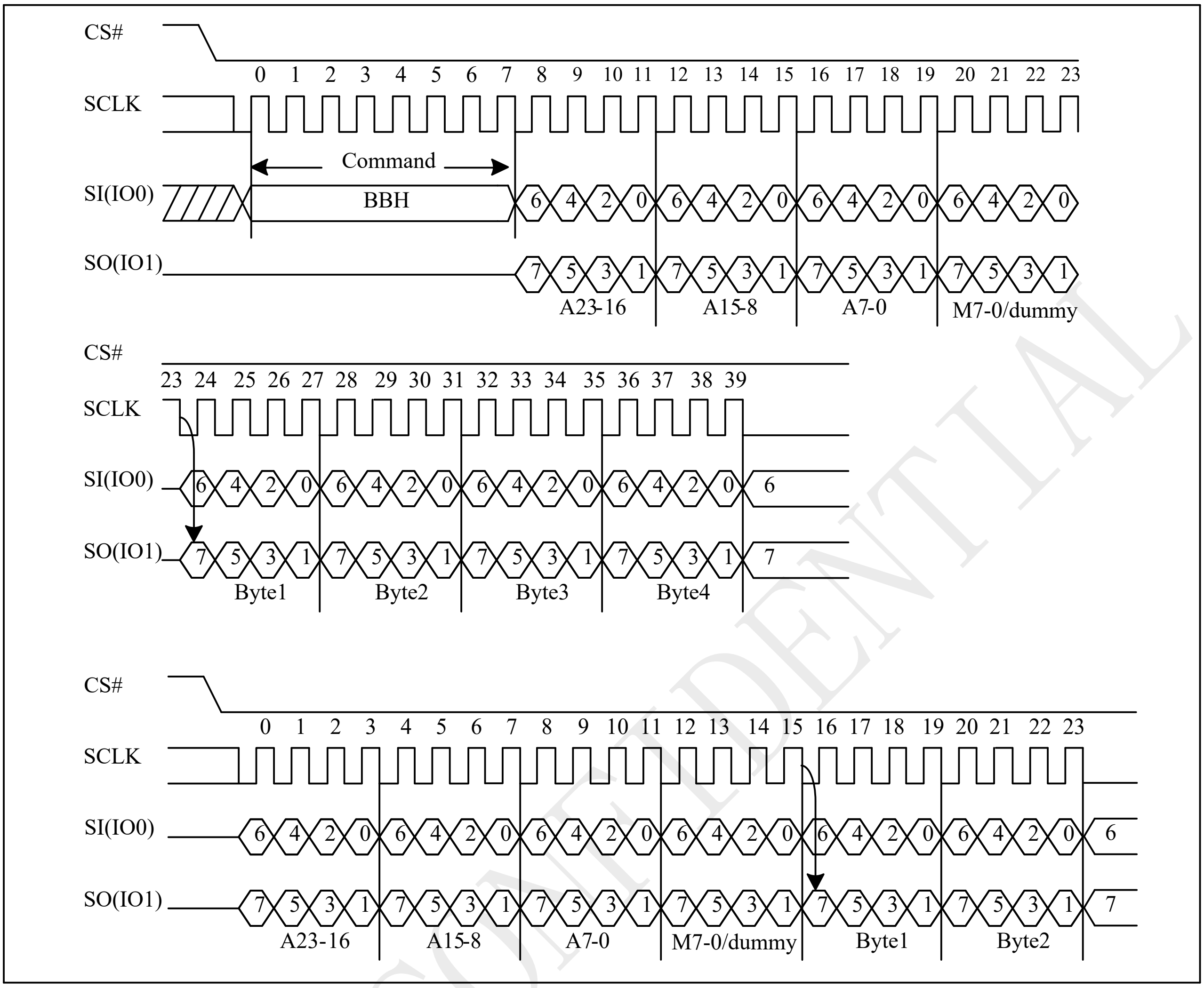
Note:
1. M[5-4] = (1,0) is inhibited.
2. DC bit can set the number of dummy clocks.

2IO Continuous Read

"BBh" command supports 2IO Continuous Read which can further reduce command overhead through setting the "Continuous Read Mode" bits (M7-0) after the input 3-byte address (A23-A0). If the "Continuous Read Mode" bits (M5-4) = (1, 0), then the next 2IO Read command (after CS# is raised and then lowered) does not require the BBH command code.

If the "Continuous Read Mode" bits (M5-4) do not equal (1, 0), the next command requires the first BBH command code, thus returning to normal operation. A "Continuous Read Mode" Reset command can be used to reset (M5-4) before issuing normal command.

Figure 10-12a 2IO Continue Read (M5-4 = (1,0))



Note:

1. 2IO Continue Read, if M5-4 = 1, 0. If not using Continue Read recommend to set M5-4 ≠ 1, 0.
2. DC bit can set the number of dummy clocks.

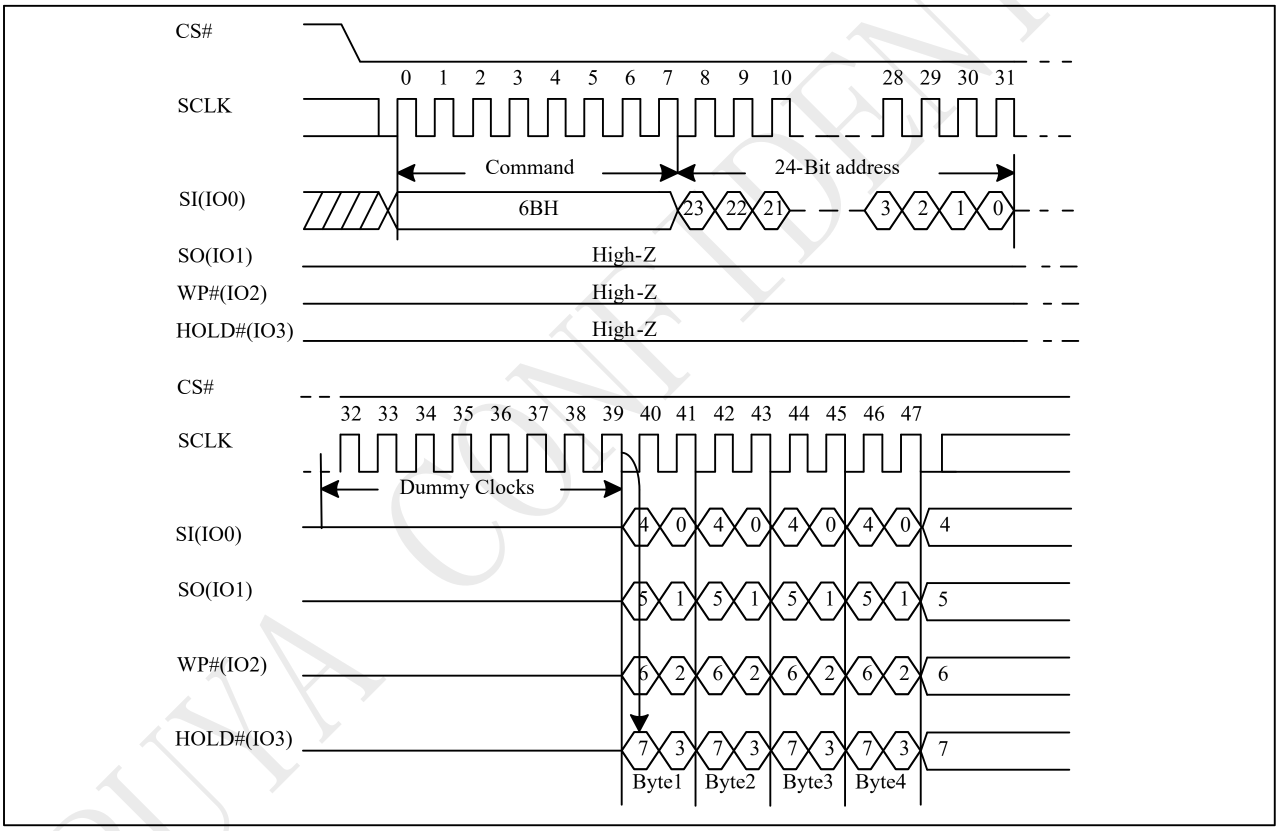
10.13 Quad Read (QREAD)

The QREAD instruction enable quad throughput of Serial NOR Flash in read mode. A Quad Enable (QE) bit of status Register must be set to "1" before sending the QREAD instruction. The address is latched on rising edge of SCLK, and data of every four bits (interleave on 4 I/O pins) shift out on the falling edge of SCLK at a maximum frequency fQ. The first address byte can be at any location. The address is automatically increased to the next higher address after each byte data is shifted out, so the whole memory can be read out at a single QREAD instruction. The address counter rolls over to 0 when the highest address has been reached. Once writing QREAD instruction, the following data out will perform as 4-bit instead of previous 1-bit.

The sequence of issuing QREAD instruction is: CS# goes low→ sending QREAD instruction → 3-byte address on SI → 8-bit dummy cycle → data out interleave on SIO3, SIO2, SIO1 & SIO0→ to end QREAD operation can use CS# to high at any time during data out.

While Program/Erase/Write Status Register cycle is in progress, QREAD instruction is rejected without any impact on the Program/Erase/Write Status Register current cycle.

Figure 10-13 Quad Read Sequence (Command 6B)



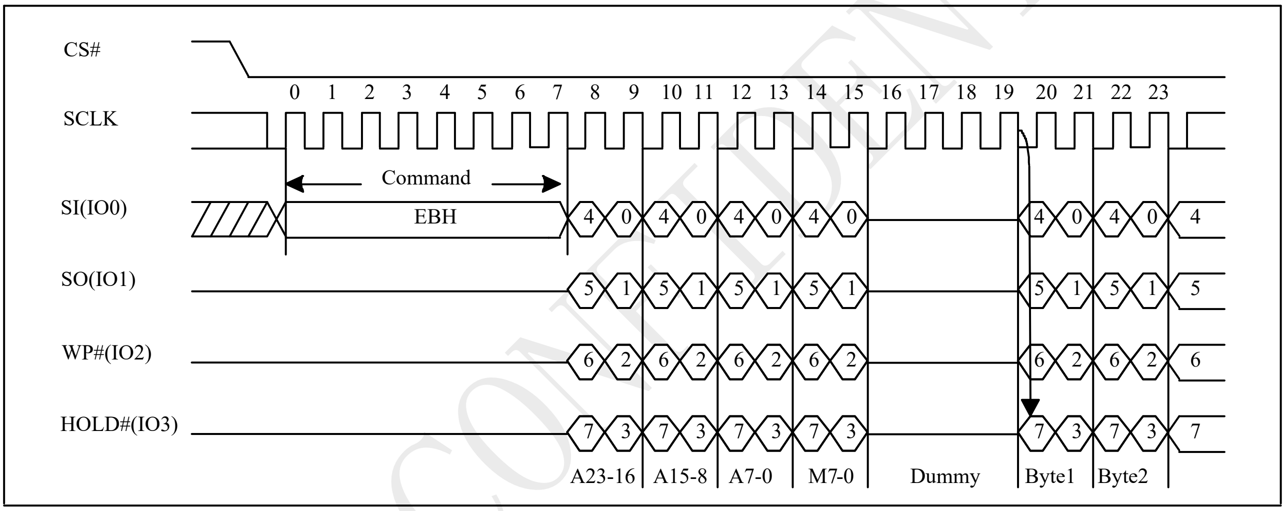
10.14 4IO Read (4READ)

The 4READ instruction enable quad throughput of Serial NOR Flash in read mode. A Quad Enable (QE) bit of status Register must be set to "1" before sending the 4READ instruction. The address is latched on rising edge of SCLK, and data of every four bits (interleave on 4 I/O pins) shift out on the falling edge of SCLK at a maximum frequency fQ. The first address byte can be at any location. The address is automatically increased to the next higher address after each byte data is shifted out, so the whole memory can be read out at a single 4READ instruction. The address counter rolls over to 0 when the highest address has been reached. Once writing 4READ instruction, the following address/dummy/data out will perform as 4-bit instead of previous 1-bit.

The sequence of issuing 4READ instruction is: CS# goes low→ sending 4READ instruction→ 24-bit address interleave on SIO3, SIO2, SIO1 & SIO0→2+4 dummy cycles→data out interleave on SIO3, SIO2, SIO1 & SIO0→ to end 4READ operation can use CS# to high at any time during data out.

While Program/Erase/Write Status Register cycle is in progress, 4READ instruction is rejected without any impact on the Program/Erase/Write Status Register current cycle.

Figure 10-14 4IO Read Sequence (Command EB M5-4 ≠ (1,0))



Note:
1. Hi-impedance is inhibited for the two clock cycles.
2. M[5-4] = (1,0) is inhibited.
3. DC bit can set the number of dummy clocks.

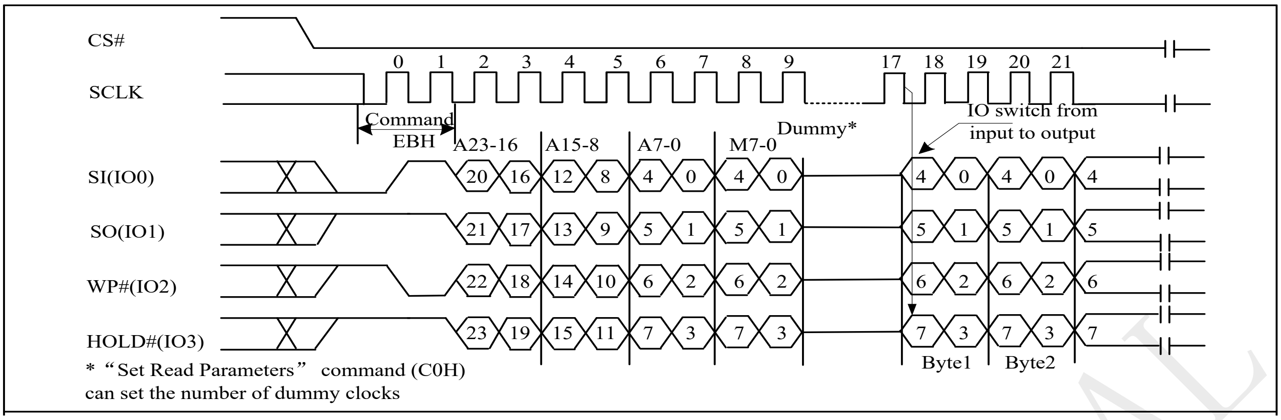
4IO Read in QPI mode

The 4READ instruction is also supported in QPI mode. When QPI mode is enabled, the number of dummy clocks is configured by the “Set Read Parameters (C0h)” instruction to accommodate a wide range of applications with different needs for either maximum Fast Read frequency or minimum data access latency. Depending on the Read Parameter Bits P[5:4] setting, the number of dummy clocks can be configured as either 10, 4, 6 or 8. The default number of dummy clocks upon power up or after a Reset instruction is 10. In QPI mode, the “Continuous Read Mode” bits M7- 0 are also considered as dummy clocks. In the default setting, the data output will follow the Continuous Read Mode bits immediately.

“Continuous Read Mode” feature is also available in QPI mode for 4IO Read instruction. Please refer to the description on next pages.

“Wrap Around” feature is not available in QPI mode for 4IO Read instruction. To perform a read operation with fixed data length wrap around in QPI mode, a dedicated “Burst Read with Wrap” (0Ch) instruction must be used.

Figure 10-14a 4IO Read in QPI mode Sequence (QPI M5-4 ≠ (1,0))



Note:

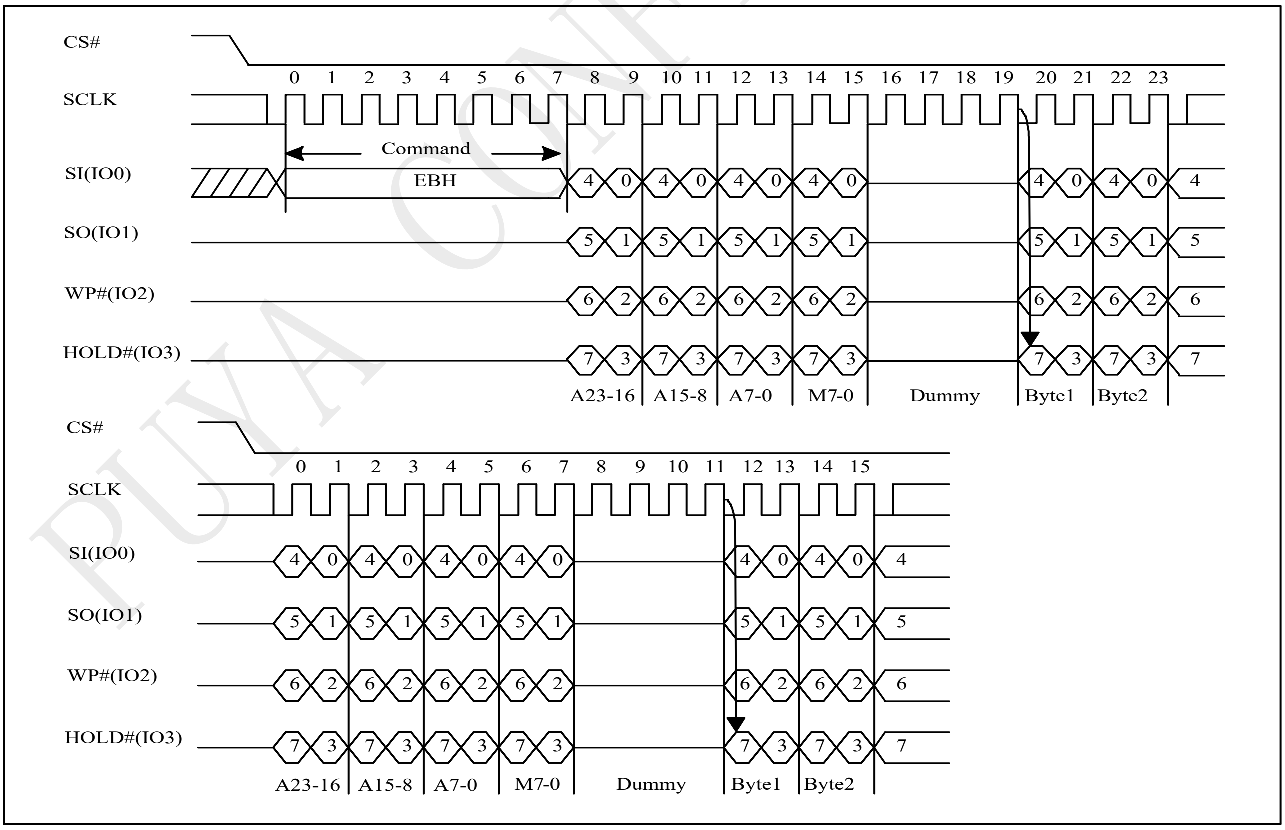
1. Hi-impedance is inhibited for the two clock cycles.
2. M[5-4] = (1,0) is inhibited.

4IO Continuous Read

“EBh” command supports 4IO Continuous Read which can further reduce command overhead through setting the “Continuous Read Mode” bits (M7-0) after the input 3-byte address (A23-A0). If the “Continuous Read Mode” bits (M5-4) = (1, 0), then the next 4IO Read command (after CS# is raised and then lowered) does not require the EBH command code.

If the “Continuous Read Mode” bits (M5-4) do not equal (1, 0), the next command requires the first EBH command code, thus returning to normal operation. A “Continuous Read Mode” Reset command can be used to reset (M5-4) before issuing normal command.

Figure 10-14b 4IO Continuous Read Sequence (M5-4 = (1,0))



Note:

1. 4IO Continuous Read Mode, if M5-4 = 1, 0. If not using Continuous Read recommend to set M5-4 ≠ 1, 0.
2. DC bit can set the number of dummy clocks.

10.15 Set Burst Read

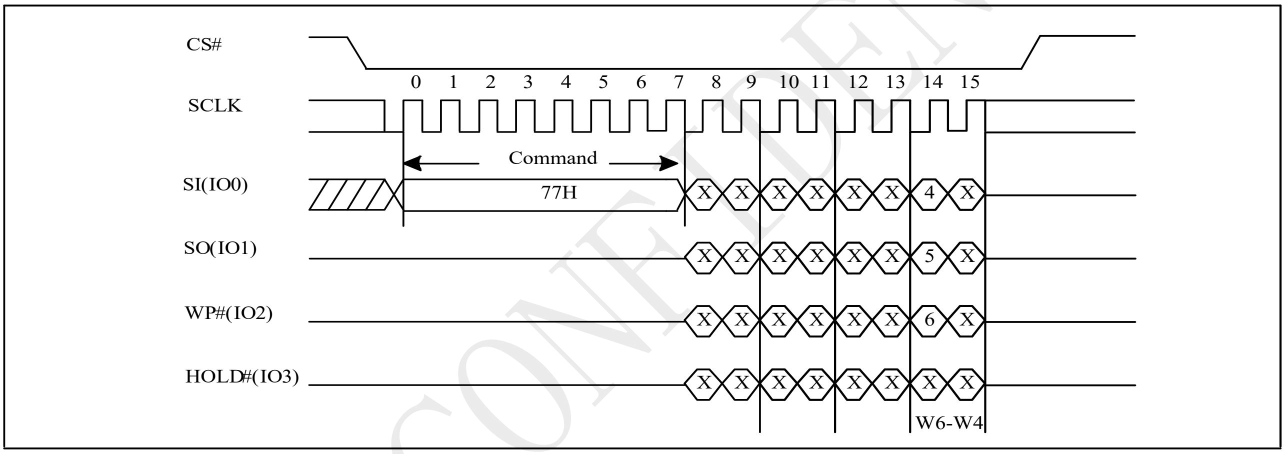
The Set Burst with Wrap command is used in conjunction with “4IO Read” command to access a fixed length of 8/16/32/64-byte section within a 256-byte page, in standard SPI mode.

The Set Burst with Wrap command sequence: CS# goes low → Send Set Burst with Wrap command → Send 24 dummy bits→ Send 8 bits “Wrap bits” → CS# goes high.

W6,W5	W4=0		W4=1 (default)	
	Wrap Aroud	Wrap Length	Wrap Aroud	Wrap Length
0,0	Yes	8-byte	No	N/A
0,1	Yes	16-byte	No	N/A
1,0	Yes	32-byte	No	N/A
1,1	Yes	64-byte	No	N/A

If the W6-W4 bits are set by the Set Burst with Wrap command, all the following “4IO Read” command will use the W6-W4 setting to access the 8/16/32/64-byte section within any page. To exit the “Wrap Around” function and return to normal read operation, another Set Burst with Wrap command should be issued to set W4=1.

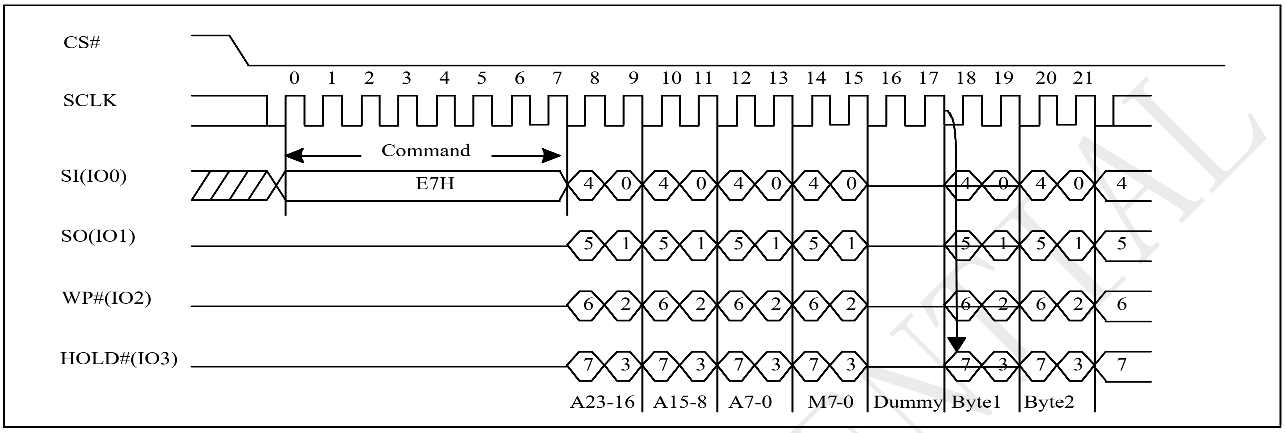
Figure 10-15 Set Burst Read (SBL) Sequence (Command 77)



10.16 4IO Word Read(E7h)

The 4IO Word Read command is similar to the 4 IO Read command except that the lowest address bit (A0) must equal 0 and only 2-dummy clock. The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out. The Quad Enable bit (QE) of Status Register (S9) must be set to enable for the 4IO Word read command.

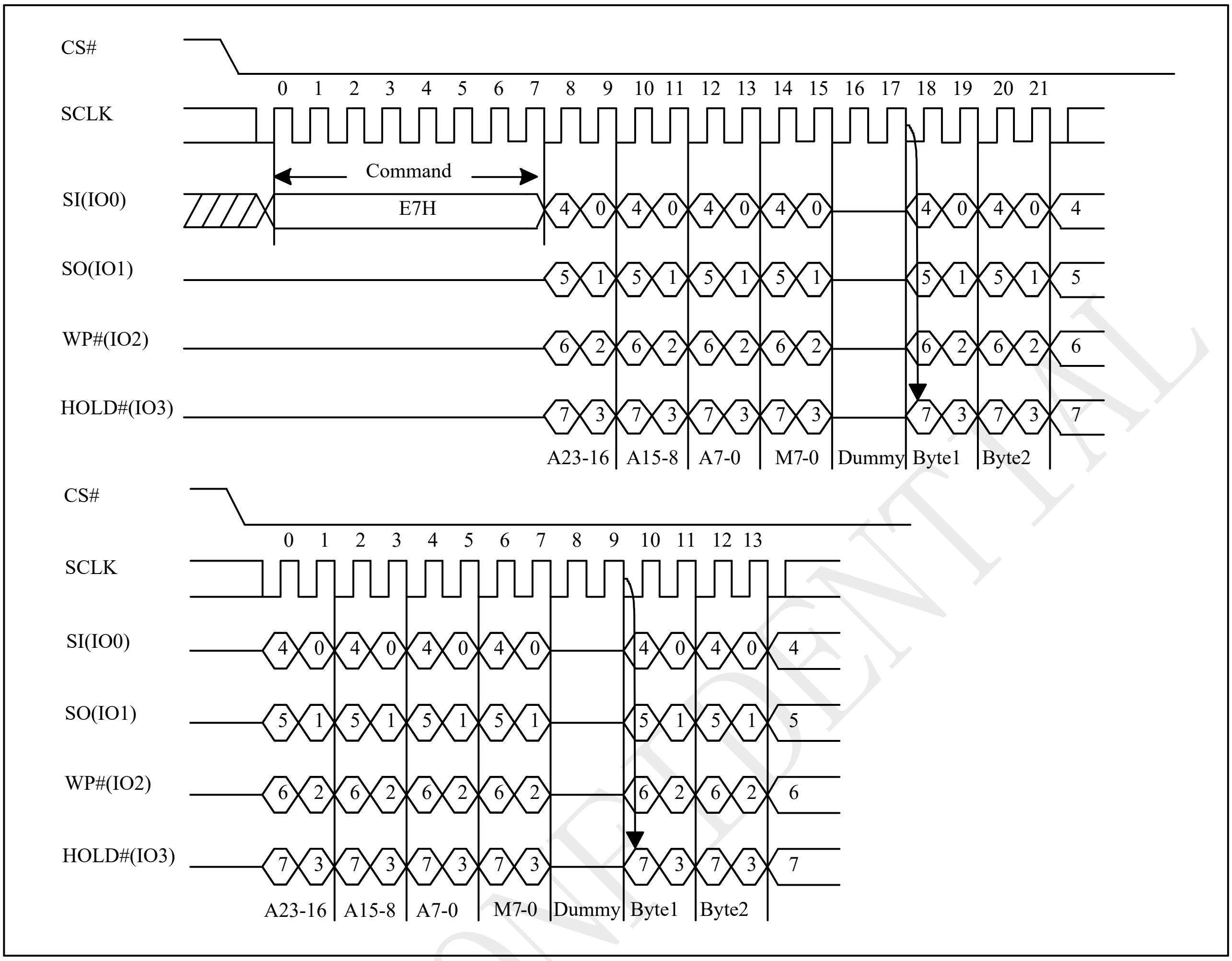
Figure 10-16 4IO Word Read Sequence (M5-4 ≠ (1,0))



4IO Word Read with "Continuous Read Mode"

The 4IO Word Read command can further reduce command overhead through setting the "Continuous Read Mode" bits (M7-0) after the input 3-byte address (A23-A0). If the "Continuous Read Mode" bits (M5-4) = (1, 0), then the next 4IO Word Read command (after CS# is raised and then lowered) does not require the E7H command code. If the "Continuous Read Mode" bits (M5-4) do not equal to (1, 0), the next command requires the first E7H command code, thus returning to normal operation. A "Continuous Read Mode" Reset command can be used to reset (M5-4) before issuing normal command.

Figure 10-17a 4IO Word Read Sequence (M5-4 = (1,0))



4IO Word Read with “8/16/32/64-Byte Wrap Around” in Standard SPI mode

The 4IO Word Read command can be used to access a specific portion within a page by issuing “Set Burst with Wrap”(77H) commands prior to E7H. The “Set Burst with Wrap”(77H) command can either enable or disable the “Wrap Around” feature for the following E7H commands. When “Wrap Around” is enabled, the data being accessed can be limited to either an8/16/32/64-byte section of a 256-byte page. The output data starts at the initial address specified in the command, once it reaches the ending boundary of the 8/16/32/64-byte section, the output will wrap around the beginning boundary automatically until CS# is pulled high to terminate the command.

The Burst with Wrap feature allows applications that use cache to quickly fetch a critical address and then fill the cache afterwards within a fixed length (8/16/32/64-byte) of data without issuing multiple read commands. The “Set Burst with Wrap” command allows three “Wrap Bits”W6-W4 to be set. The W4 bit is used to enable or disable the “Wrap Around” operation while W6-W5 is used to specify the length of the wrap around section within a page.

10.17 Set Read Parameters (C0h)

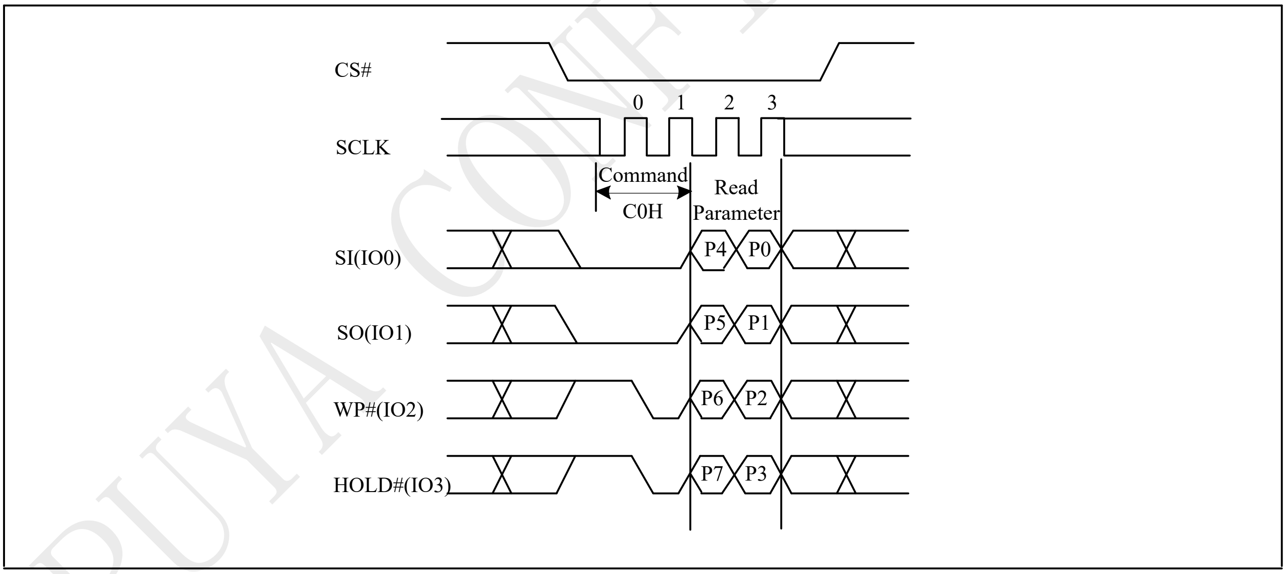
In QPI mode, to accommodate a wide range of applications with different needs for either maximum read frequency or minimum data access latency, "Set Read Parameters (C0h)" instruction can be used to configure the number of dummy clocks for "Fast Read (0Bh)", "4IO Read (EBh)" , "Burst Read with Wrap (0Ch)" , "Read SFDP Mode (5Ah)" instructions, and to configure the number of bytes of "Wrap Length" for the "Burst Read with Wrap (0Ch)" instruction.

In Standard SPI mode, the "Set Read Parameters (C0h)" instruction is not accepted. The dummy clocks for various Fast Read instructions in Dual/Quad SPI mode are configured by DC bit. The "Wrap Length" is set by W5-4 bit in the "Set Burst with Wrap (77h)" instruction. This setting will remain unchanged when the device is switched from Standard SPI mode to QPI mode.

The default "Wrap Length" after a power up or a Reset instruction is 8 bytes, the default number of dummy clocks is 10 which includes "Continuous Read Mode" byte M7-0. The number of dummy clocks is only programmable for "Fast Read (0Bh)", "4IO Read (EBh)" & "Burst Read with Wrap (0Ch)" instructions in the QPI mode. Whenever the device is switched from SPI mode to QPI mode, the number of dummy clocks should be set again, prior to any 0Bh, EBh or 0Ch instructions.

P5-P4	Dummy Clocks	P1-P0	Wrap Length
0,0	10	0,0	8-byte
0,1	4	0,1	16-byte
1,0	6	1,0	32-byte
1,1	8	1,1	64-byte

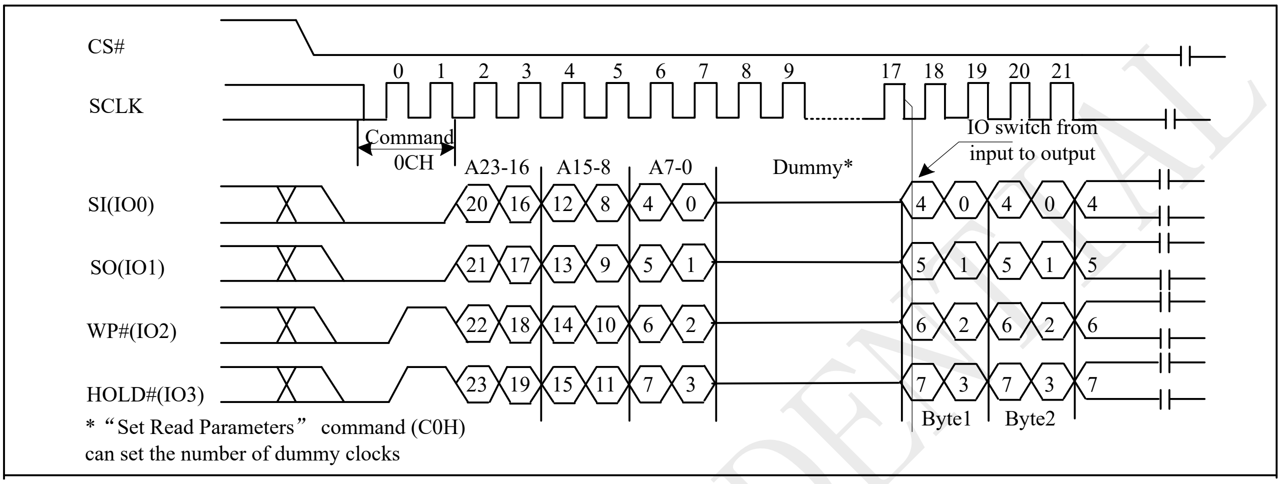
Figure 10-17 Set Read Parameters Sequence (QPI)



10.18 Burst Read with Wrap (0Ch)

The “Burst Read with Wrap (0CH)” command provides an alternative way to perform the read operation with “Wrap Around” in QPI mode. This command is similar to the “Fast Read (0BH)” command in QPI mode, except the addressing of the read operation will “Wrap Around” to the beginning boundary of the “Wrap Around” once the ending boundary is reached. The “Wrap Length” and the number of dummy clocks can be configured by the “Set Read Parameters (C0H)” command.

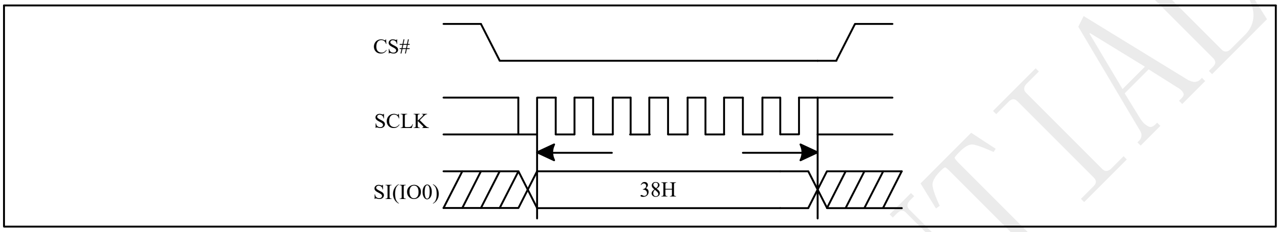
Figure 10-18 Burst Read with Wrap Sequence (QPI)



10.19 Enable QPI (38H)

The device support both Standard/Dual/Quad SPI and QPI mode. The “Enable QPI (38H)” command can switch the device from SPI mode to QPI mode. See the command Table 2a for all support QPI commands. In order to switch the device to QPI mode, the Quad Enable (QE) bit in Status Register-1 must be set to 1 first, and “Enable QPI (38H)” command must be issued. If the QE bit is 0, the “Enable QPI (38H)” command will be ignored and the device will remain in SPI mode. When the device is switched from SPI mode to QPI mode, the existing Write Enable Latch and Program/Erase Suspend status, and the Wrap Length setting will remain unchanged.

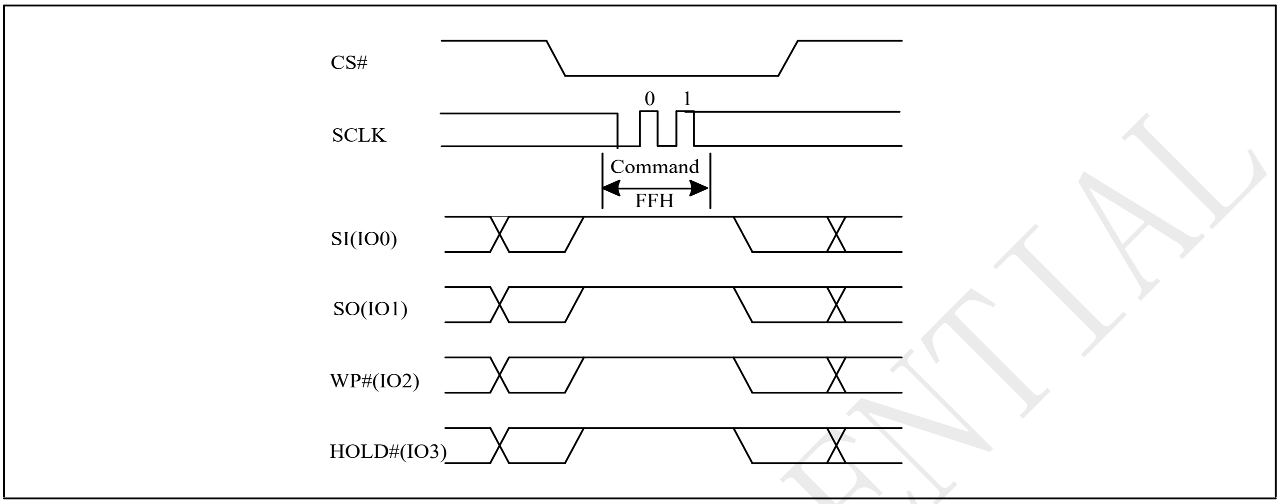
Figure 10-19 Enable QPI Sequence (38H)



10.20 Disable QPI (FFH)

To exit the QPI mode and return to Standard/Dual/Quad SPI mode, the “Disable QPI (FFH)” command must be issued. When the device is switched from QPI mode to SPI mode, the existing Write Enable Latch and Program/Erase Suspend status, and the Wrap Length setting will remain unchanged.

Figure 10-20 Disable QPI Sequence (QPI)



10.21 Page Erase (PE)

The Page Erase (PE) instruction is for erasing the data of the chosen Page to be "1". A Write Enable (WREN) instruction must execute to set the Write Enable Latch (WEL) bit before sending the Page Erase (PE).

To perform a Page Erase with the standard page size (256 bytes), an instruction of 81h must be clocked into the device followed by three address bytes comprised of 2 page address bytes that specify the page in the main memory to be erased, and 1 dummy byte.

The sequence of issuing PE instruction is: CS# goes low → sending PE instruction code→ 3-byte address on SI → CS# goes high.

Figure 10-21 Page Erase Sequence (Command 81)

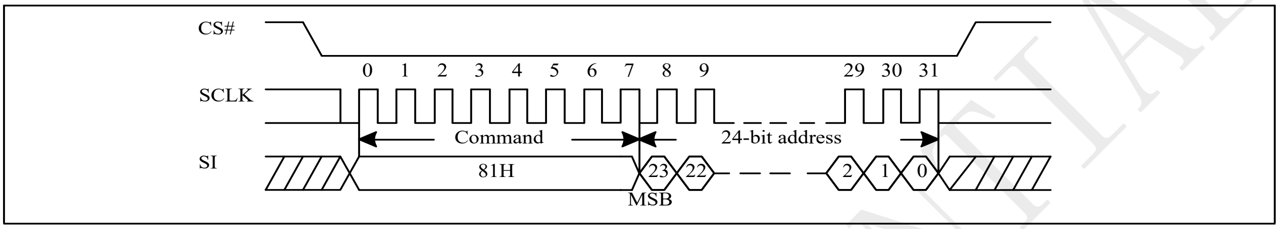
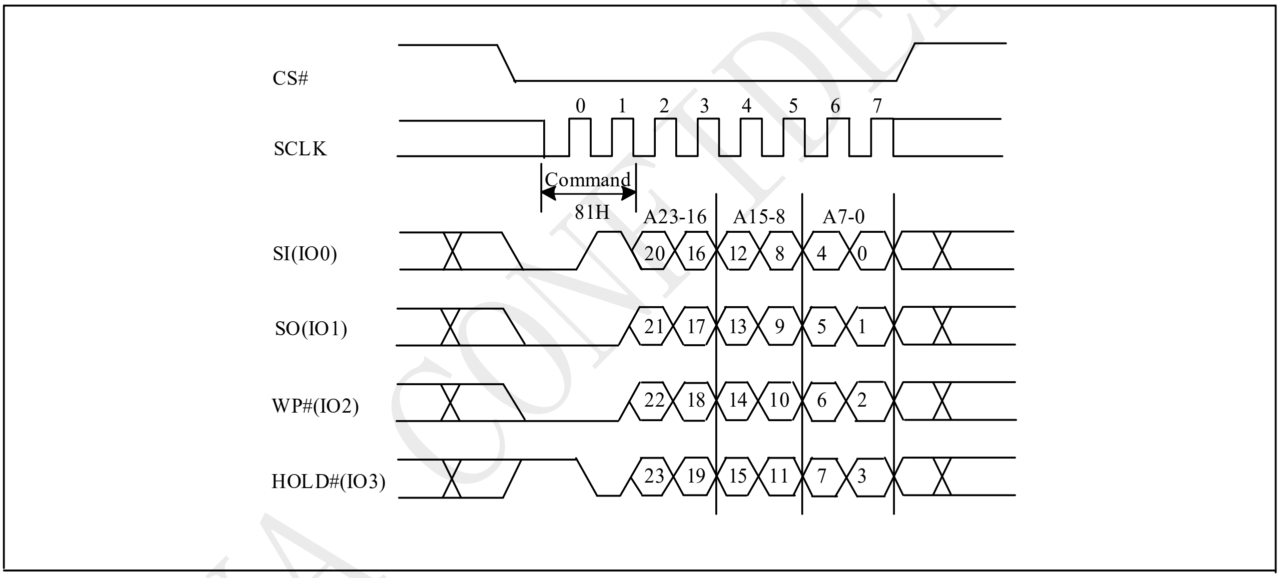


Figure 10-21a Page Erase Sequence (QPI)



10.22 Sector Erase (SE)

The Sector Erase (SE) instruction is for erasing the data of the chosen sector to be "1". A Write Enable (WREN) instruction must execute to set the Write Enable Latch (WEL) bit before sending the Sector Erase (SE). Any address of the sector is a valid address for Sector Erase (SE) instruction. The CS# must go high exactly at the byte boundary (the latest eighth of address byte been latched-in); otherwise, the instruction will be rejected and not executed.

Address bits [Am-A12] (Am is the most significant address) select the sector address.

The sequence of issuing SE instruction is: CS# goes low → sending SE instruction code→ 3-byte address on SI → CS# goes high. The SIO[3:1] are don't care.

Figure 10-22 Sector Erase (SE) Sequence (Command 20)

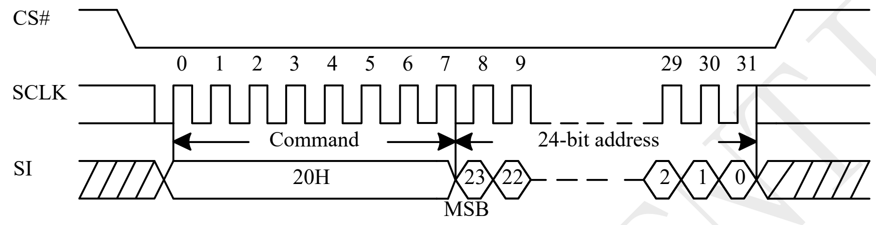
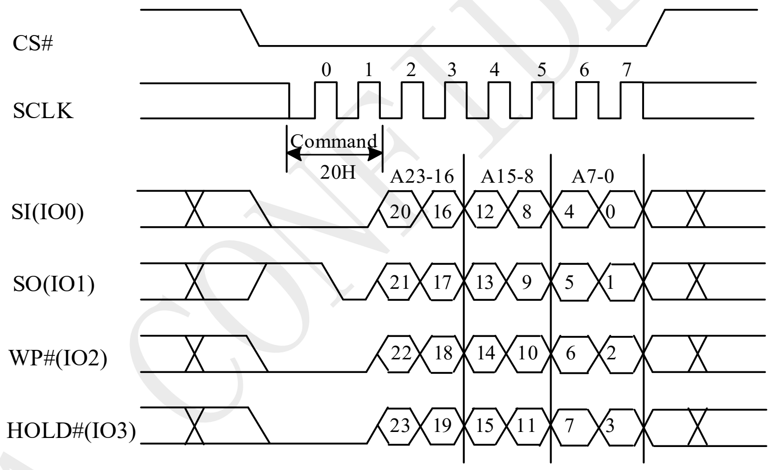


Figure 10-22a Sector Erase (SE) Sequence (QPI)



The self-timed Sector Erase Cycle time (tSE) is initiated as soon as Chip Select (CS#) goes high. The Write in progress (WIP) bit still can be check out during the Sector Erase cycle is in progress. The WIP sets 1 during the tSE timing, and sets 0 when Sector Erase Cycle is completed, and the Write Enable Latch (WEL) bit is reset. If the sector is protected by BP4, BP3, BP2, BP1, BP0 bits, the Sector Erase (SE) instruction will not be executed on the sector.

10.23 Block Erase (BE32K)

The Block Erase (BE32K) instruction is for erasing the data of the chosen block to be "1". The instruction is used for 32K-byte block erase operation. A Write Enable (WREN) instruction must be executed to set the Write Enable Latch (WEL) bit before sending the Block Erase (BE32K). Any address of the block is a valid address for Block Erase (BE32K) instruction. The CS# must go high exactly at the byte boundary (the least significant bit of address byte has been latched-in); otherwise, the instruction will be rejected and not executed.

The sequence of issuing BE32K instruction is: CS# goes low → sending BE32K instruction code → 3-byte address on SI → CS# goes high. The SIO[3:1] are don't care.

The self-timed Block Erase Cycle time (tBE32K) is initiated as soon as Chip Select (CS#) goes high. The Write in Progress (WIP) bit still can be checked while the Block Erase cycle is in progress. The WIP sets during the tBE32K timing, and clears when Block Erase Cycle is completed, and the Write Enable Latch (WEL) bit is cleared. If the block is protected by BP4, BP3, BP2, BP1, BP0 bits, the array data will be protected (no change) and the WEL bit still be reset.

Figure 10-23 Block Erase 32K(BE32K) Sequence (Command 52)

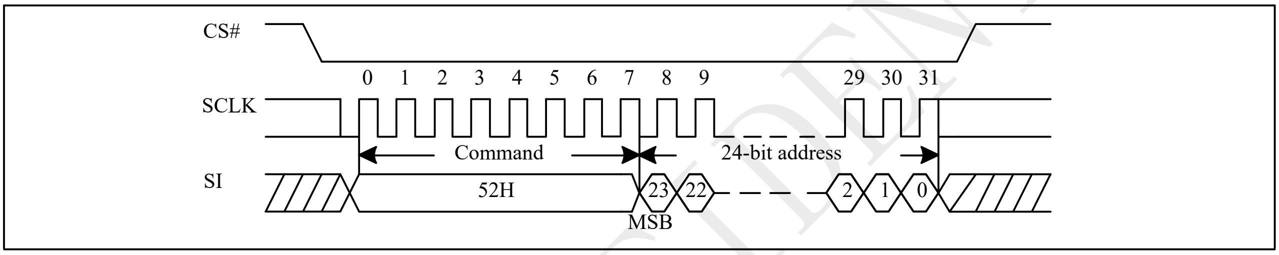
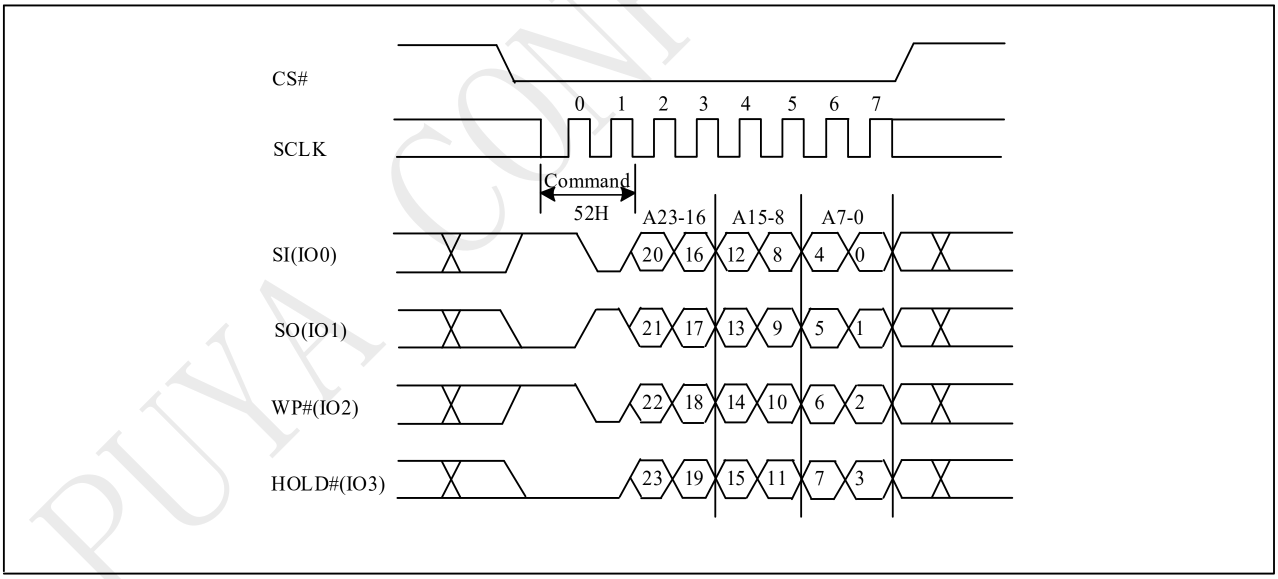


Figure 10-23a Block Erase 32K(BE32K) Sequence (QPI)



10.24 Block Erase (BE)

The Block Erase (BE) instruction is for erasing the data of the chosen block to be "1". The instruction is used for 64K-byte block erase operation. A Write Enable (WREN) instruction must execute to set the Write Enable Latch (WEL) bit before sending the Block Erase (BE). Any address of the block is a valid address for Block Erase (BE) instruction. The CS# must go high exactly at the byte boundary (the latest eighth of address byte been latched-in); otherwise, the instruction will be rejected and not executed.

The sequence of issuing BE instruction is: CS# goes low→ sending BE instruction code→ 3-byte address on SI→CS# goes high. The SIO[3:1] are "don't care".

The self-timed Block Erase Cycle time (tBE) is initiated as soon as Chip Select (CS#) goes high. The Write in Progress (WIP) bit still can be checked during the Block Erase cycle is in progress. The WIP sets 1 during the tBE timing, and sets 0 when Block Erase Cycle is completed, and the Write Enable Latch (WEL) bit is reset. If the block is protected by BP4, BP3, BP2, BP1, BP0 bits, the Block Erase (BE) instruction will not be executed on the block.

Figure 10-24 Block Erase (BE) Sequence (Command D8)

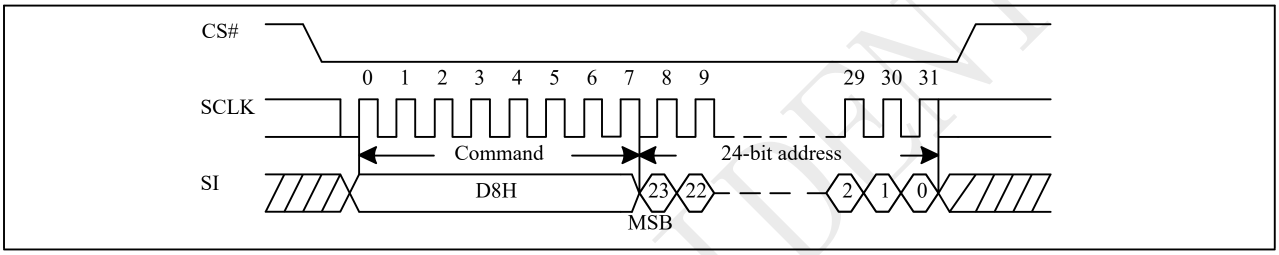
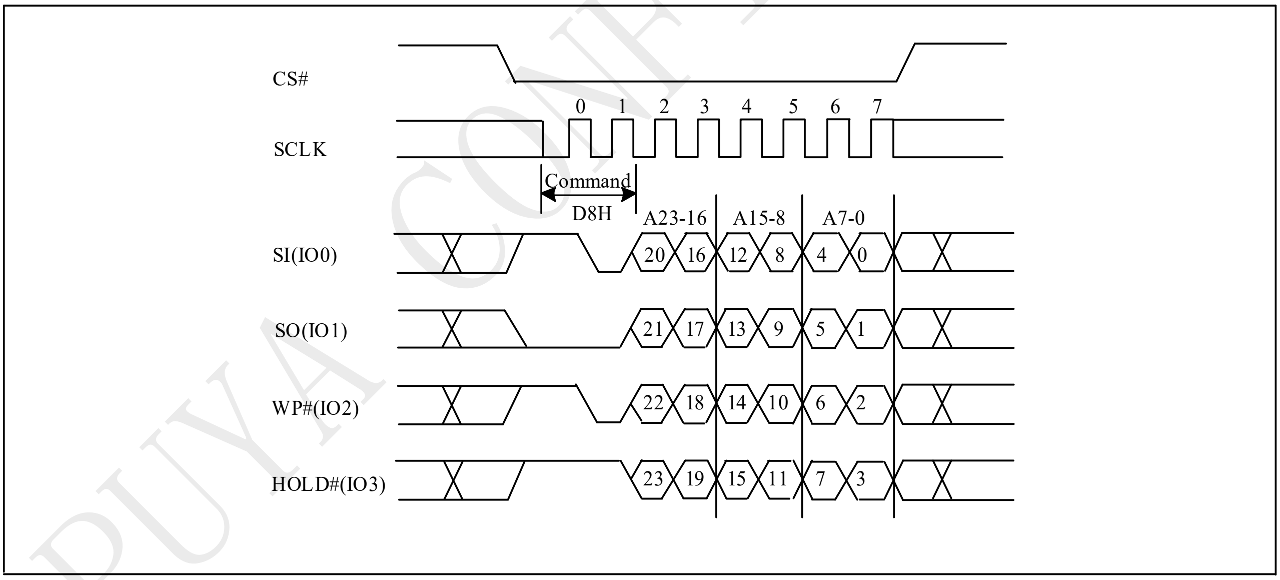


Figure 10-24a Block Erase (BE) Sequence (QPI)



10.25 Chip Erase (CE)

The Chip Erase (CE) instruction is for erasing the data of the whole chip to be "1". A Write Enable (WREN) instruction must execute to set the Write Enable Latch (WEL) bit before sending the Chip Erase (CE). The CS# must go high exactly at the byte boundary (the latest eighth of address byte been latched-in); otherwise, the instruction will be rejected and not executed.

The sequence of issuing CE instruction is: CS# goes low→ sending CE instruction code→ CS# goes high. The self-timed Chip Erase Cycle time (tCE) is initiated as soon as Chip Select (CS#) goes high. The Write in Progress (WIP) bit still can be checked during the Chip Erase cycle is in progress. The WIP sets 1 during the tCE timing, and sets 0 when Chip Erase Cycle is completed, and the Write Enable Latch (WEL) bit is reset. If the chip is protected by BP4,BP3, BP2, BP1, BP0 bits, the Chip Erase (CE) instruction will not be executed. It will be only executed when all Block Protect(BP4, BP3, BP2, BP1, BP0) are set to “None protected”.

Figure 10-25 Chip Erase (CE) Sequence (Command 60 or C7)

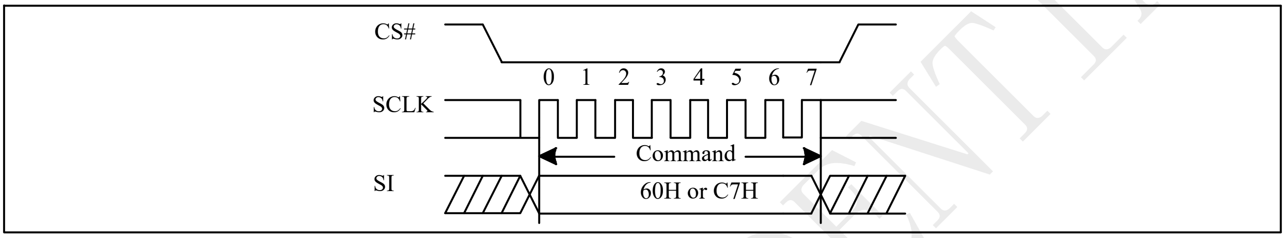
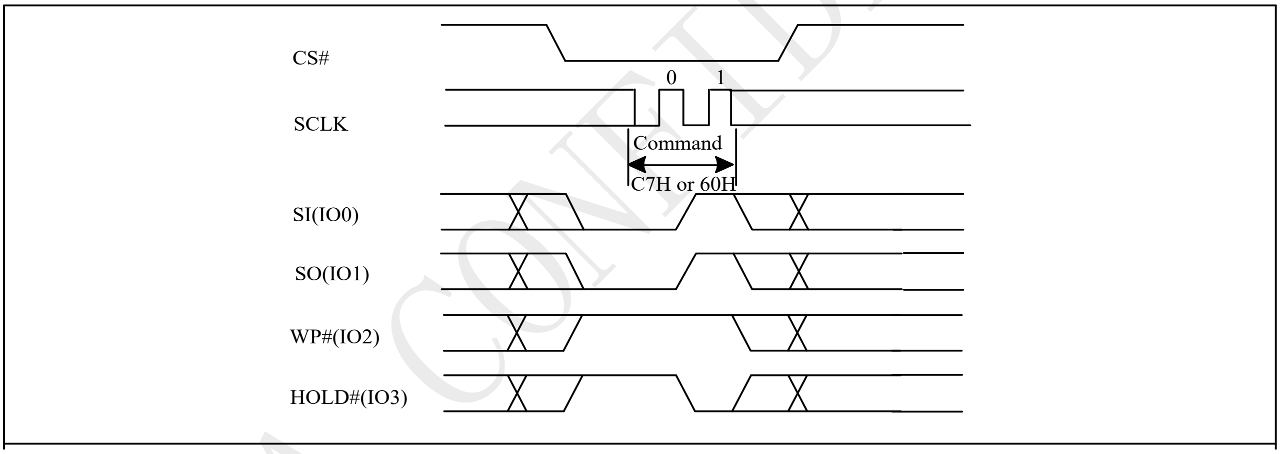


Figure 10-25a Chip Erase (CE) Sequence (QPI)



10.26 Page Program (PP)

The Page Program (PP) instruction is for programming the memory to be "0". A Write Enable (WREN) instruction must execute to set the Write Enable Latch (WEL) bit before sending the Page Program (PP). The device programs only the last 256 data bytes sent to the device. If the entire 256 data bytes are going to be programmed, A7-A0 (The eight least significant address bits) should be set to 0. If the eight least significant address bits (A7-A0) are not all 0, all transmitted data going beyond the end of the current page are programmed from the start address of the same page (from the address A7-A0 are all 0). If more than 256 bytes are sent to the device, the data of the last 256-byte is programmed at the request page and previous data will be disregarded. If less than 256 bytes are sent to the device, the data is programmed at the requested address of the page.

Each page programming operation should be done only once after erase operation. It is possible to program from one byte up to a page size in each Page programming operation.

For the very best performance, programming should be done in full pages of 256 bytes aligned on 256 byte boundaries with each Page being programmed only once.

The sequence of issuing PP instruction is: CS# goes low→ sending PP instruction code→ 3-byte address on SI→ at least 1-byte on data on SI→ CS# goes high.

The CS# must be kept low during the whole Page Program cycle; The CS# must go high exactly at the byte boundary (the latest eighth bit of data being latched in), otherwise the instruction will be rejected and will not be executed.

The self-timed Page Program Cycle time (tPP) is initiated as soon as Chip Select (CS#) goes high. The Write in Progress (WIP) bit still can be checked during the Page Program cycle is in progress. The WIP sets 1 during the tPP timing, and sets 0 when Page Program Cycle is completed, and the Write Enable Latch (WEL) bit is reset. If the page is protected by BP4, BP3, BP2, BP1, BP0 bits, the Page Program (PP) instruction will not be executed. The SIO[3:1] are "don't care".

Figure 10-26 Page Program (PP) Sequence (Command 02)

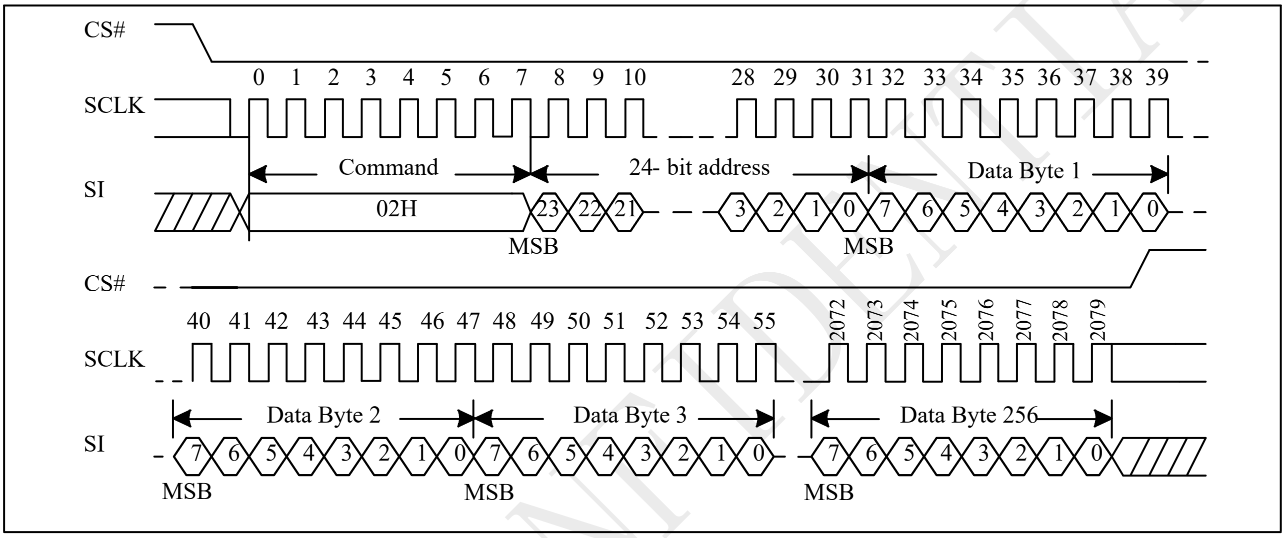
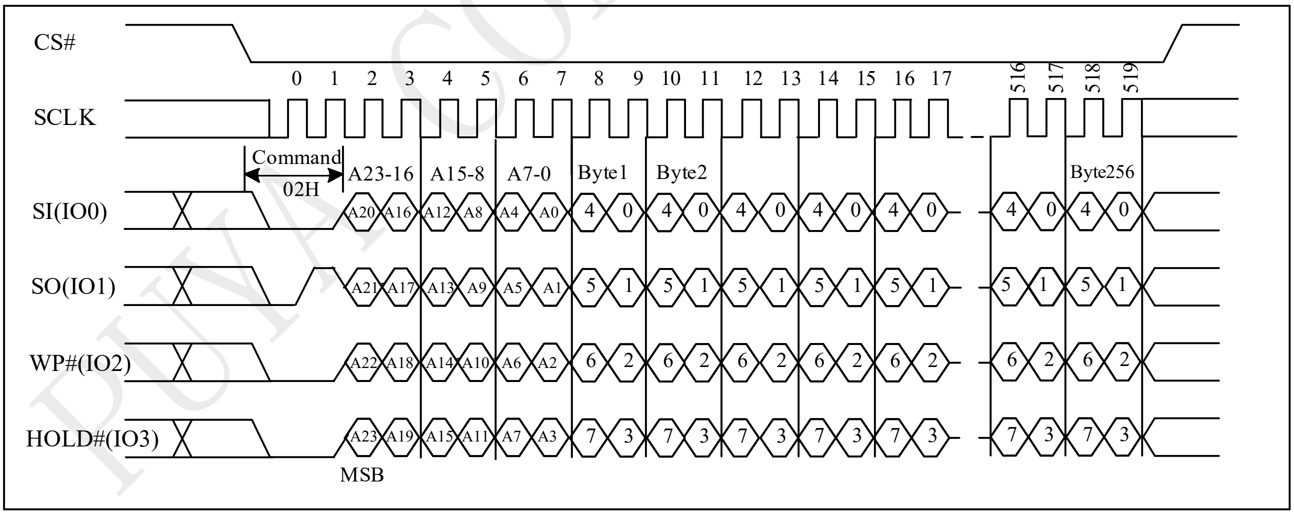


Figure 10-26a Page Program (PP) Sequence (QPI)

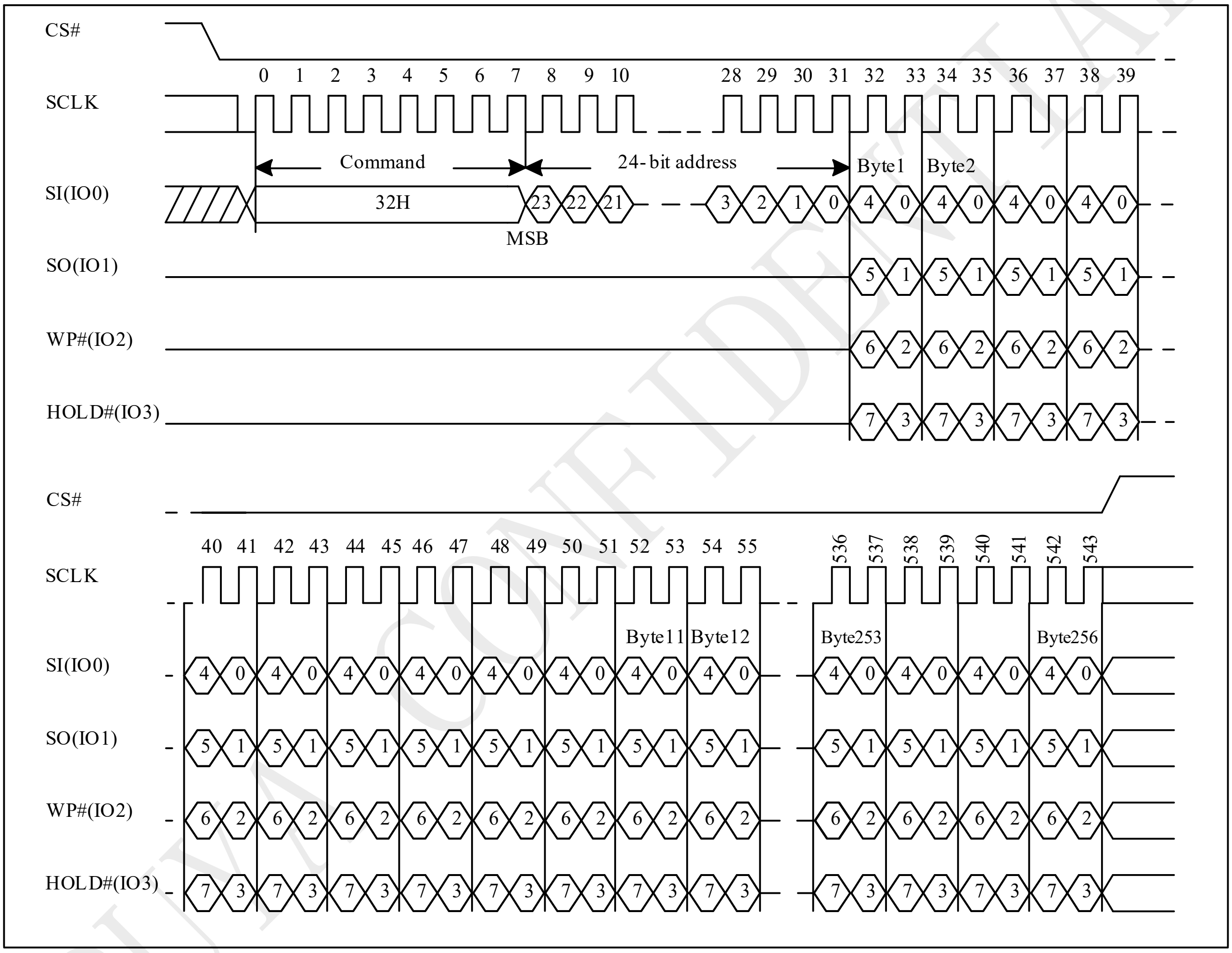


10.27 Quad Page Program (QPP)

The Quad Page Program (QPP) instruction is for programming the memory to be "0". A Write Enable (WREN)instruction must execute to set the Write Enable Latch (WEL) bit and Quad Enable (QE) bit must be set to "1" before sending the Quad Page Program (QPP). The Quad Page Programming takes four pins: SIO0, SIO1, SIO2, and SIO3 as data input, which can improve programmer performance and the effectiveness of application. The QPP operation frequency supports as fast as fQPP. The other function descriptions are as same as standard page program.

The sequence of issuing QPP instruction is: CS# goes low→ sending QPP instruction code→ 3-byte address on SIO0 → at least 1-byte on data on SIO[3:0]→CS# goes high.

Figure 10-27 Quad Page Program (QPP) Sequence (Command 32)



10.28 Erase Security Registers (ERSCUR)

The product provides 3*512-byte Security Registers which can be erased and programmed individually. These registers may be used by the system manufacturers to store security and other important information separately from the main memory array.

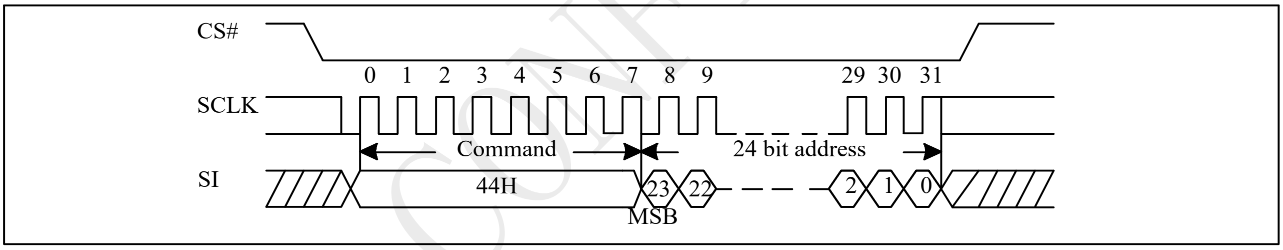
The Erase Security Registers command is similar to Sector/Block Erase command. A Write Enable (WREN) command must previously have been executed to set the Write Enable Latch (WEL) bit.

The Erase Security Registers command sequence: CS# goes low → sending ERSCUR instruction →sending 24 bit address → CS# goes high.

CS# must be driven high after the eighth bit of the command code has been latched in; otherwise the Erase Security Registers command is not executed. As soon as CS# is driven high, the self-timed Erase Security Registers cycle (whose duration is tSE) is initiated. While the Erase Security Registers cycle is in progress, the Status Register may be read to check the value of the Write in Progress (WIP) bit. The Write in Progress (WIP) bit is 1 during the self-timed Erase Security Registers cycle, and is 0 when it is completed. The Security Registers Lock Bit (LB3-1) in the Status Register can be used to OTP protect the security registers. Once the LB bit is set to 1, the Security Registers will be permanently locked; the Erase Security Registers command will be ignored.

Address	A23-16	A15-12	A11-9	A8-0
Security Register #1	00H	0001	000	Byte Address
Security Register #2	00H	0010	000	Byte Address
Security Register #3	00H	0011	000	Byte Address

Figure 10-28 Erase Security Registers (ERSCUR) Sequence (Command 44)



10.29 Program Security Registers (PRSCUR)

The product provides 3*512-byte Security Registers which can be programmed 256Byte per time individually. The Program Security Registers command is similar to the Page Program command. It allows from 1 to 256 bytes Security Registers data to be programmed. A Write Enable (WREN) command must previously have been executed to set the Write Enable Latch (WEL) bit before sending the Program Security Registers command.

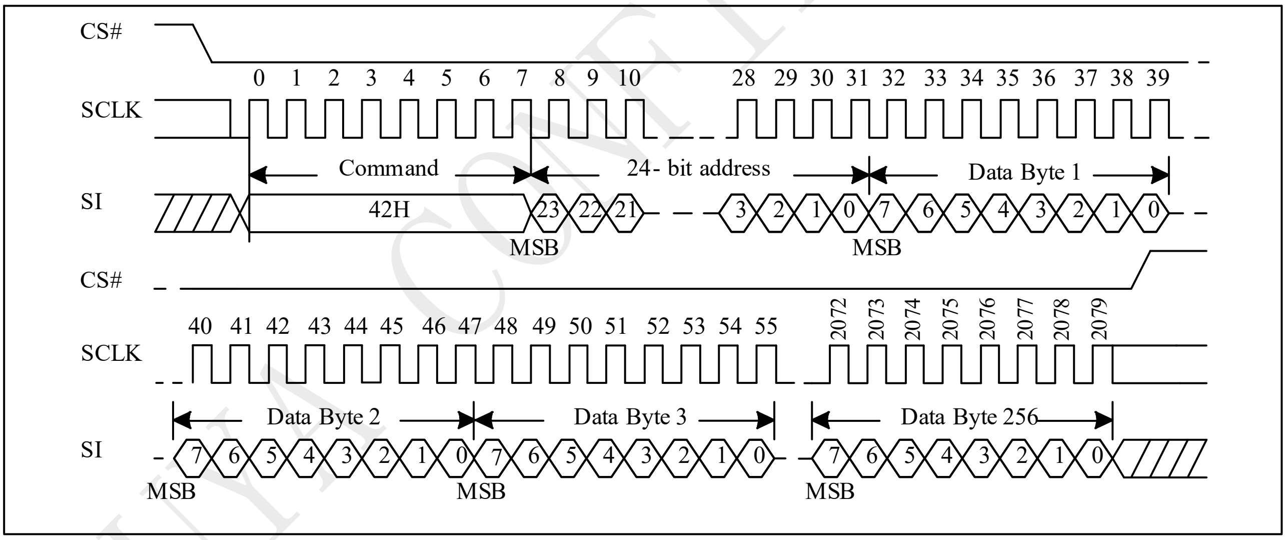
The Program Security Registers command sequence: CS# goes low → sending PRSCUR instruction →sending 24 bit address → sending at least one byte data → CS# goes high.

As soon as CS# is driven high, the self-timed Program Security Registers cycle (whose duration is tPP) is initiated. While the Program Security Registers cycle is in progress, the Status Register may be read to check the value of the Write in Progress (WIP) bit. The Write in Progress (WIP) bit is 1 during the self-timed Program Security Registers cycle, and is 0 when it is completed.

If the Security Registers Lock Bit (LB3-1) is set to 1, the Security Registers will be permanently locked. Program Security Registers command will be ignored.

Address	A23-16	A15-12	A11-9	A8	A7-0
Security Register #1	00H	0001	000	0/1	Byte Address
Security Register #2	00H	0010	000	0/1	Byte Address
Security Register #3	00H	0011	000	0/1	Byte Address

Figure 10-29 Program Security Registers (PRSCUR) Sequence (Command 42)



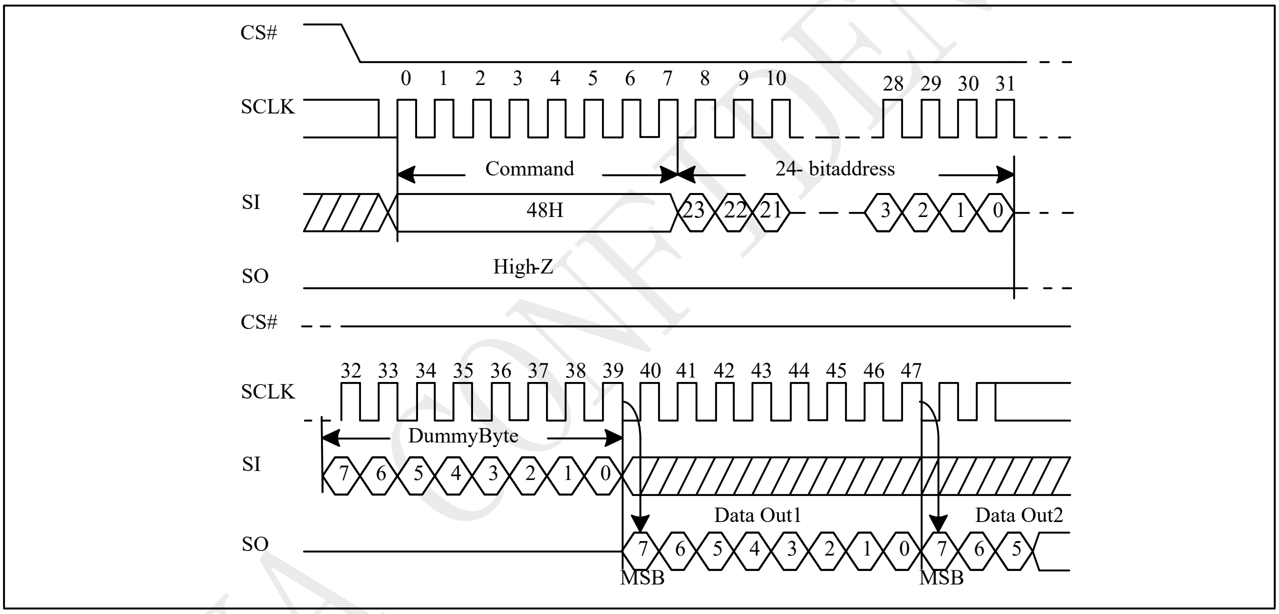
10.30 Read Security Registers (RDSCUR)

The Read Security Registers command is similar to Fast Read command. The command is followed by a 3-byte address (A23-A0) and a dummy byte, each bit being latched-in during the rising edge of SCLK. Then the memory content, at that address, is shifted out on SO, each bit being shifted out, at a Max frequency fC, during the falling edge of SCLK. The first byte addressed can be at any location. The address is automatically incremented to the next higher address after each byte of data is shifted out. Once the A8-A0 address reaches the last byte of the register (Byte 1FFH), it will reset to 00H, the command is completed by driving CS# high.

The sequence of issuing RDSCUR instruction is: CS# goes low → sending RDSCUR instruction → sending 24 bit address → 8 bit dummy byte → Security Register data out on SO → CS# goes high.

Address	A23-16	A15-12	A11-9	A8-0
Security Register #1	00H	0001	000	Byte Address
Security Register #2	00H	0010	000	Byte Address
Security Register #3	00H	0011	000	Byte Address

Figure 10-30 Read Security Registers (RDSCUR) Sequence (Command 48)



10.31 Deep Power-down (DP)

The Deep Power-down (DP) instruction is for setting the device on the minimizing the power consumption (to entering the Deep Power-down mode), the standby current is reduced from ISB1 to ISB2). The Deep Power-down mode requires the Deep Power-down (DP) instruction to enter, during the Deep Power-down mode, the device is not active and all Write/Program/Erase instruction are ignored.

The sequence of issuing DP instruction is: CS# goes low→ sending DP instruction code→ CS# goes high.

Once the DP instruction is set, all instruction will be ignored except the Release from Deep Power-down mode (RDP), Read Electronic Signature (RES) instruction, and soft reset instruction (66H, 99H). (RES instruction to allow the ID been read out). When Power- down, the deep power-down mode automatically stops, and when power-up, the device automatically is in standby mode. For RDP instruction the CS# must go high exactly at the byte boundary (the latest eighth bit of instruction code been latched-in); otherwise, the instruction will not be executed. As soon as Chip Select (CS#) goes high, a delay of tDP is required before entering the Deep Power-down mode and reducing the current to ISB2.

Figure 10-31 Deep Power-down (DP) Sequence (Command B9)

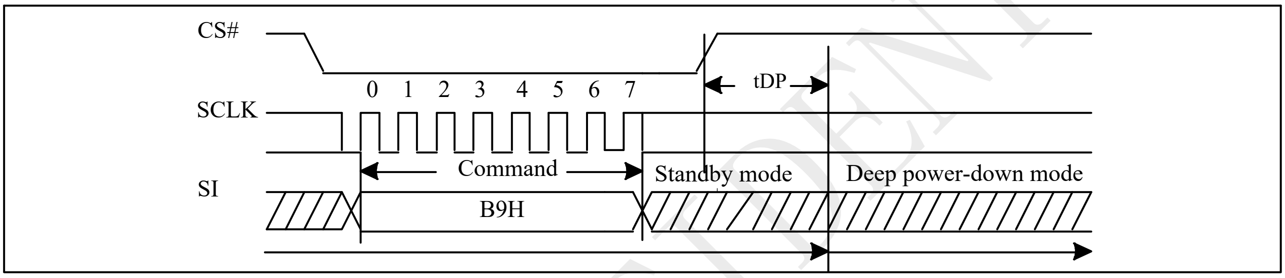
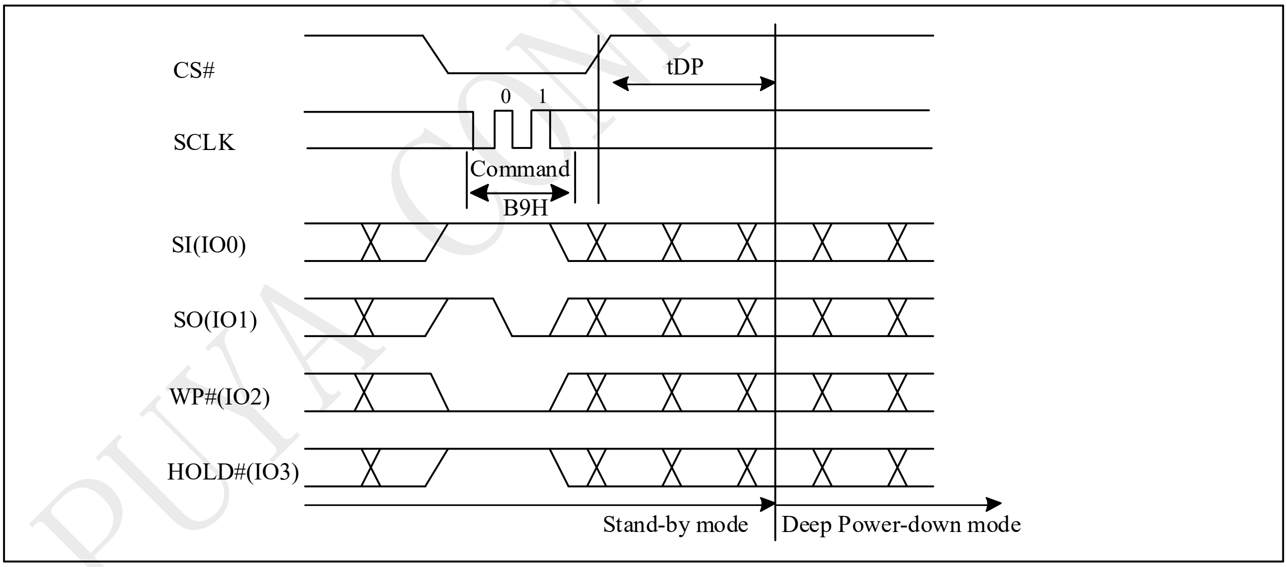


Figure 10-31a Deep Power-down (DP) Sequence (QPI)



10.32 Release form Deep Power-Down (RDP), Read Electronic Signature (RES)

The Release from Deep Power-down (RDP) instruction is terminated by driving Chip Select (CS#) High. When Chip Select (CS#) is driven high, the device is put in the Stand-by Power mode. If the device was not previously in the Deep Power-down mode, the transition to the Stand-by Power mode is immediate. If the device was previously in the Deep Power-down mode, though, the transition to the Stand-by Power mode is delayed by tRES2, and Chip Select (CS#) must remain High for at least tRES2(max). Once in the Stand-by Power mode, the device waits to be selected, so that it can receive, decode and execute instructions.

RES instruction is for reading out the old style of 8-bit Electronic Signature, whose values are shown as table of ID Definitions. This is not the same as RDID instruction. It is not recommended to use for new design. For new design, please use RDID instruction. Even in Deep power-down mode, the RDP and RES are also allowed to be executed, only except the device is in progress of program/erase/write cycle; there's no effect on the current program/erase/ write cycle in progress.

The RES instruction is ended by CS# goes high after the ID been read out at least once. The ID outputs repeatedly if continuously send the additional clock cycles on SCLK while CS# is at low. If the device was not previously in Deep Power-down mode, the device transition to standby mode is immediate. If the device was previously in Deep Power-down mode, there's a delay of tRES2 to transit to standby mode, and CS# must remain to high at least tRES2 (max). Once in the standby mode, the device waits to be selected, so it can be receive, decode, and execute instruction.

The RDP instruction is for releasing from Deep Power-Down Mode.

Figure 10-32 Read Electronic Signature (RES) Sequence (Command AB)

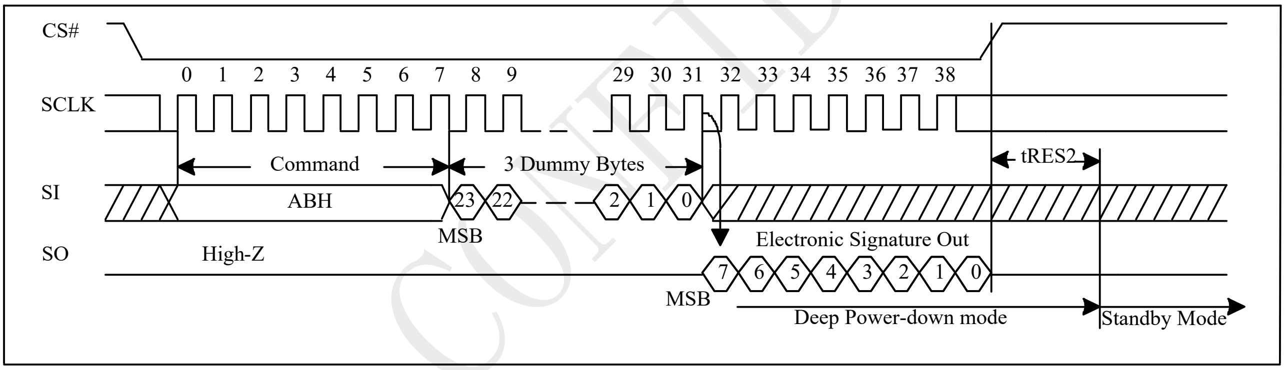


Figure 10-32a Read Electronic Signature (RES) Sequence (QPI)

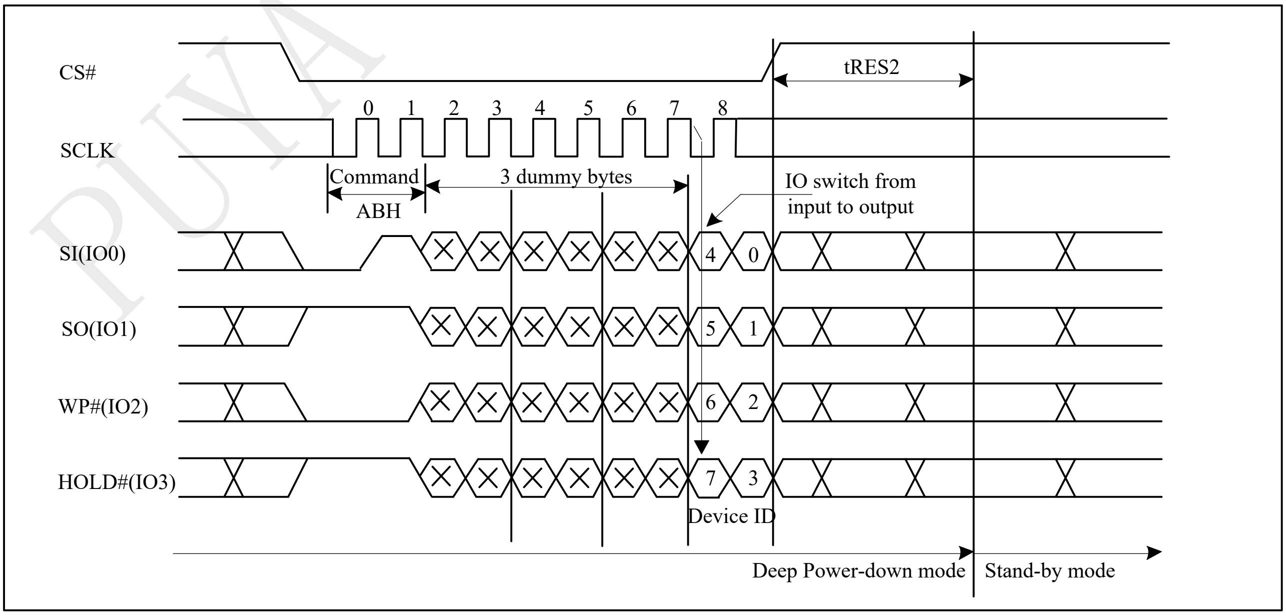


Figure 10-32b Release from Deep Power-down (RDP) Sequence (Command AB)

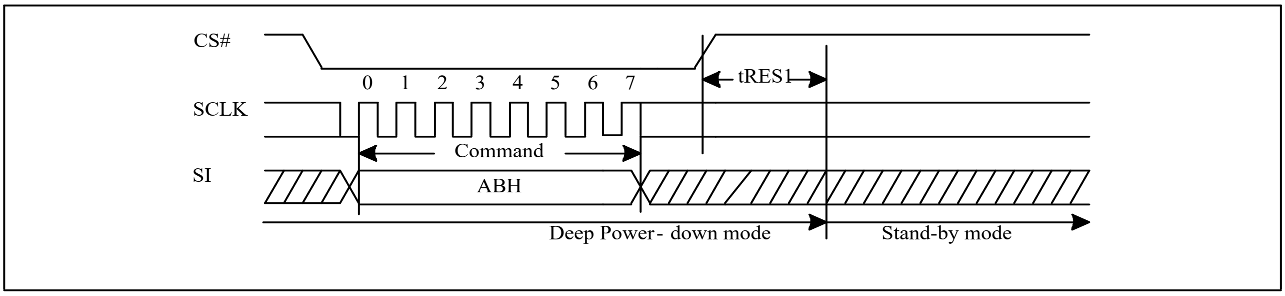
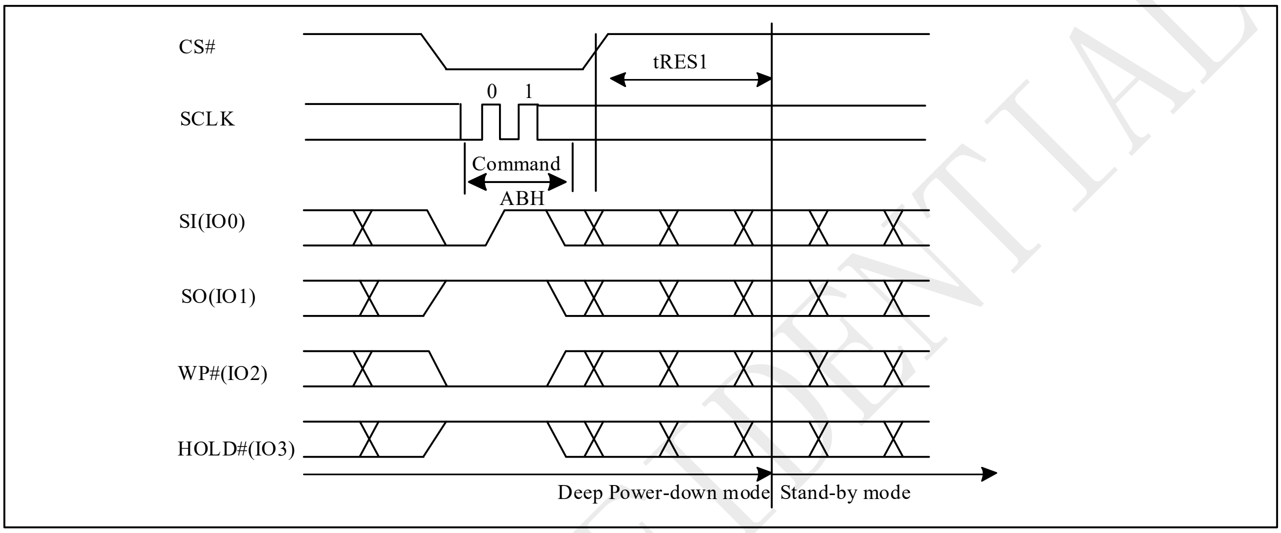


Figure 10-32c Release from Deep Power-down (RDP) Sequence (QPI)



10.33 Read Electronic Manufacturer ID & Device ID (REMS)

The REMS instruction returns both the JEDEC assigned manufacturer ID and the device ID. The Device ID values are listed in "Table ID Definitions".

The REMS instruction is initiated by driving the CS# pin low and sending the instruction code "90h" followed by two dummy bytes and one address byte (A7~A0). After which the manufacturer ID for PUYA (85h) and the device ID are shifted out on the falling edge of SCLK with the most significant bit (MSB) first.The manufacturer ID will be output first, followed by the device ID. While CS# is low, the manufacturer and device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving CS# high.

Figure 10-33 Read Electronic Manufacturer & Device ID (REMS) Sequence (Command 90)

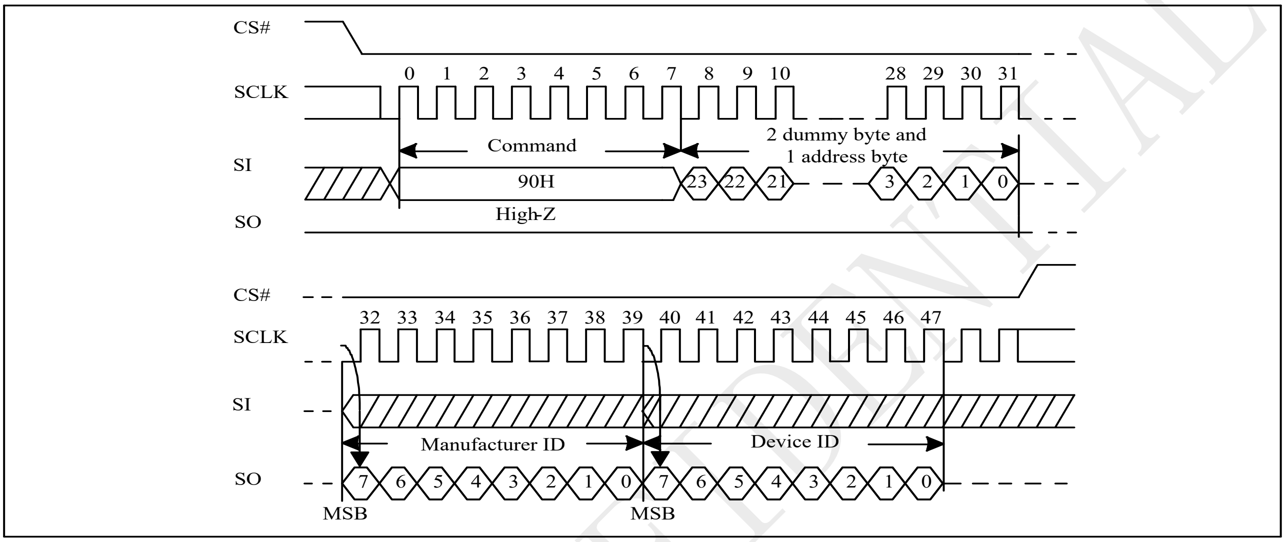
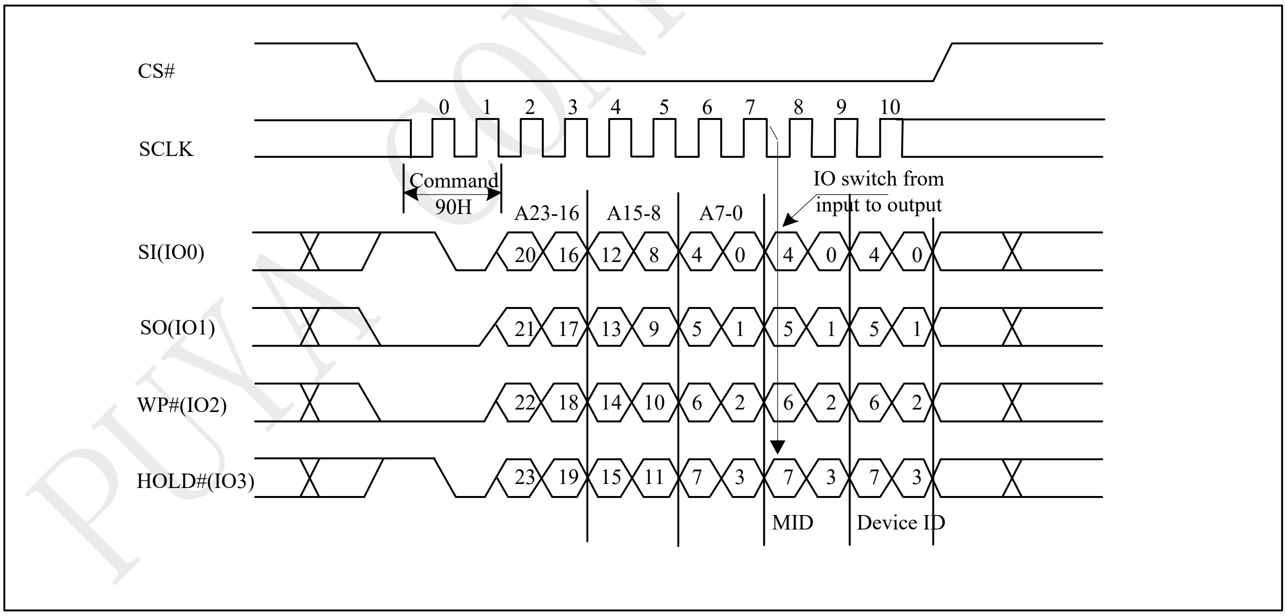


Figure 10-33a Read Electronic Manufacturer & Device ID (REMS) Sequence (QPI)

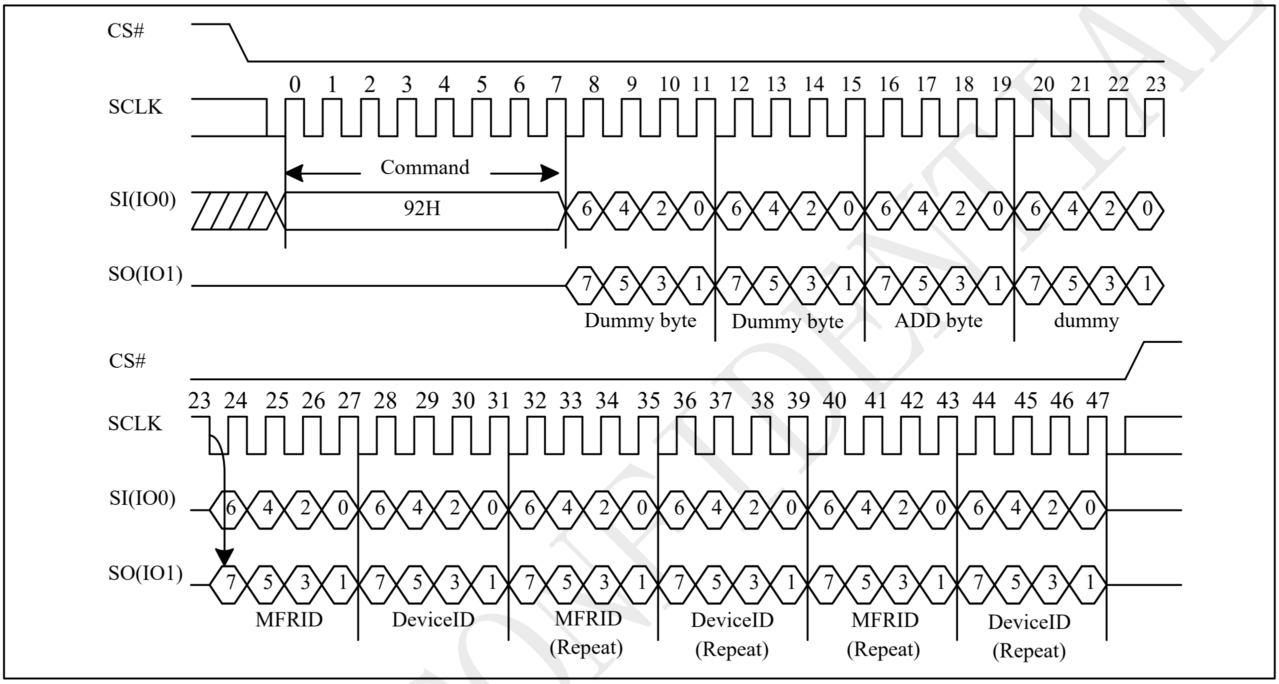


10.34 Dual I/O Read Electronic Manufacturer ID & Device ID (DREMS)

The DREMS instruction is similar to the REMS command and returns the JEDEC assigned manufacturer ID which takes two pins: SIO0, SIO1 as address input and ID output I/O

The instruction is initiated by driving the CS# pin low and shift the instruction code "92h" followed by two dummy bytes and one bytes address (A7~A0). After which, the Manufacturer ID for PUYA (85h) and the Device ID are shifted out on the falling edge of SCLK with most significant bit (MSB) first. The manufacturer ID will be output first, followed by the device ID. The Manufacturer and Device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving CS# high.

Figure 10-34 DUAL I/O Read Electronic Manufacturer & Device ID (DREMS) Sequence (Command 92)

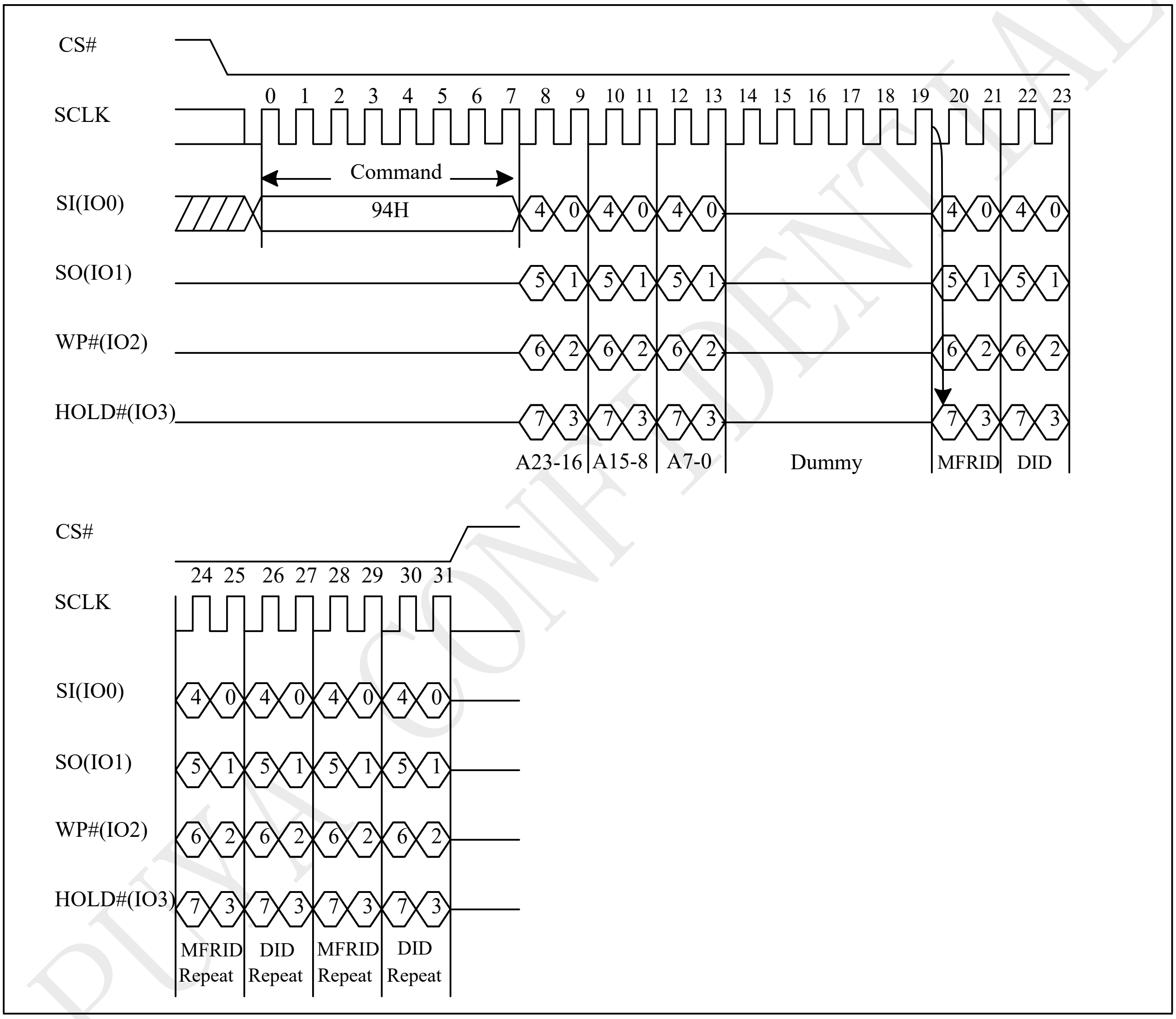


10.35 Quad I/O Read Electronic Manufacturer ID & Device ID (QREMS)

The QREMS instruction is similar to the REMS command and returns the JEDEC assigned manufacturer ID which takes four pins: SIO0, SIO1, SIO2, SIO3 as address input and ID output I/O

The instruction is initiated by driving the CS# pin low and shift the instruction code "94h" followed by two dummy bytes and one byte’s address (A7~A0). After which, the Manufacturer ID for PUYA (85h) and the Device ID are shifted out on the falling edge of SCLK with most significant bit (MSB) first. The manufacturer ID will be output first, followed by the device ID. The Manufacturer and Device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving CS# high.

Figure 10-35 QUAD I/O Read Electronic Manufacturer & Device ID (QREMS) Sequence (Command 94)



10.36 Read Identification (RDID)

The RDID instruction is for reading the manufacturer ID of 1-byte and followed by Device ID of 2-byte. The PUYA Manufacturer ID and Device ID are list as "Table ID Definitions”.

The sequence of issuing RDID instruction is: CS# goes low→ sending RDID instruction code → 24-bits ID data out on SO→ to end RDID operation can use CS# to high at any time during data out. While Program /Erase operation is in progress, it will not decode the RDID instruction, so there's no effect on the cycle of program/erase operation which is currently in progress. When CS# goes high, the device is at standby stage.

Figure 10-36 Read Identification (RDID) Sequence (Command 9F)

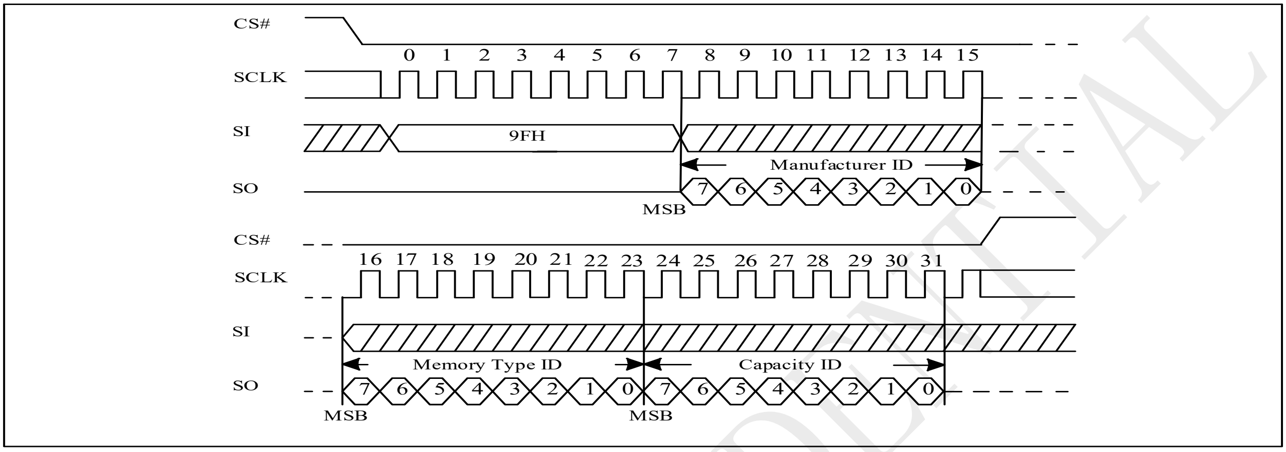


Figure 10-41a Read Identification (RDID) Sequence (QPI)

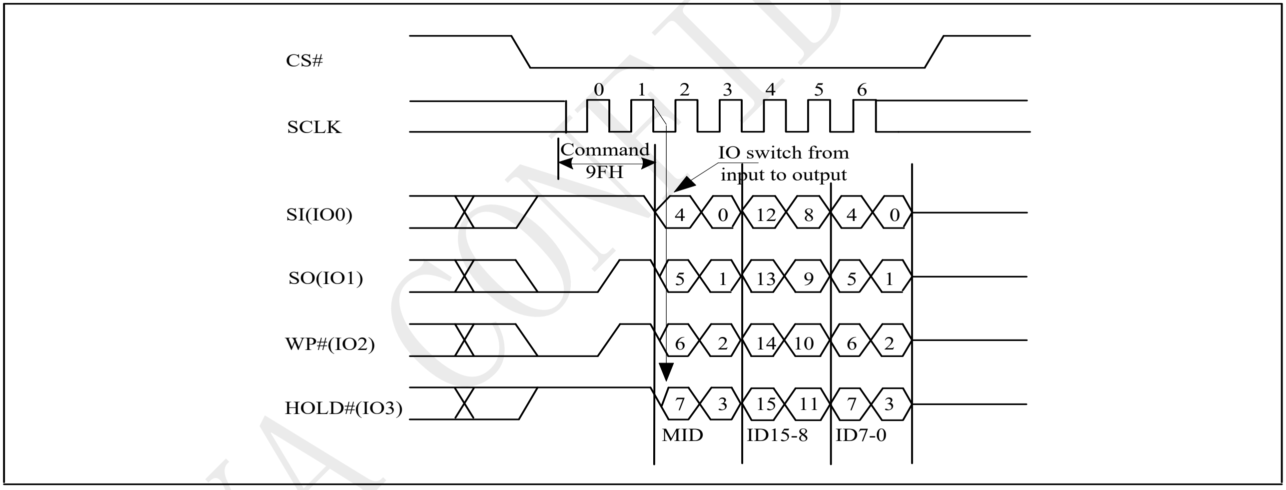


Table ID Definitions

P25Q40TU	RDID command	manufacturer ID	memory type	memory density
		85	60	13
	RES command	electronic ID		
		12		
	REMS command	manufacturer ID		device ID
		85		12

P25Q20TU	RDID command	manufacturer ID	memory type	memory density
		85	60	12
	RES command	electronic ID		
		11		
	REMS command	manufacturer ID		device ID
		85		11

10.37 Program/Erase Suspend/Resume

The Suspend instruction interrupts a Page Program, Page Erase, Sector Erase, or Block Erase operation to allow access to the memory array. After the program or erase operation has entered the suspended state, the memory array can be read except for the page(s) being programmed or the page(s) or sector or block being erased.

Readable Area of Memory While a Program or Erase Operation is Suspended

Suspended Operation	Readable Region of Memory Array
Page(s) Program	All but the Page(s) being programmed
Page(s) Erase	All but the Page(s) being erased
Sector Erase(4KB)	All but the 4KB Sector being erased
Block Erase(32KB)	All but the 32KB Block being erased
Block Erase(64KB)	All but the 64KB Block being erased

When the Serial NOR Flash receives the Suspend instruction, there is a latency of tPSL or tESL before the Write Enable Latch (WEL) bit clears to “0” and the SUS sets to “1”, after which the device is ready to accept one of the commands listed in "Table Acceptable Commands During Program/Erase Suspend after tPSL/tESL" (e.g. FAST READ). Refer to " AC Characteristics" for tPSL and tESL timings. "Table Acceptable Commands During Suspend (tPSL/tESL not required)" lists the commands for which the tPSL and tESL latencies do not apply. For example, RDSR, RDSCUR, RSTEN, and RST can be issued at any time after the Suspend instruction.

Status Register bit 15 (SUS) can be read to check the suspend status. The SUS (Program/Erase Suspend Bit) sets to “1” when a program or erase operation is suspended. The SUS clears to “0” when the program or erase operation is resumed.

Acceptable Commands During Program/Erase Suspend after tPSL/tESL

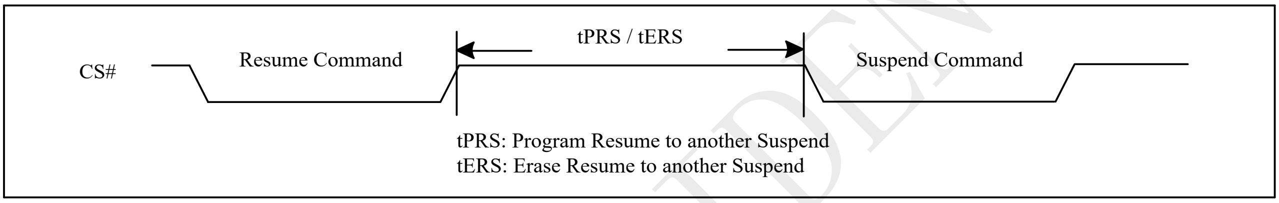
Command name	Command Code	Suspend Type	
		Program Suspend	Erase Suspend
READ	03H	•	•
FAST READ	0BH	•	•
DREAD	3BH	•	•
QREAD	6BH	•	•
2READ	BBH	•	•
4READ	EBH	•	•
Word read	E7H	•	•
Burst Read with Wrap	0CH	•	•
QPIEN	38H	•	•
Disable QPI	FFH	•	•
RDSFDP	5AH	•	•
RDID	9FH	•	•
REMS	90H	•	•
DREMS	92H	•	•
QREMS	94H	•	•
SBL	77H	•	•
Set Read Parameter	C0H	•	•
WREN	06H		•
RESUME	7AH	•	•
PP	02H		•
QPP	32H		•

Command name	Command Code	Suspend Type	
		Program Suspend	Erase Suspend
Erase Security Registers	44H		
Program Security Registers	42H		•
read Security Registers	48H	•	•
WRDI	04H	•	•

Acceptable Commands During Suspend（tPSL/tESL not required）

Command name	Command Code	Suspend Type	
		Program Suspend	Erase Suspend
RDSR	05H	•	•
RDSR2	35H	•	•
RES	ABH	•	•
RSTEN	66H	•	•
RST	99H	•	•
NOP	00H	•	•

Figure 10-37 Resume to Suspend Latency



tPRS: Program Resume to another Suspend
tERS: Erase Resume to another Suspend

10.38 Erase Suspend to Program

The “Erase Suspend to Program” feature allows Page Programming while an erase operation is suspended. Page Programming is permitted in any unprotected memory except within the sector of a suspended Sector Erase operation or within the block of a suspended Block Erase operation. The Write Enable (WREN) instruction must be issued before any Page Program instruction.

A Page Program operation initiated within a suspended erase cannot itself be suspended and must be allowed to finish before the suspended erase can be resumed. The Status Register can be polled to determine the status of the Page Program operation. The WEL and WIP bits of the Status Register will remain “1” while the Page Program operation is in progress and will both clear to “0” when the Page Program operation completes.

Figure 10-38 Suspend to Read/Program Latency

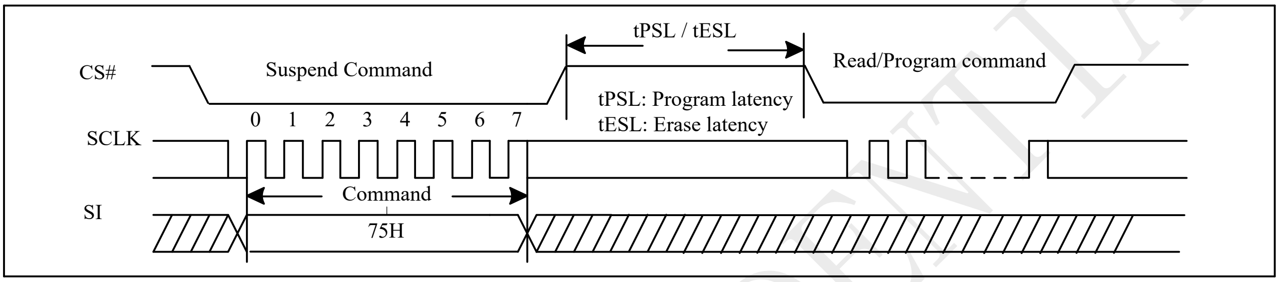
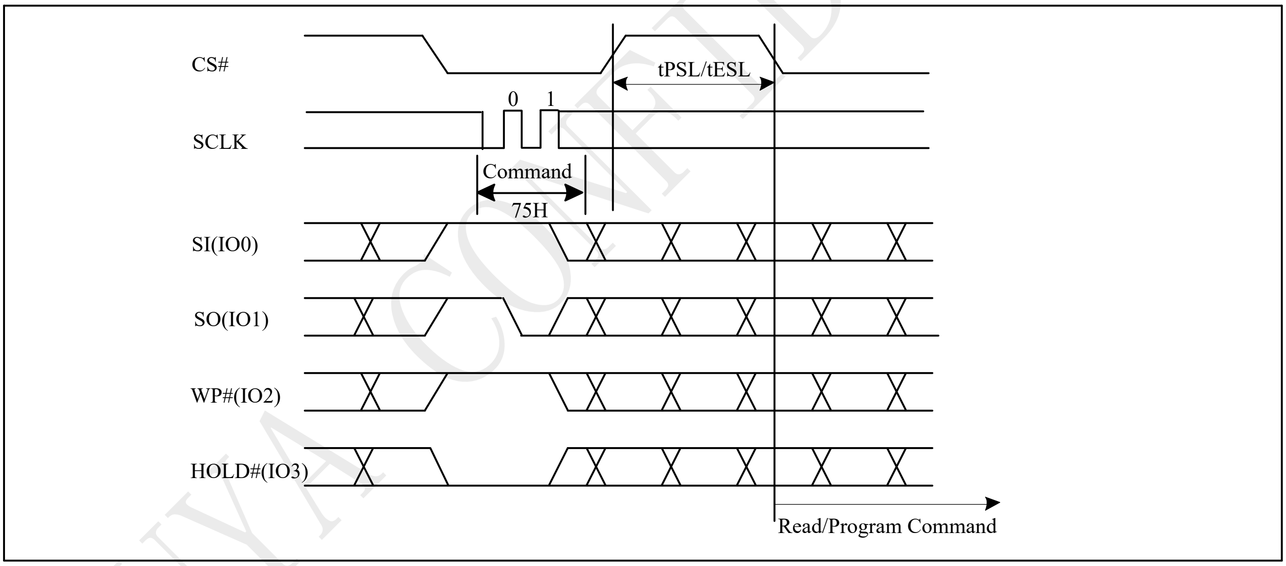


Figure 10-38a Suspend to Read/Program Latency(QPI)



Notes:
1. Please note that Program only available after the Erase-Suspend operation
2. To check suspend ready information, please read status register bit15 (SUS)

10.39 Program Resume and Erase Resume

The Resume instruction resumes a suspended Page Program, Page Erase, Sector Erase, or Block Erase operation. Before issuing the Resume instruction to restart a suspended erase operation, make sure that there is no Page Program operation in progress.

Immediately after the Serial NOR Flash receives the Resume instruction, the WEL and WIP bits are set to “1” and the SUS is cleared to “0”. The program or erase operation will continue until finished ("Resume to Read Latency") or until another Suspend instruction is received. A resume-to-suspend latency of tPRS or tERS must be observed before issuing another Suspend instruction ("Resume to Suspend Latency").

Figure 10-39 Resume to Read Latency

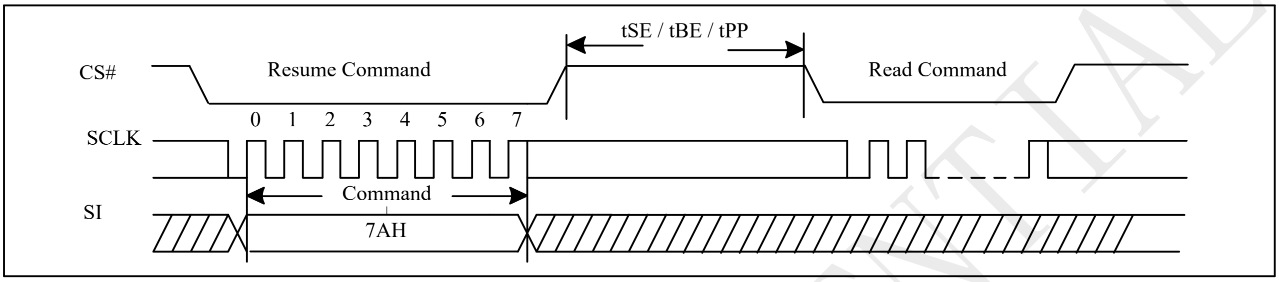
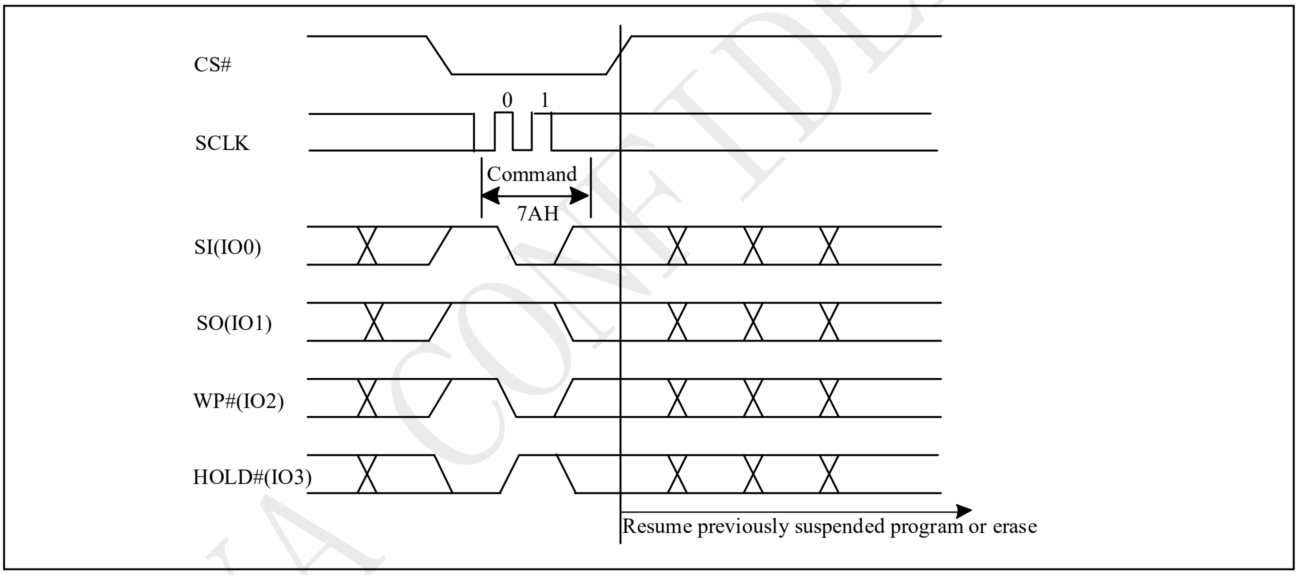


Figure 10-39a Resume to Read Latency(QPI)



10.40 No Operation (NOP)

The "No Operation" command is only able to terminate the Reset Enable (RSTEN) command and will not affect any other command.

The SIO[3:1] are don't care.

10.41 Software Reset (RSTEN/RST)

The Software Reset operation combines two instructions: Reset-Enable (RSTEN) command and Reset (RST) command. It returns the device to a standby mode. All the volatile bits and settings will be cleared then, which makes the device return to the default status as power on, except the ep_fail bit.

To execute Reset command (RST), the Reset-Enable (RSTEN) command must be executed first to perform the Reset operation. If there is any other command to interrupt after the Reset-Enable command, the Reset-Enable will be invalid.

The SIO[3:1] are "don't care".

If the Reset command is executed during program or erase operation, the operation will be disabled, the data under processing could be damaged or lost.

Figure 10-41 Software Reset Recovery

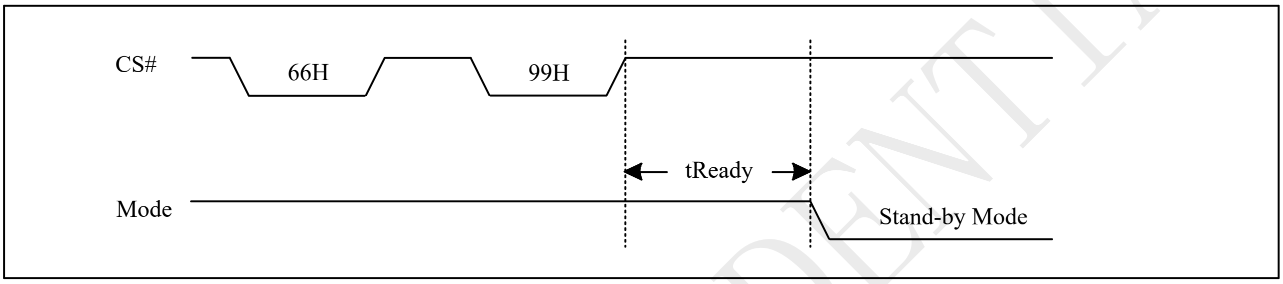


Figure 10-41a Reset Sequence

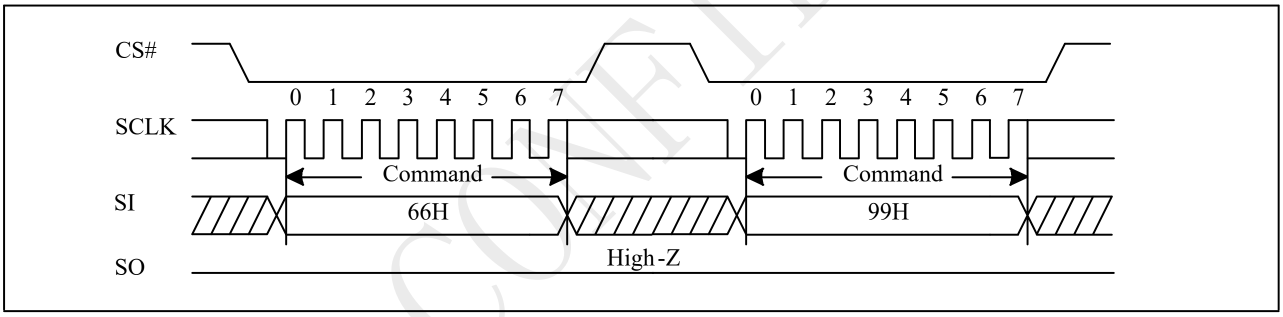
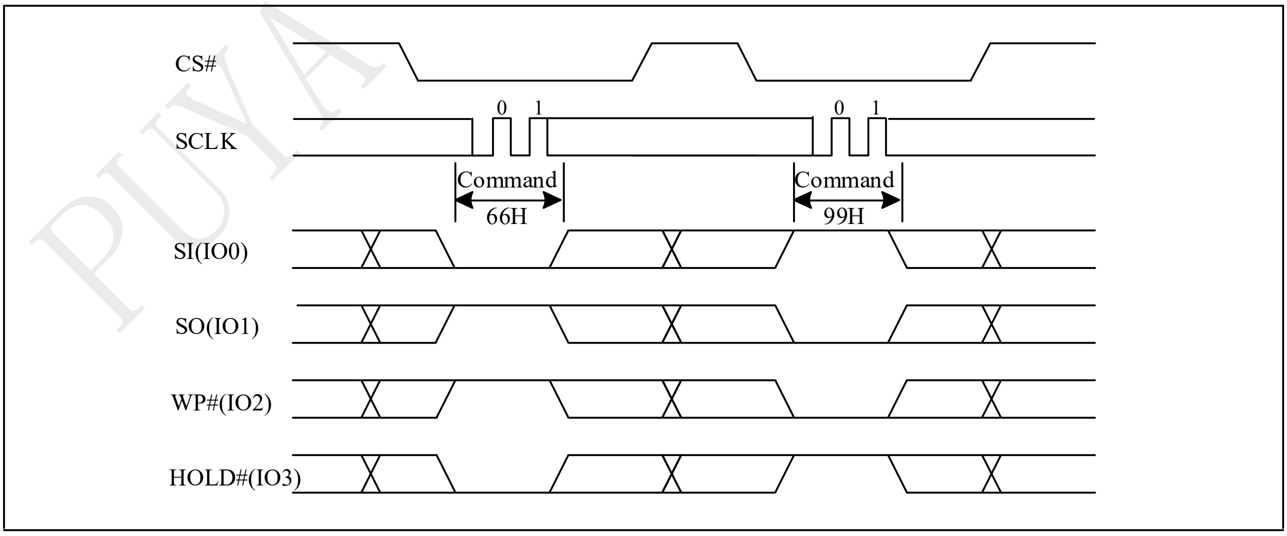


Figure 10-42b Reset Sequence(QPI)

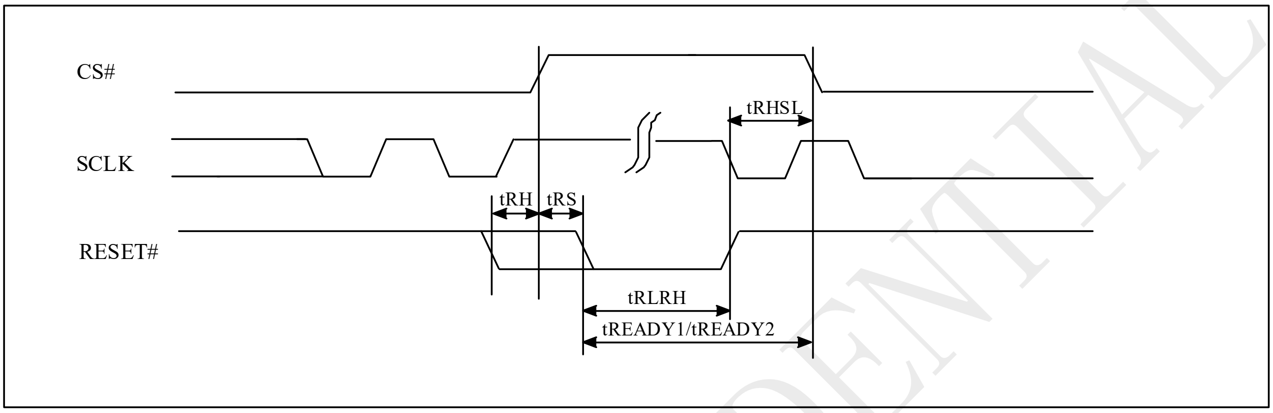


10.42 RESET

Driving the RESET#(HOLD#) pin low for a period of tRLRH or longer will reset the device. After reset cycle, the device is at the following states:

- Standby mode
- All the volatile bits such as WEL/WIP/SRAM lock bit will return to the default status as power on.

If the device is under programming or erasing, driving the HOLD# pin low will also terminate the operation and data could be lost. During the resetting cycle, the SO data becomes high impedance and the current will be reduced to minimum.



RESET Timing (Power On)

Symbol	Parameter	Min	Typ	Max	Unit
tRHSL	Reset# high before CS# low	10			us
tRS	Reset# setup time	150			ns
tRH	Reset# hold time	150			ns
tRLRH	Reset# low pulse width	10			us
tREADY1	Reset Recovery time			30	us

RESET Timing (Other Operation)

Symbol	Parameter	Min	Typ	Max	Unit
tRHSL	Reset# high before CS# low	10			us
tRS	Reset# setup time	150			ns
tRH	Reset# hold time	150			ns
tRLRH	Reset# low pulse width	10			us
tREADY2	Reset Recovery time (except WRSR/WRCR)			50	us
	Reset Recovery time (for WRSR/WRCR)			12	ms

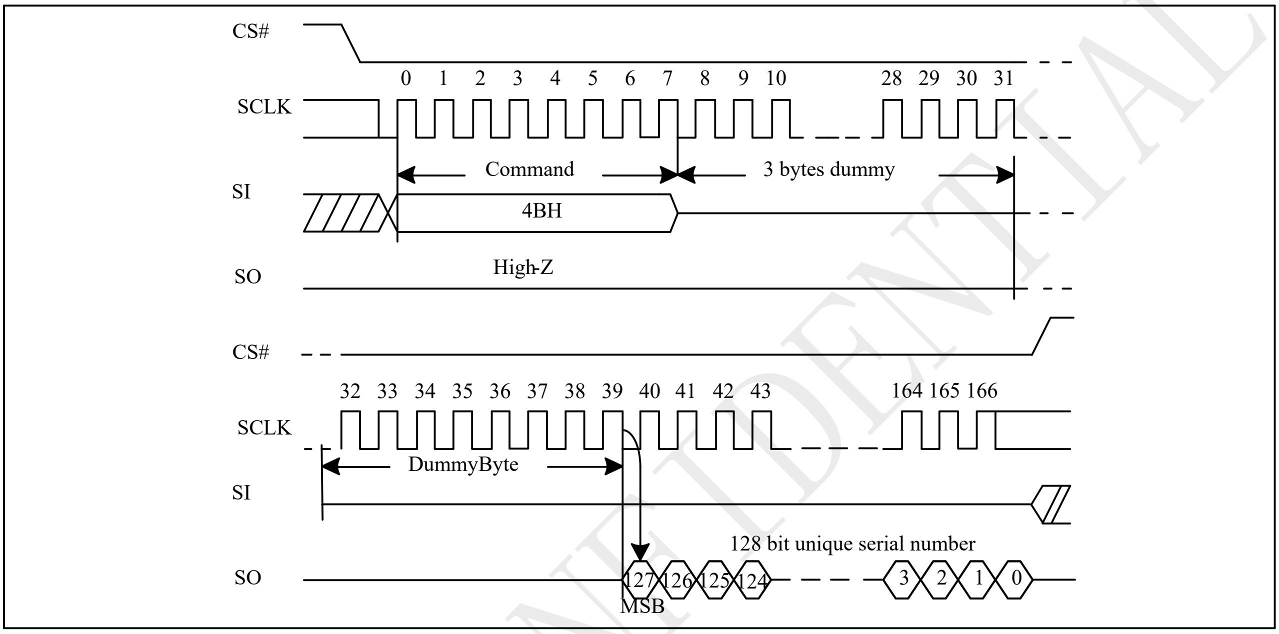
10.43 Read Unique ID (RUID)

The Read Unique ID command accesses a factory-set read-only 128bit number that is unique to each P25QSxx device. The Unique ID can be used in conjunction with user software methods to help prevent copying or cloning of a system.

The Read Unique ID command sequence: CS# goes low → sending Read Unique ID command →Dummy Byte1 →Dummy Byte2 →Dummy Byte3 → Dummy Byte4 → 128bit Unique ID Out → CS# goes high.

The command sequence is show below.

Figure 10-43 Read Unique ID (RUID) Sequence (Command 4B)



10.44 Read SFDP Mode (RDSFDP)

The Serial Flash Discoverable Parameter (SFDP) standard provides a consistent method of describing the functional and feature capabilities of serial flash devices in a standard set of internal parameter tables. These parameter tables can be interrogated by host system software to enable adjustments needed to accommodate divergent features from multiple vendors. The concept is similar to the one found in the Introduction of JEDEC Standard, JESD68 on CFI.

The sequence of issuing RDSFDP instruction is same as FREAD: CS# goes low→ send RDSFDP instruction (5Ah)→send 3 address bytes on SI pin→ send 1 dummy byte on SI pin→ read SFDP code on SO→ to end RDSFDP operation can use CS# to high at any time during data out.

Detail SFDP data please contact Puya.

Figure 10-44 Read Serial Flash Discoverable Parameter (RDSFDP) Sequence

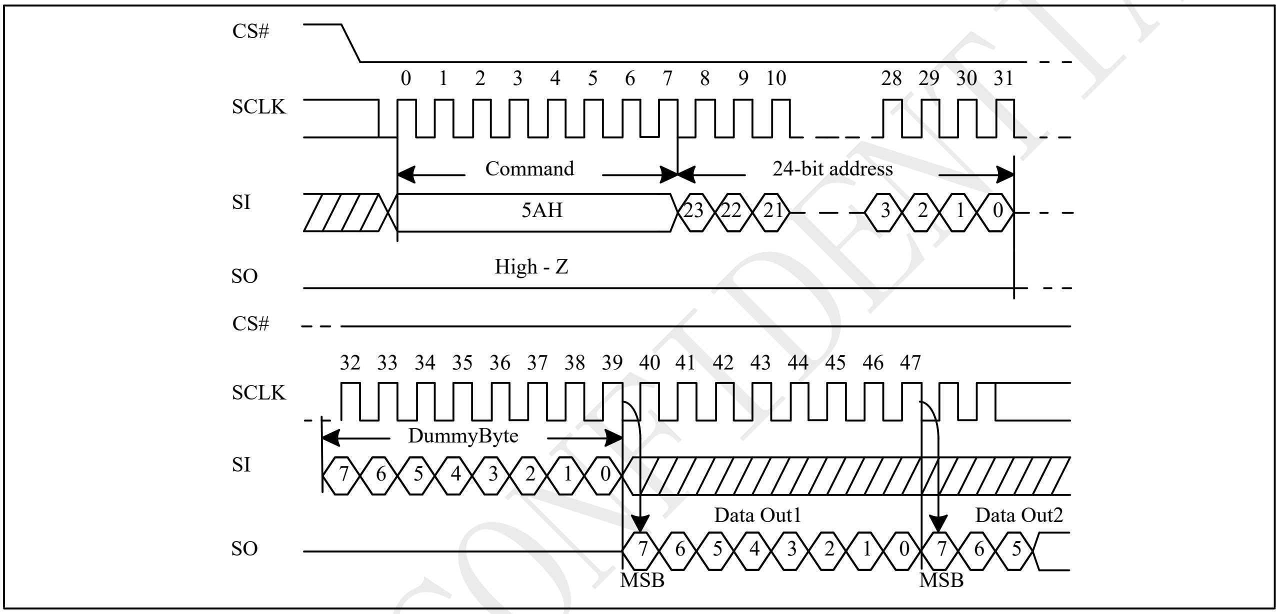
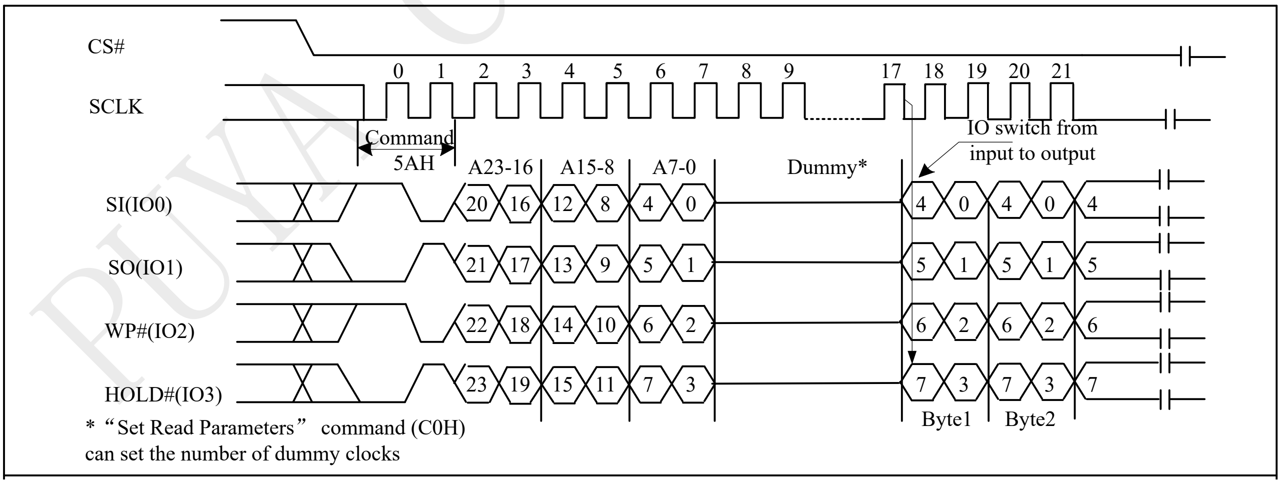


Figure 10-44a Read Serial Flash Discoverable Parameter (RDSFDP) Sequence(QPI)



11 Ordering Information

P 25 Q 40TU A - SS H - I T - x

Company Designator
P = Puya Semiconductor

Product Family
25 = SPI interface flash

Product Serial
Q = Q serial

Memory Density
40T = 4Mb

Operation Voltage
U = 1.65V~3.6V

Generation
A = A Version Default = blank

Package Type

SS = SOP8 150mil	UX = USON8 3x2x0.55mm
TS = TSSOP8	SV = USON8 1.5x1.5x0.45mm
WF = WAFER	

Plating Technology
H: RoHS Compliant Halogen free, Antimony free

Device Grade
I =- 40 ~ 85C

Packing Type
T = TUBE
R = TAPE & REEL
Y = TRAY
W = WAFER

Ordering Option
Default = blank

12 Valid Part Numbers and Top Marking

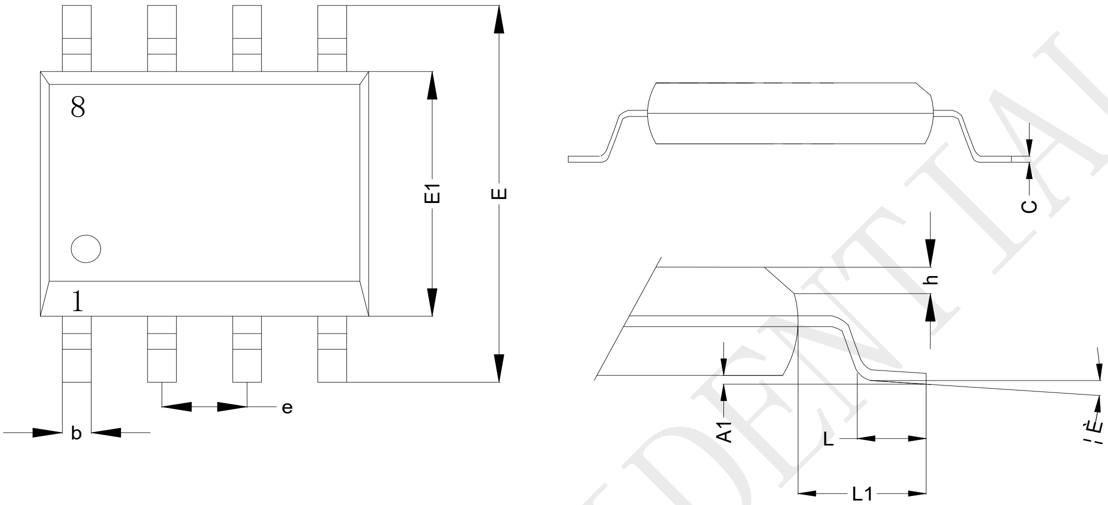
The following table provides the valid part numbers for the P25Q40TU Flash Memory. Please contact PUYA for specific availability by density and package type. PUYA Flash memories use a 15-digit Product Number for ordering.

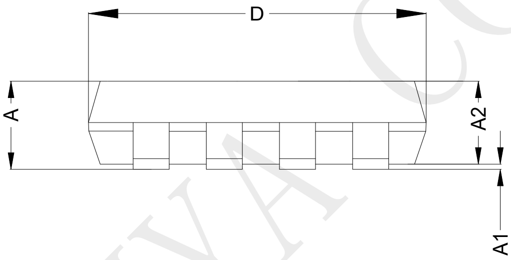
Package Type	Product Number	Density	Top Side Marking	Temp.	Packing Type
SS* SOP8 150mil	P25Q40TU-SSH-IT	4M-bit	P25Q40TU xxxxxxx	85C	Tube
SS* SOP8 150mil	P25Q40TU-SSH-IR	4M-bit	P25Q40TU xxxxxxx	85C	Reel
TS* TSSOP8	P25Q40TU-TSH-IT	4M-bit	P25Q40TU xxxxxxx	85C	Reel
TS* TSSOP8	P25Q40TU-TSH-IR	4M-bit	P25Q40TU xxxxxxx	85C	Reel
UX* USON8 3x2mm	P25Q40TU-UXH-IR	4M-bit	PQ40T Xxxx	85C	Reel
SV* USON8 1.5x1.5mm	P25Q40TU-SVH-IR	4M-bit	Q4TU xxxx	85C	Reel
SS* SOP8 150mil	P25Q20TU-SSH-IT	2M-bit	P25Q20TU xxxxxxx	85C	Tube
SS* SOP8 150mil	P25Q20TU-SSH-IR	2M-bit	P25Q20TU xxxxxxx	85C	Reel
TS* TSSOP8	P25Q20TU-TSH-IT	2M-bit	P25Q20TU xxxxxxx	85C	Reel
TS* TSSOP8	P25Q20TU-TSH-IR	2M-bit	P25Q20TU xxxxxxx	85C	Reel
UX* USON8 3x2mm	P25Q20TU-UXH-IR	2M-bit	PQ20T Xxxx	85C	Reel
SV* USON8 1.5x1.5mm	P25Q20TU-SVH-IR	2M-bit	Q2TU xxxx	85C	Reel

Note：The package marked with "*", if necessary, please contact Puya sales.

13 Package Information

13.1 8-Lead SOP(150mil)





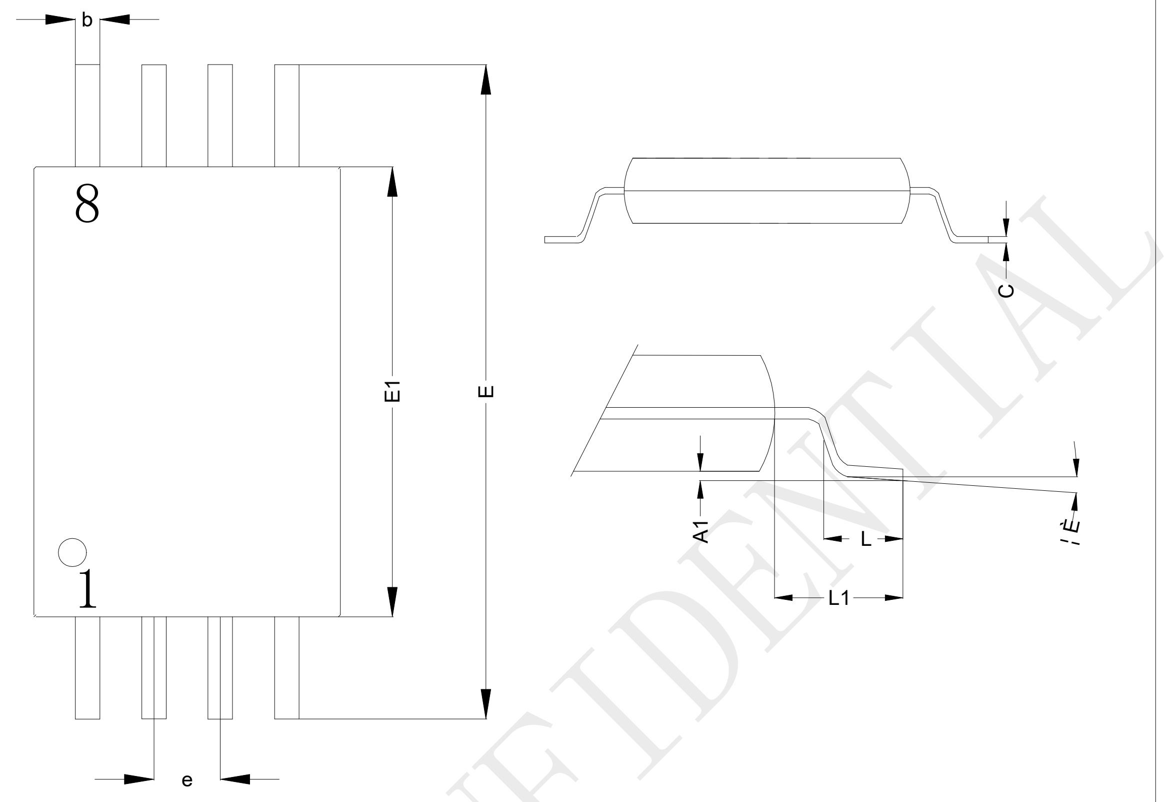
Common Dimensions
(Unit of Measure=millimeters)

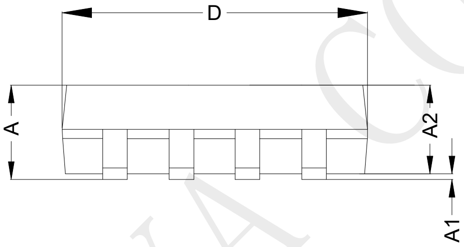
Symbol	Min	Typ	Max
A	1.350	-	1.750
A1	0.100	-	0.250
A2	1.250	-	-
b	0.310	-	0.510
c	0.170	-	0.250
D	4.800	4.900	5.000
E	5.800	6.000	6.200
E1	3.800	3.900	4.000
e	-	1.270	-
L	0.400	-	1.270
L1	-	1.050	-
¦È	0	-	8¡ã
h	0.25	-	0.50

Note： 1. Dimensions are not to scale

	TITLE	DRAWING NO.	REV
	Puya SOP8（150mil）POD	QRPD-0004	1.1

13.2 8-Lead TSSOP





Common Dimensions

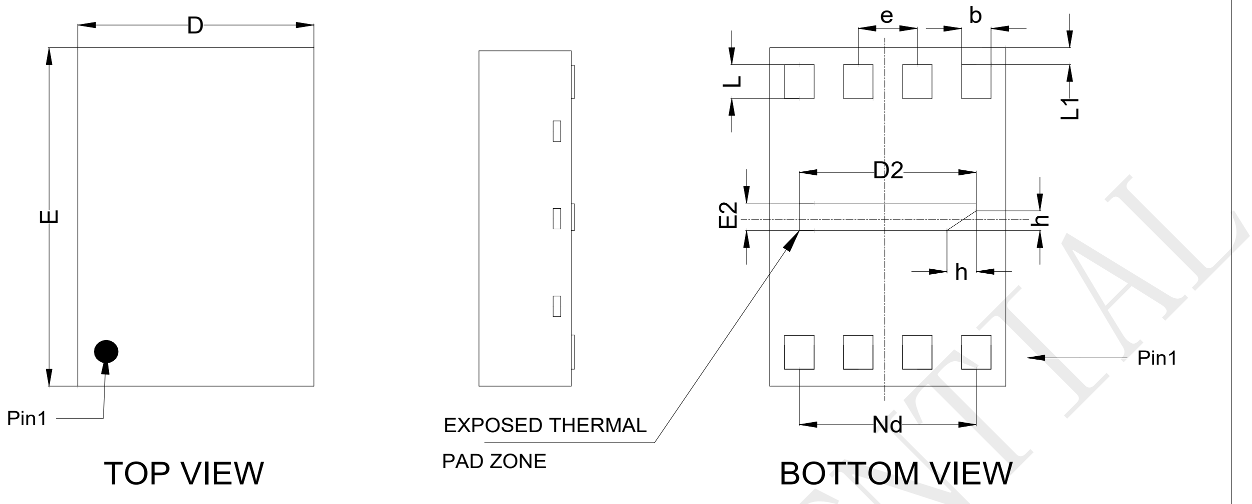
(Unit of Measure=millimeters)

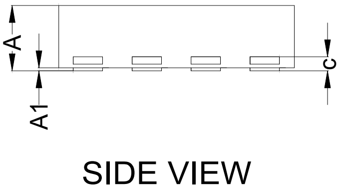
Symbol	Min	Typ	Max
A	-	-	1.200
A1	0.050	-	0.150
A2	0.800	1.000	1.050
b	0.190	-	0.300
c	0.090	-	0.200
D	2.900	3.000	3.100
E	6.200	6.400	6.600
E1	4.300	4.400	4.500
e	-	0.650	-
L	0.450	-	0.750
L1	-	1.000	-
¦È	0	-	8¡ã

Note：1. Dimensions are not to scale

PUYA	TITLE PUYA TSSOP8 POD	DRAWING NO. QRPD-0019	REV 1.1

13.3 8-Pad USON(3x2x0.55mm)





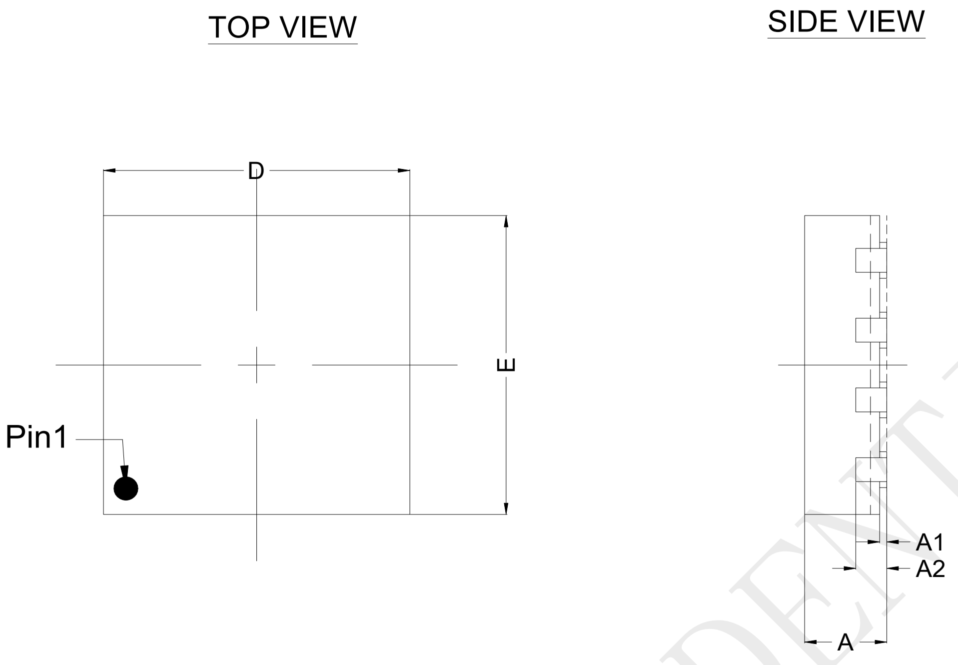
Common Dimensions
(Unit of Measure=millimeters)

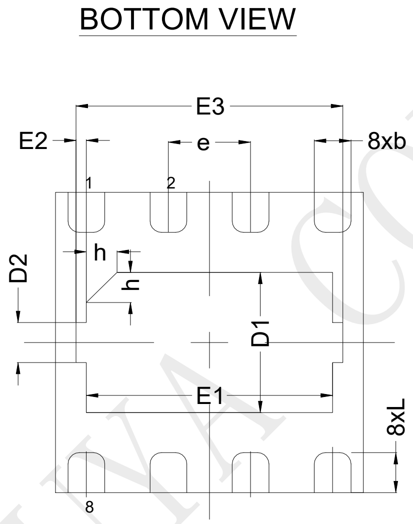
Symbol	Min	Typ	Max
A	0.50	0.55	0.60
A1	0.00	0.02	0.05
b	0.18	0.25	0.30
D	1.90	2.00	2.10
D2	1.50	1.60	1.70
E	2.90	3.00	3.10
E2	0.10	0.20	0.30
e		0.50BSC	
L	0.30	0.35	0.40
h	0.05	0.15	0.25
Nd		1.50BSC	
L1	0.05	0.10	0.15
c	0.10	0.15	0.20

Note：1. Dimensions are not to scale

PUYA	TITLE Puya USON8L 2x3x0.55-0.5PITCH POD	DRAWING NO. QRPD-0009	REV 1.0

13.4 8-Pad USON(1.5x1.5x0.45mm)





Common Dimensions

(Unit of Measure=millimeters)

Symbol	Min	Typ	Max
A	0.400	0.450	0.500
A1	0.000	0.035	0.050
A2	0.127REF		
b	0.150	0.200	0.250
D	1.450	1.500	1.550
E	1.450	1.500	1.550
e	0.400BSC		
L	0.150	0.200	0.250
D1	0.600	0.700	0.800
E1	1.100	1.200	1.300
D2	0.200REF		
E2	0.050REF		
E3	1.200	1.300	1.400
h	0.100	0.150	0.200

Note£ Dimensions are not to scale.

TITLE PUYA USON8 1.5x1.5x0.45-0.4 PITCH POD	DRAWING NO. QRPD-0008	REV 1.2

14 Revision History

Rev.	Date	Description	Note
1.0	2025-03-25	Initial Release	-